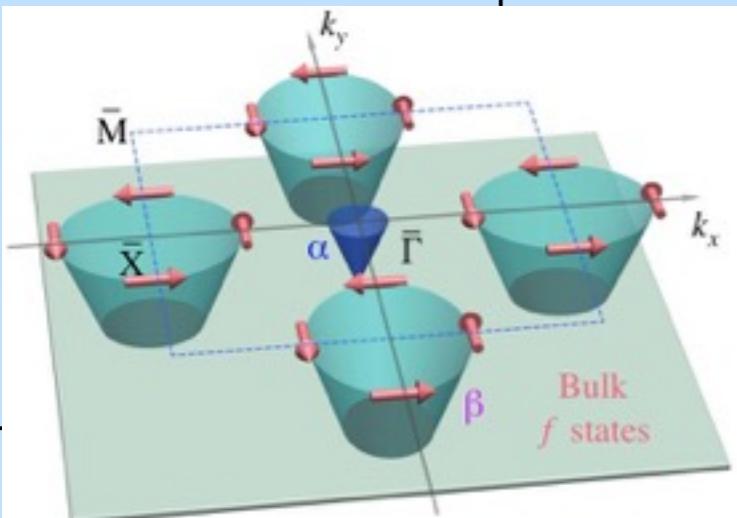




(S-)ARPES investigation on the first topological Kondo insulator: SmB₆



Nan Xu

Swiss Light Source, Paul Scherrer Institut
& École polytechnique fédérale de Lausanne

Acknowledgment

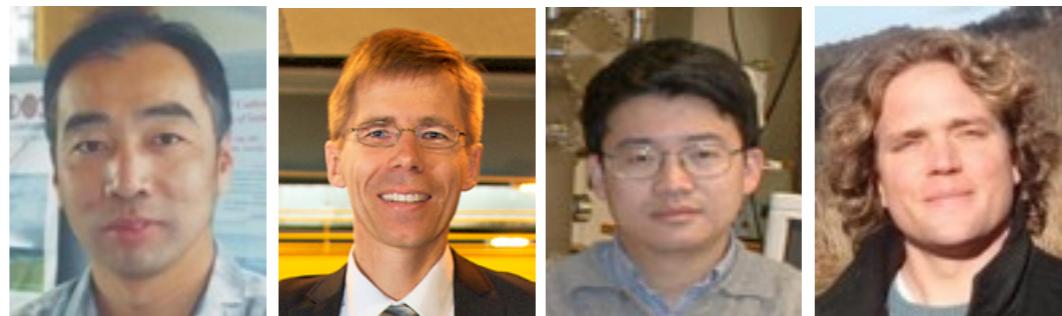
(S-)ARPES measurements

PSI: M. Shi, J. Mesot, C. Matt, R. Dhaka, Y. Huang, N. Plumb, M. Radovic

IOP: H. Ding, X. Shi

COPHEE: J. H. Dil, G. Landolt, S. Muff

IFW: S.V. Borisenko



High-quality single crystals

PSI: E. Pomjakushina, K. Conder, P. Biswas, A. Amato, Z. Salman

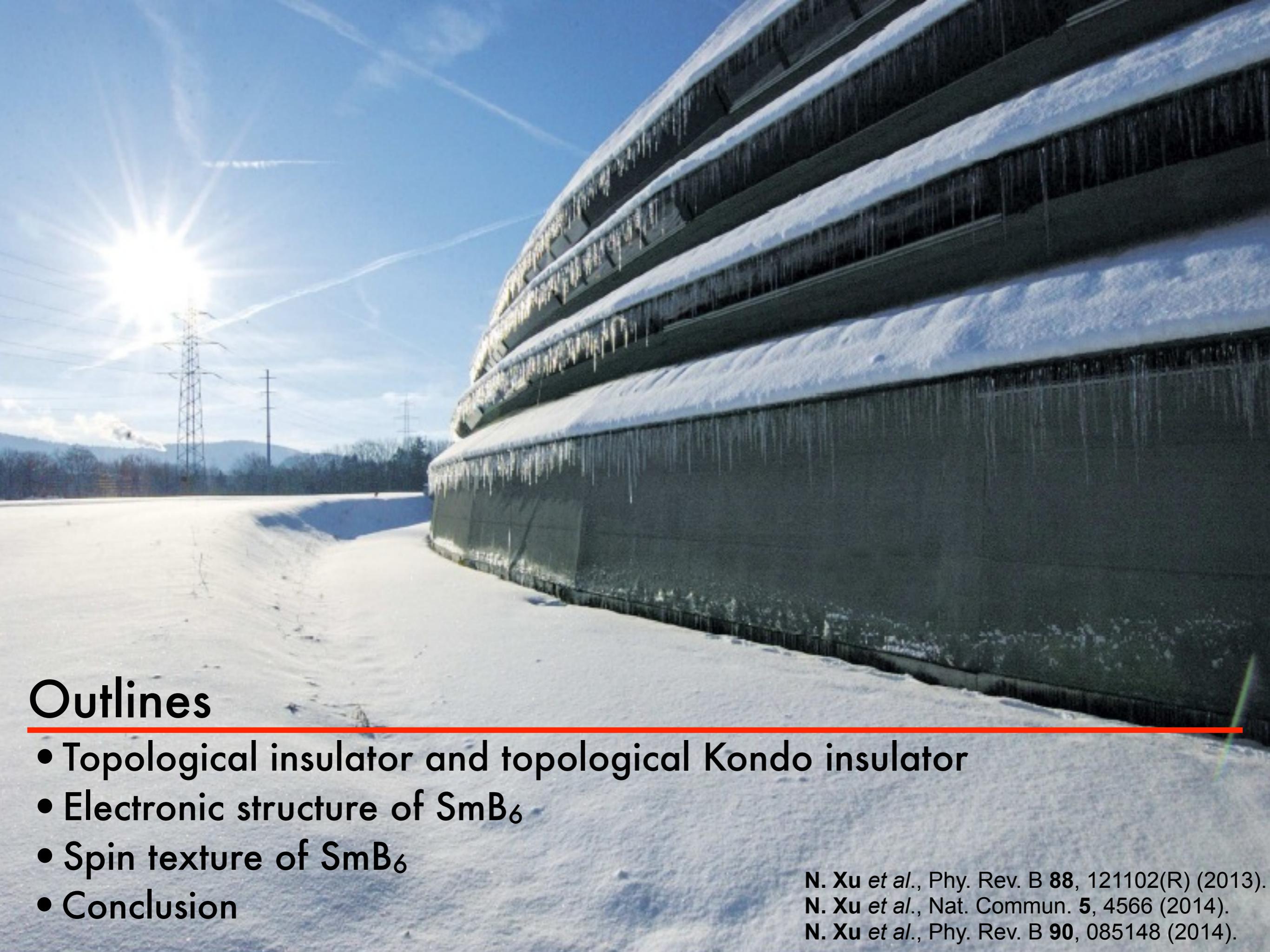
University of Warwick: D. Paul



Theoretical support

IOP: Z. Fang, X. Dai, H. M. Weng, R. Yu



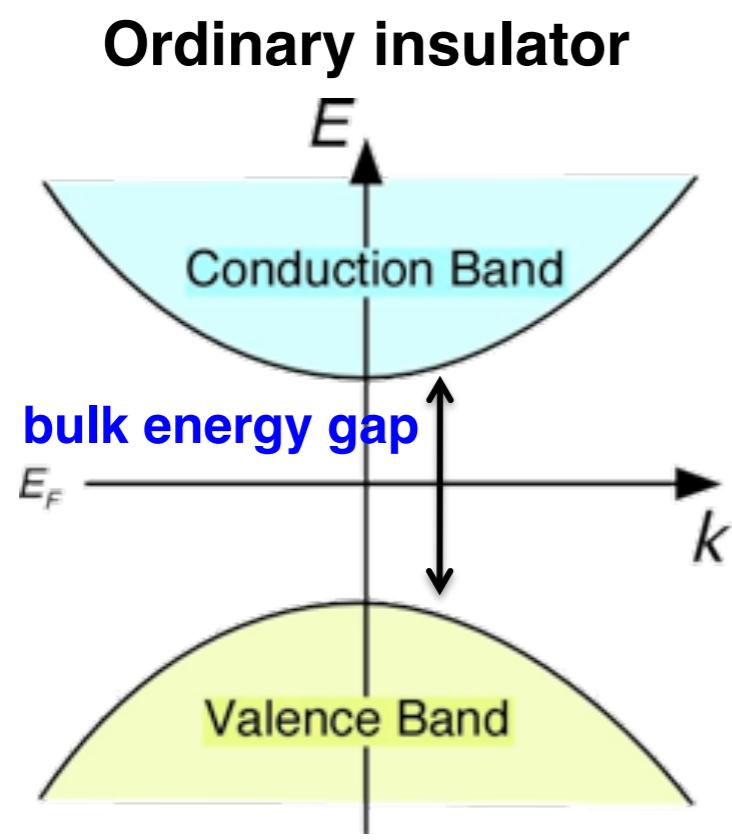
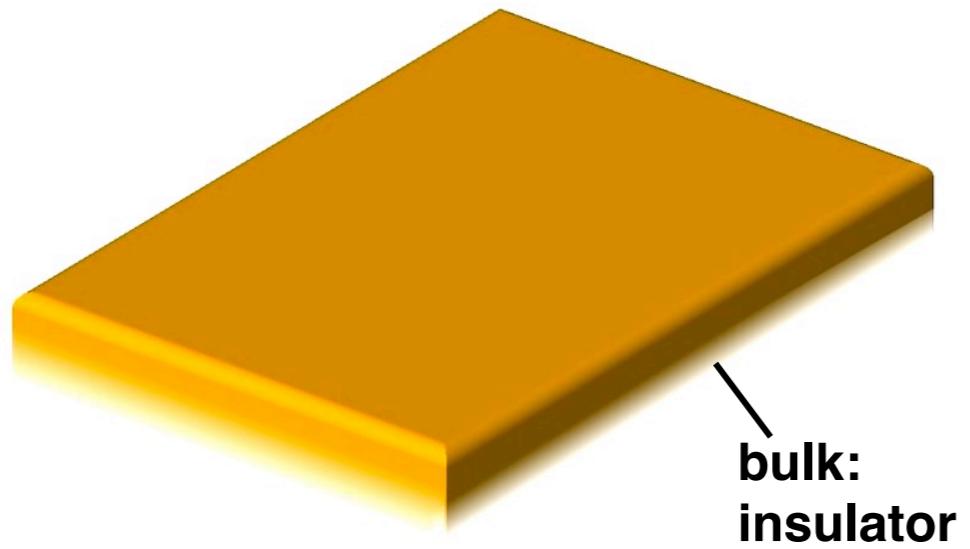


Outlines

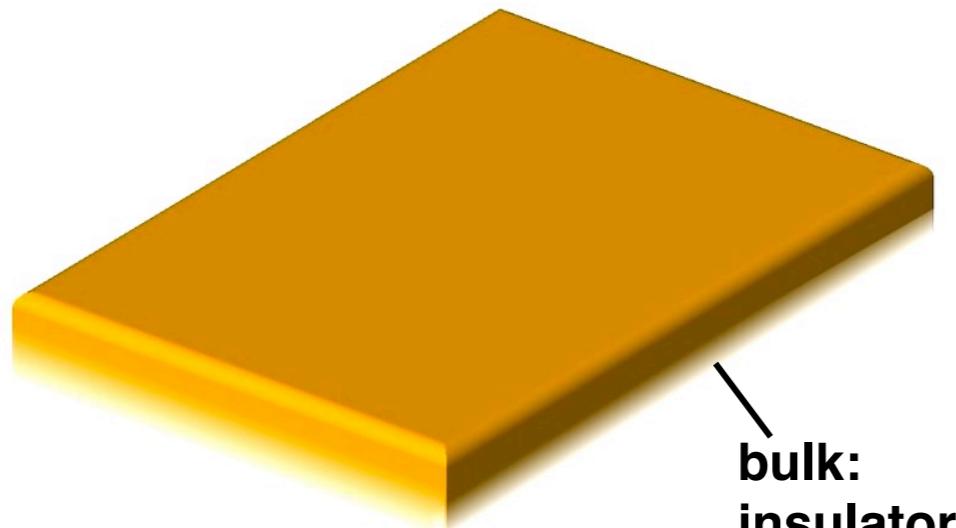
- Topological insulator and topological Kondo insulator
- Electronic structure of SmB_6
- Spin texture of SmB_6
- Conclusion

N. Xu *et al.*, *Phy. Rev. B* **88**, 121102(R) (2013).
N. Xu *et al.*, *Nat. Commun.* **5**, 4566 (2014).
N. Xu *et al.*, *Phy. Rev. B* **90**, 085148 (2014).

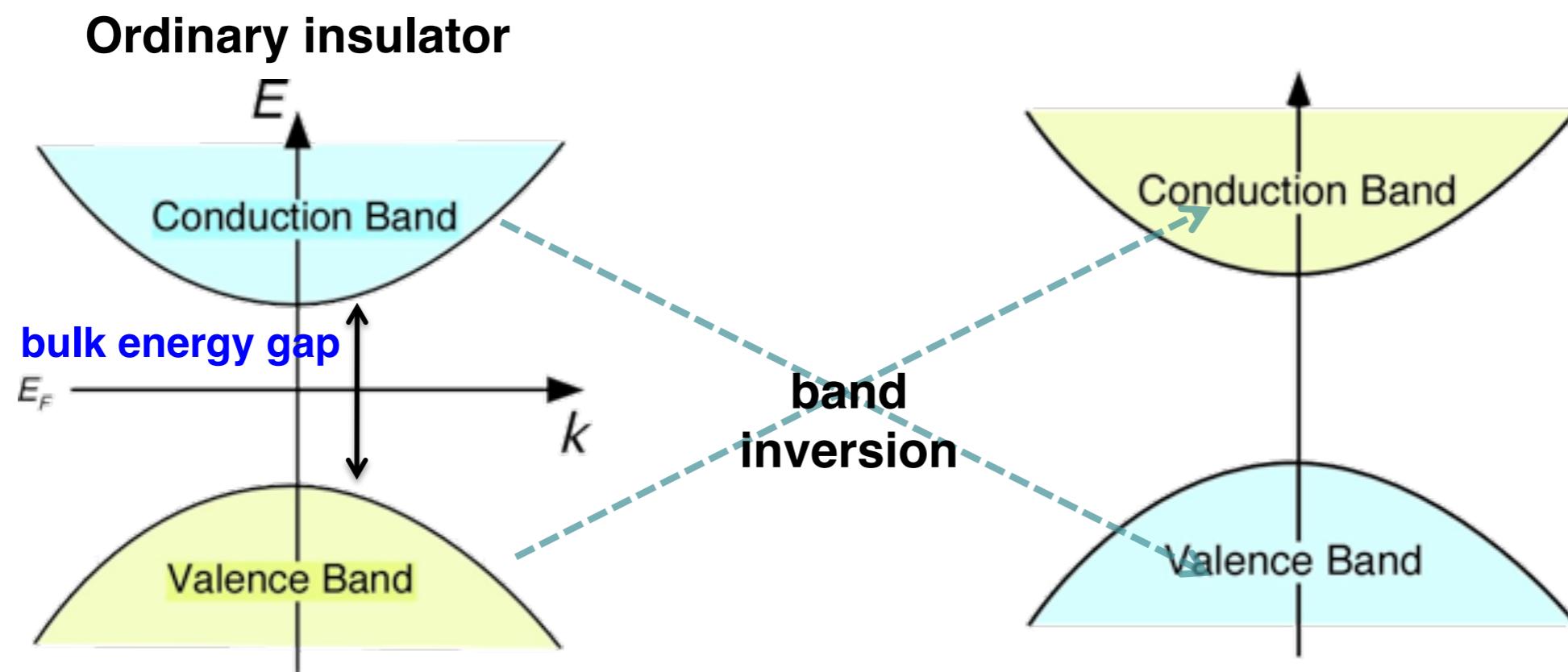
Topological Insulator



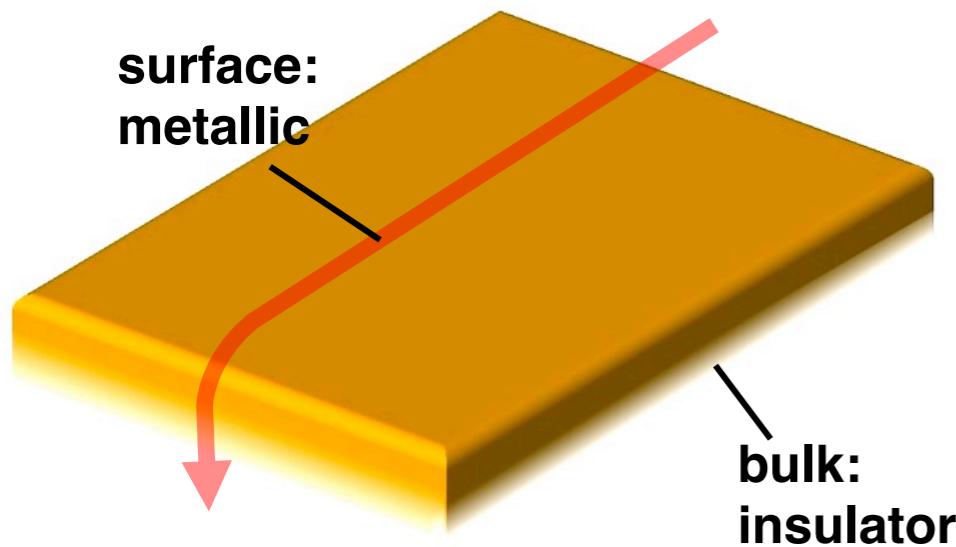
Topological Insulator



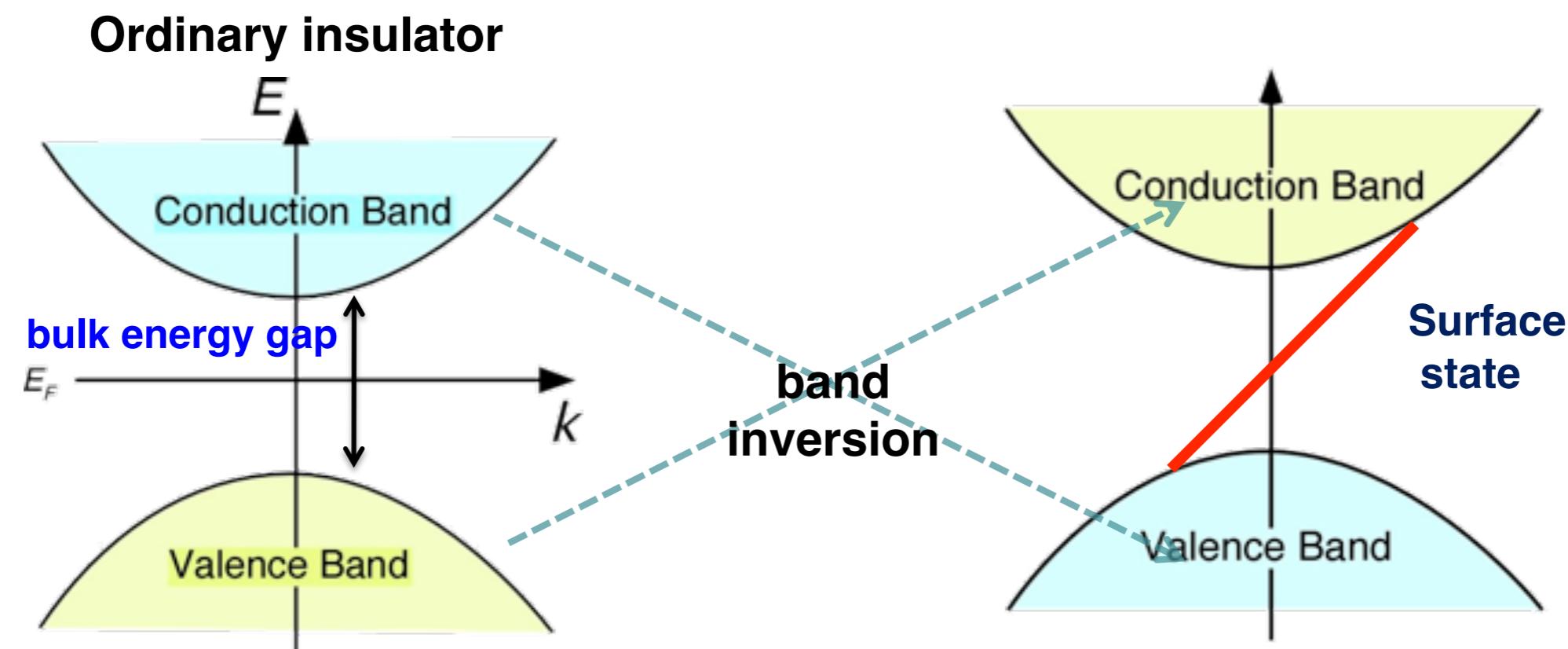
Spin-orbit interaction



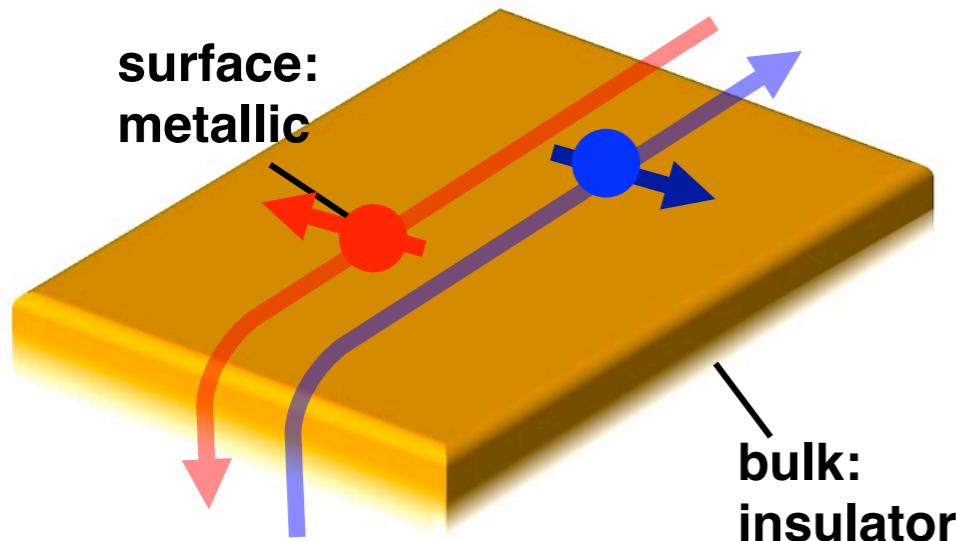
Topological Insulator



**Spin-orbit interaction
+ Topology (surface)**



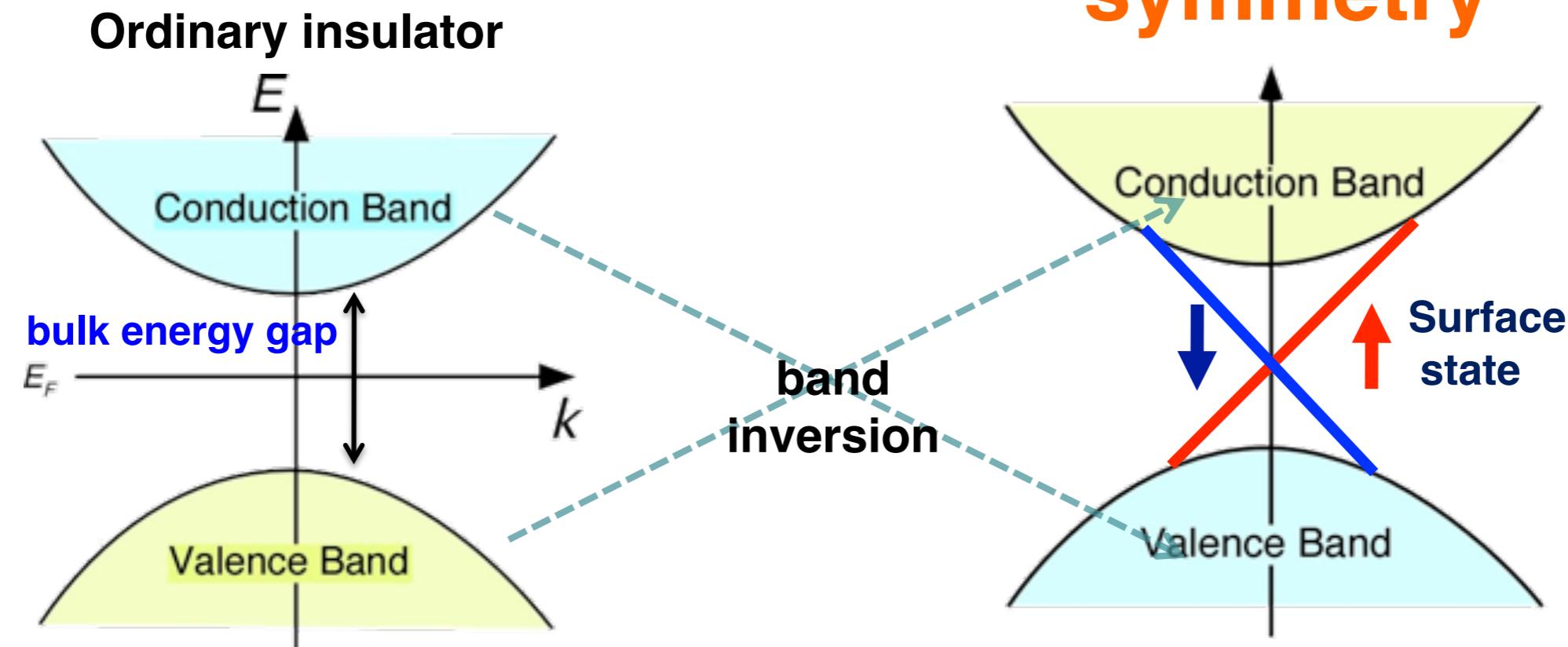
Topological Insulator



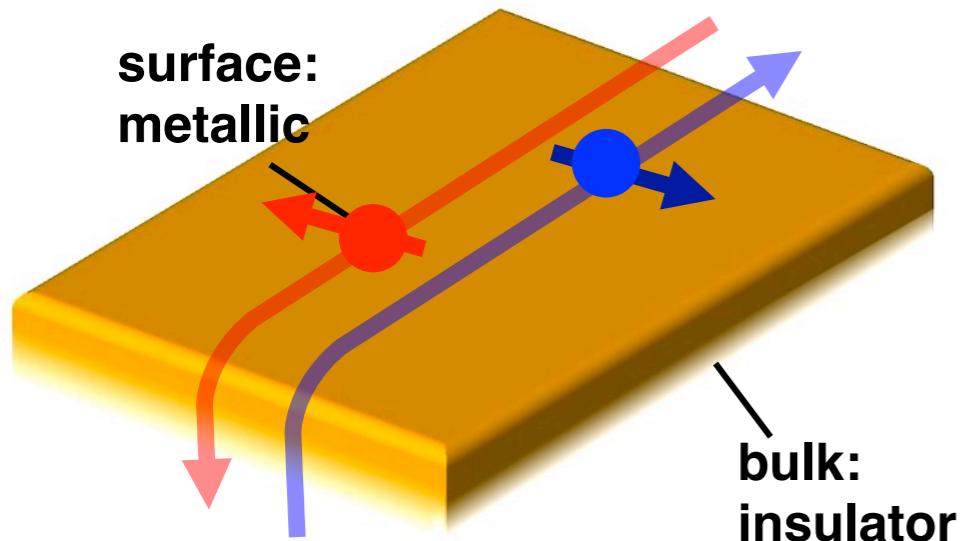
Spin-orbit interaction
+ Topology (surface)



+ Time reversal symmetry



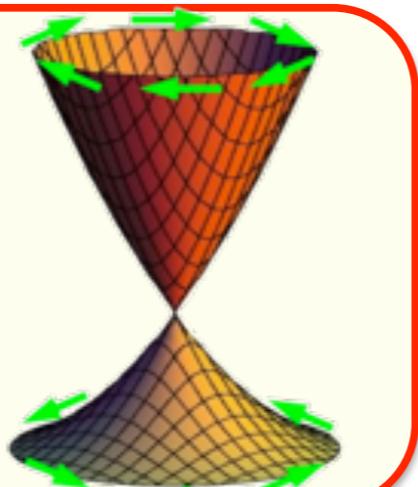
Topological Insulator



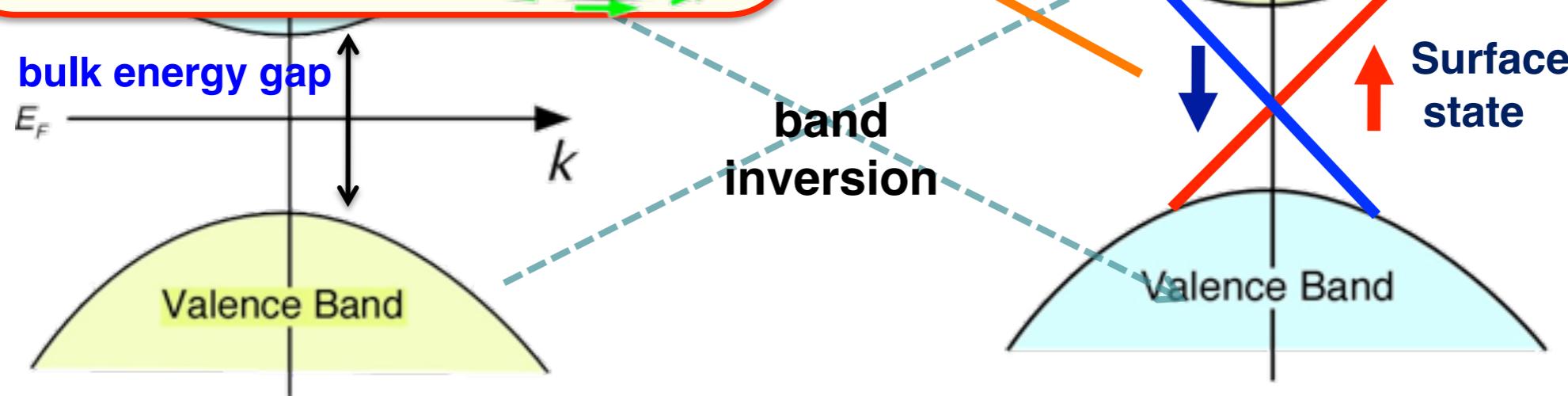
Spin-orbit interaction
+ Topology (surface)



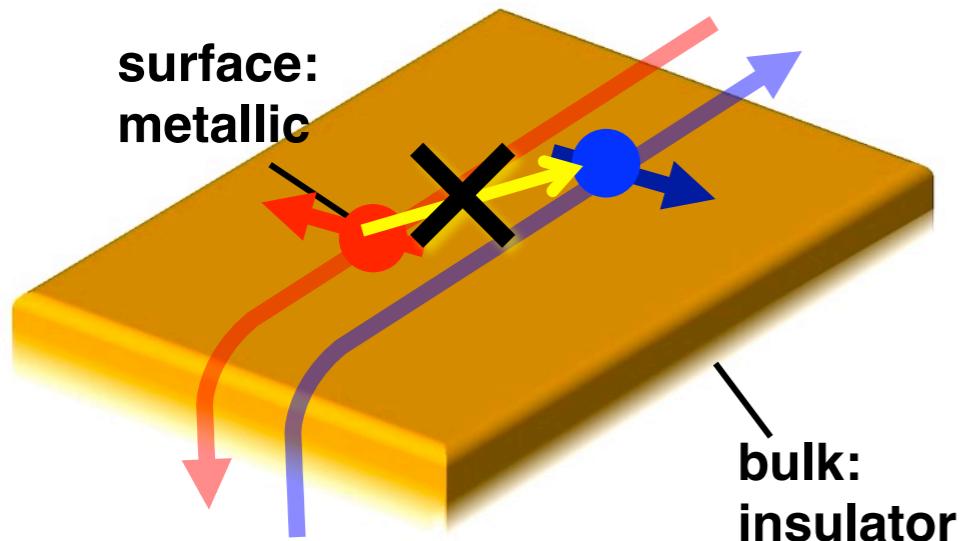
Dirac-cone state
helical spin



+ Time reversal symmetry



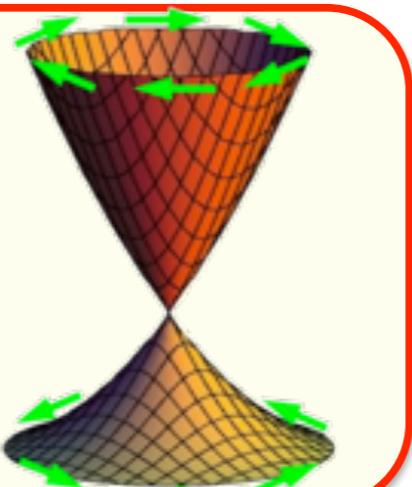
Topological Insulator



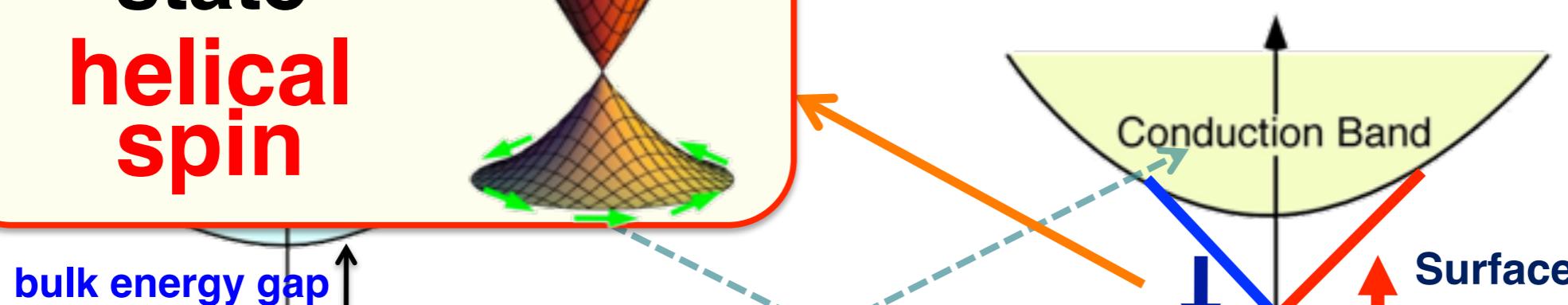
Spin-orbit interaction
+ Topology (surface)



Dirac-cone state
helical spin



+ Time reversal symmetry



Characteristics of Dirac cone

- Tunable spin-polarization by E -field
- Back-scattering prohibited : error-free devices

No Bulk Insulating

Experimental

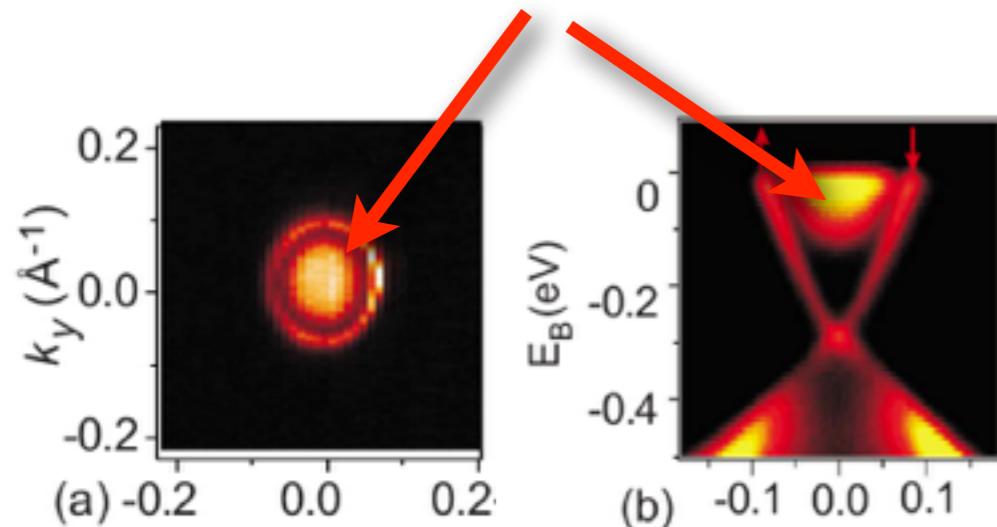
Table I. Summary of topological insulator materials that have been experimentally addressed. The definite table, S.S., P.T., and SM stand for surface state, phase transition, and semimetal, respectively.)

Type	Material	Band gap	Bulk transport
2D, $\nu = 1$	CdTe/HgTe/CdTe	< 10 meV	insulating
2D, $\nu = 1$	AlSb/InAs/GaSb/AlSb	~4 meV	weakly insulating
3D (1;111)	Bi _{1-x} Sb _x	< 30 meV	weakly insulating
3D (1;111)	Sb	semimetal	metallic
3D (1;000)	Bi ₂ Se ₃	0.3 eV	metallic
3D (1;000)	Bi ₂ Te ₃	0.17 eV	metallic
3D (1;000)	Sb ₂ Te ₃	0.3 eV	metallic
3D (1;000)	Bi ₂ Te ₂ Se	~0.2 eV	reasonably insulating
3D (1;000)	(Bi,Sb) ₂ Te ₃	< 0.2 eV	moderately insulating
3D (1;000)	Bi _{2-x} Sb _x Te _{3-y} Se _y	< 0.3 eV	reasonably insulating
3D (1;000)	Bi ₂ Te _{1.6} S _{1.4}	0.2 eV	metallic
3D (1;000)	Bi _{1.1} Sb _{0.9} Te ₂ S	0.2 eV	moderately insulating
3D (1;000)	Sb ₂ Te ₂ Se	?	metallic
3D (1;000)	Bi ₂ (Te,Se) ₂ (Se,S)	0.3 eV	semi-metallic
3D (1;000)	TlBiSe ₂	~0.35 eV	metallic
3D (1;000)	TlBiTe ₂	~0.2 eV	metallic
3D (1;000)	TlBi(S,Se) ₂	< 0.35 eV	metallic
3D (1;000)	PbBi ₂ Te ₄	~0.2 eV	metallic
3D (1;000)	PbSb ₂ Te ₄	?	metallic
3D (1;000)	GeBi ₂ Te ₄	0.18 eV	metallic
3D (1;000)	PbBi ₄ Te ₇	0.2 eV	metallic
3D (1;000)	GeBi _{4-x} Sb _x Te ₇	0.1–0.2 eV	metallic
3D (1;000)	(PbSe) ₅ (Bi ₂ Se ₃) ₆	0.5 eV	metallic
3D (1;000)	(Bi ₂)(Bi ₂ Se _{2.6} S _{0.4})	semimetal	metallic
3D (1;000)	(Bi ₂)(Bi ₂ Te ₃) ₂	?	?
3D TCI	SnTe	0.3 eV (4.2 K)	metallic
3D TCI	Pb _{1-x} Sn _x Te	< 0.3 eV	metallic
3D TCI	Pb _{0.77} Sn _{0.23} Se	invert with T	metallic
2D, $\nu = 1?$	Bi bilayer	~0.1 eV	?
3D (1;000)?	Ag ₂ Te	?	metallic
3D (1;111)?	SmB ₆	20 meV	insulating
3D (0;001)?	Bi ₁₄ Rh ₃ I ₉	0.27 eV	metallic
3D (1;000)?	RBiPt ($R = \text{Lu, Dy, Gd}$)	zero gap	metallic
Weyl SM?	Nd ₂ (Ir _{1-x} Rh _x) ₂ O ₇	zero gap	metallic

No Bulk Insulating

Experimental

Bulk Conducting Band



D. Hsieh, et al., Nature, 460, 1101. (2009)

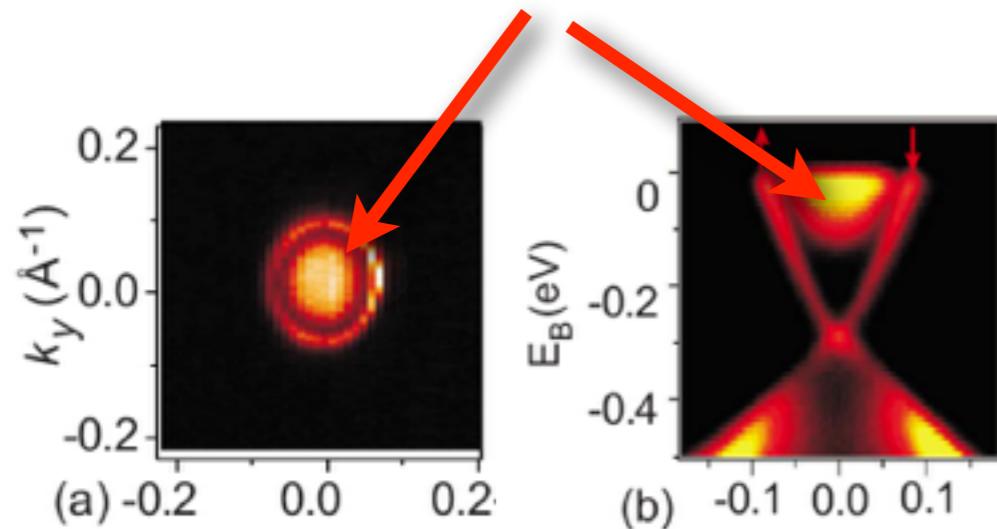
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3D (1;000)	Bi_2Se_3	0.3 eV	metallic
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3D (1;000)	$(\text{Bi},\text{Sb})_2\text{Te}_3$	< 0.2 eV	moderately insulating
3D (1;000)	$\text{Bi}_{2-x}\text{Sb}_x\text{Te}_{3-y}\text{Se}_y$	< 0.3 eV	reasonably insulating
3D (1;000)	$\text{Bi}_2\text{Te}_{1.6}\text{S}_{1.4}$	0.2 eV	metallic
3D (1;000)	$\text{Bi}_{1.1}\text{Sb}_{0.9}\text{Te}_2\text{S}$	0.2 eV	moderately insulating
3D (1;000)	$\text{Sb}_2\text{Te}_2\text{Se}$?	metallic
3D (1;000)	$\text{Bi}_2(\text{Te},\text{Se})_2(\text{Se},\text{S})$	0.3 eV	semi-metallic
3D (1;000)	TlBiSe_2	~0.35 eV	metallic
3D (1;000)	TlBiTe_2	~0.2 eV	metallic
3D (1;000)	$\text{TlBi}(\text{S},\text{Se})_2$	< 0.35 eV	metallic
3D (1;000)	PbBi_2Te_4	~0.2 eV	metallic
3D (1;000)	PbSb_2Te_4	?	metallic
3D (1;000)	GeBi_2Te_4	0.18 eV	metallic
3D (1;000)	PbBi_4Te_7	0.2 eV	metallic
3D (1;000)	$\text{GeBi}_{4-x}\text{Sb}_x\text{Te}_7$	0.1–0.2 eV	metallic
3D (1;000)	$(\text{PbSe})_5(\text{Bi}_2\text{Se}_3)_6$	0.5 eV	metallic
3D (1;000)	$(\text{Bi}_2)(\text{Bi}_2\text{Se}_{2.6}\text{S}_{0.4})$	semimetal	metallic
3D (1;000)	$(\text{Bi}_2)(\text{Bi}_2\text{Te}_3)_2$?	?
3D TCI	SnTe	0.3 eV (4.2 K)	metallic
3D TCI	$\text{Pb}_{1-x}\text{Sn}_x\text{Te}$	< 0.3 eV	metallic
3D TCI	$\text{Pb}_{0.77}\text{Sn}_{0.23}\text{Se}$	invert with T	metallic
2D, $\nu = 1?$	Bi bilayer	~0.1 eV	?
3D (1;000)?	Ag ₂ Te	?	metallic
3D (1;111)?	SmB ₆	20 meV	insulating
3D (0;001)?	$\text{Bi}_{14}\text{Rh}_3\text{I}_9$	0.27 eV	metallic
3D (1;000)?	$R\text{BiPt}$ ($R = \text{Lu, Dy, Gd}$)	zero gap	metallic
Weyl SM?	$\text{Nd}_2(\text{Ir}_{1-x}\text{Rh}_x)_2\text{O}_7$	zero gap	metallic

No Bulk Insulating

Experimental

Bulk Conducting Band



D. Hsieh, et al., Nature, 460, 1101. (2009)

No Bulk insulating

- Transport measurements
- Bulk sensitive measurements
- Spintronics applications

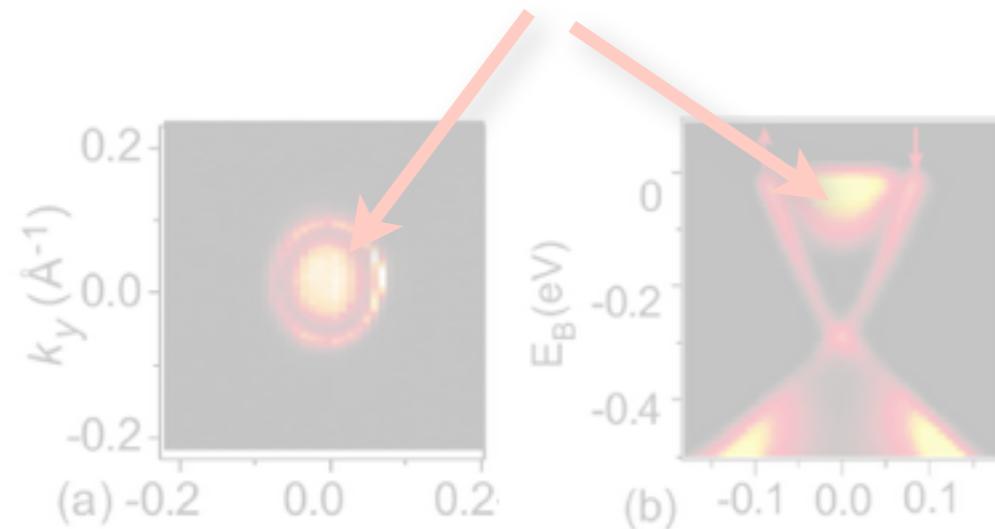
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3D (1;000)	$(\text{Bi},\text{Sb})_2\text{Te}_3$	< 0.2 eV	moderately insulating
3D (1;000)	$\text{Bi}_{2-x}\text{Sb}_x\text{Te}_{3-y}\text{Se}_y$	< 0.3 eV	reasonably insulating
3D (1;000)	$\text{Bi}_2\text{Te}_{1.6}\text{S}_{1.4}$	0.2 eV	metallic
3D (1;000)	$\text{Bi}_{1.1}\text{Sb}_{0.9}\text{Te}_2\text{S}$	0.2 eV	moderately insulating
3D (1;000)	$\text{Sb}_2\text{Te}_2\text{Se}$?	metallic
3D (1;000)	$\text{Bi}_2(\text{Te},\text{Se})_2(\text{Se},\text{S})$	0.3 eV	semi-metallic
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3D (1;000)	$\text{TlBi}(\text{S},\text{Se})_2$	< 0.35 eV	metallic
3D (1;000)	PbBi_2Te_4	~0.2 eV	metallic
3D (1;000)	PbSb_2Te_4	?	metallic
3D (1;000)	GeBi_2Te_4	0.18 eV	metallic
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3D (1;000)	$(\text{Bi}_2)(\text{Bi}_2\text{Se}_{2.6}\text{S}_{0.4})$	semimetal	metallic
3D (1;000)	$(\text{Bi}_2)(\text{Bi}_2\text{Te}_3)_2$?	?
3D TCI	SnTe	0.3 eV (4.2 K)	metallic
3D TCI	$\text{Pb}_{1-x}\text{Sn}_x\text{Te}$	< 0.3 eV	metallic
3D TCI	$\text{Pb}_{0.77}\text{Sn}_{0.23}\text{Se}$	invert with T	metallic
2D, $\nu = 1?$	Bi bilayer	~0.1 eV	?
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Weyl SM?	$\text{Nd}_2(\text{Ir}_{1-x}\text{Rh}_x)_2\text{O}_7$	zero gap	metallic

Correlation effect

Experimental

Bulk Conducting Band



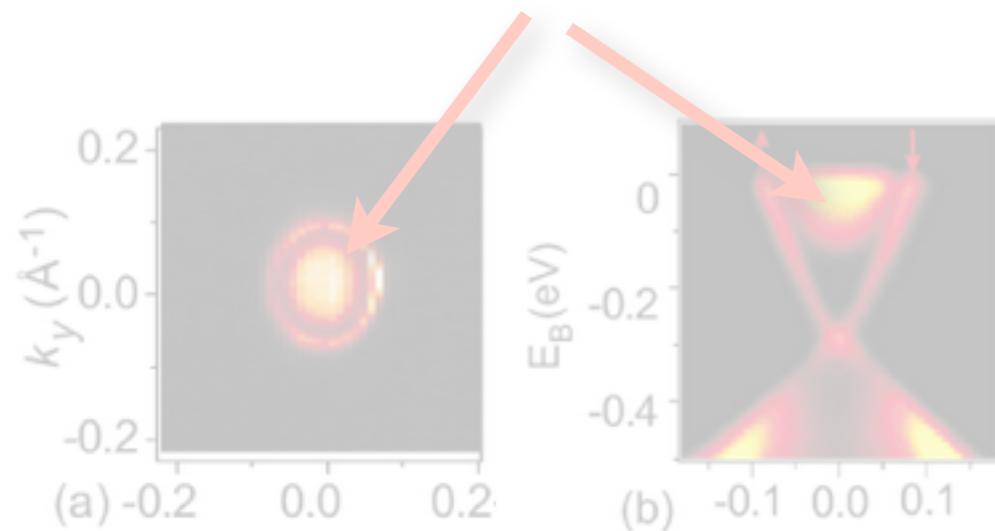
No Bulk insulating

- Transport measurements
- Bulk sensitive measurements
- Spintronics applications

Correlation effect

Experimental

Bulk Conducting Band



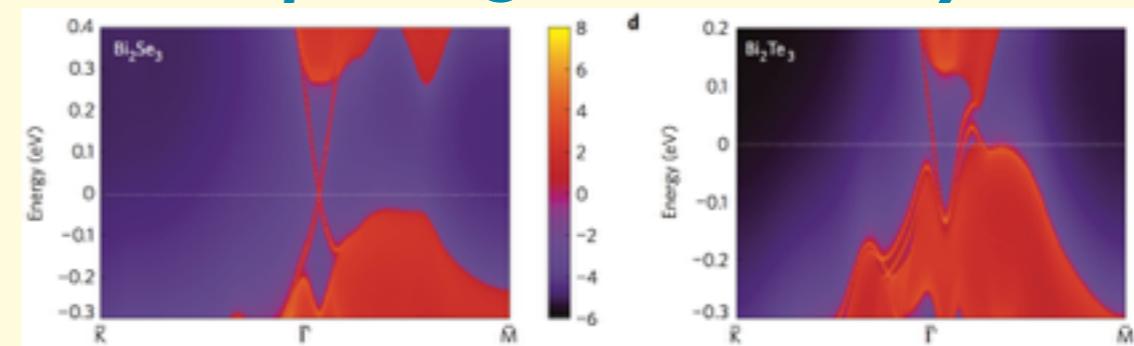
No Bulk insulating

- Transport measurements
- Bulk sensitive measurements
- Spintronics applications

D. Hsieh, et al., Nature, 460, 1101. (2009)

Theoretical

Non(weak)-interacting Topological theory

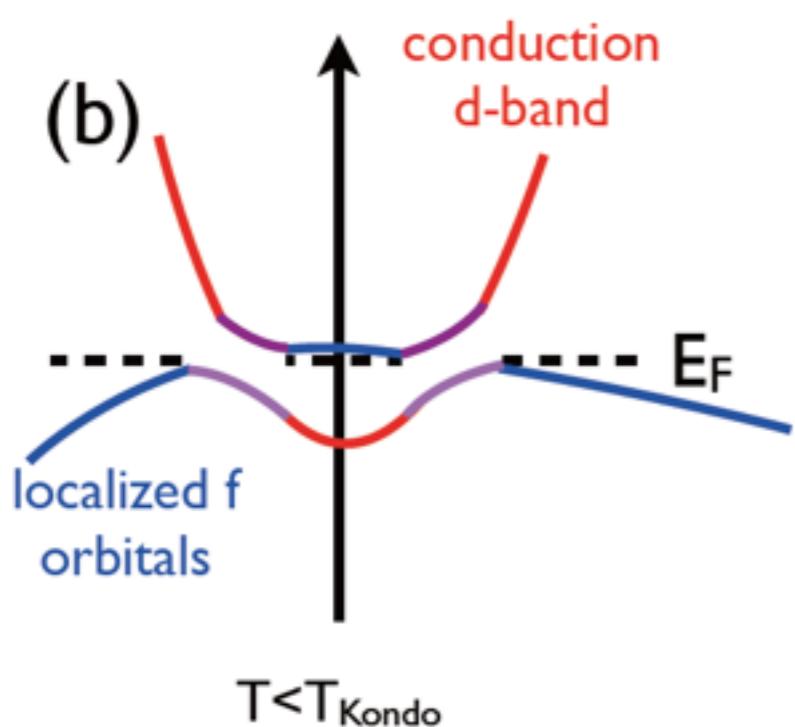
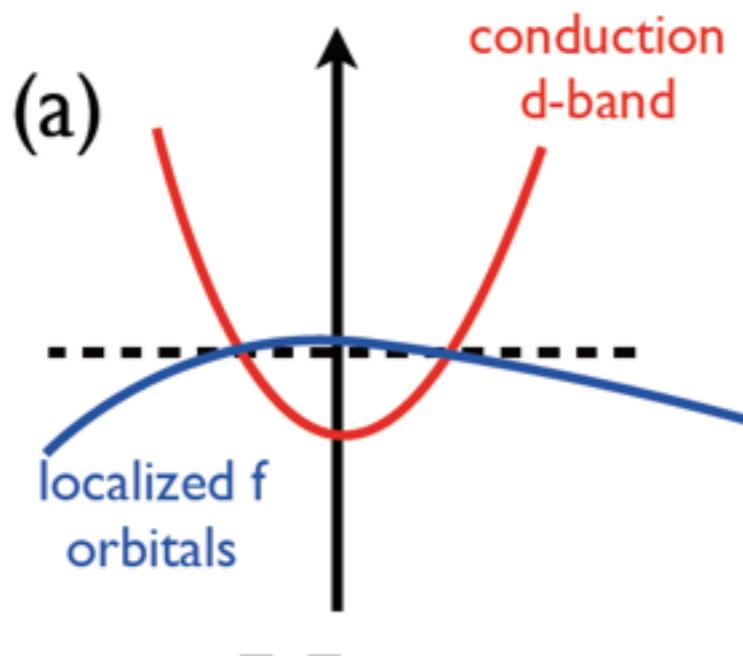


H. Zhang, et al., Nature Physics, 5, 438. (2009)
X.-L. Qi, S.-C. Zhang, Rev. Mod. Phys. 83, 1057 (2011).
M.Z. Hasan, C.L. Kane, Rev. Mod. Phys. 82, 3045 (2010).

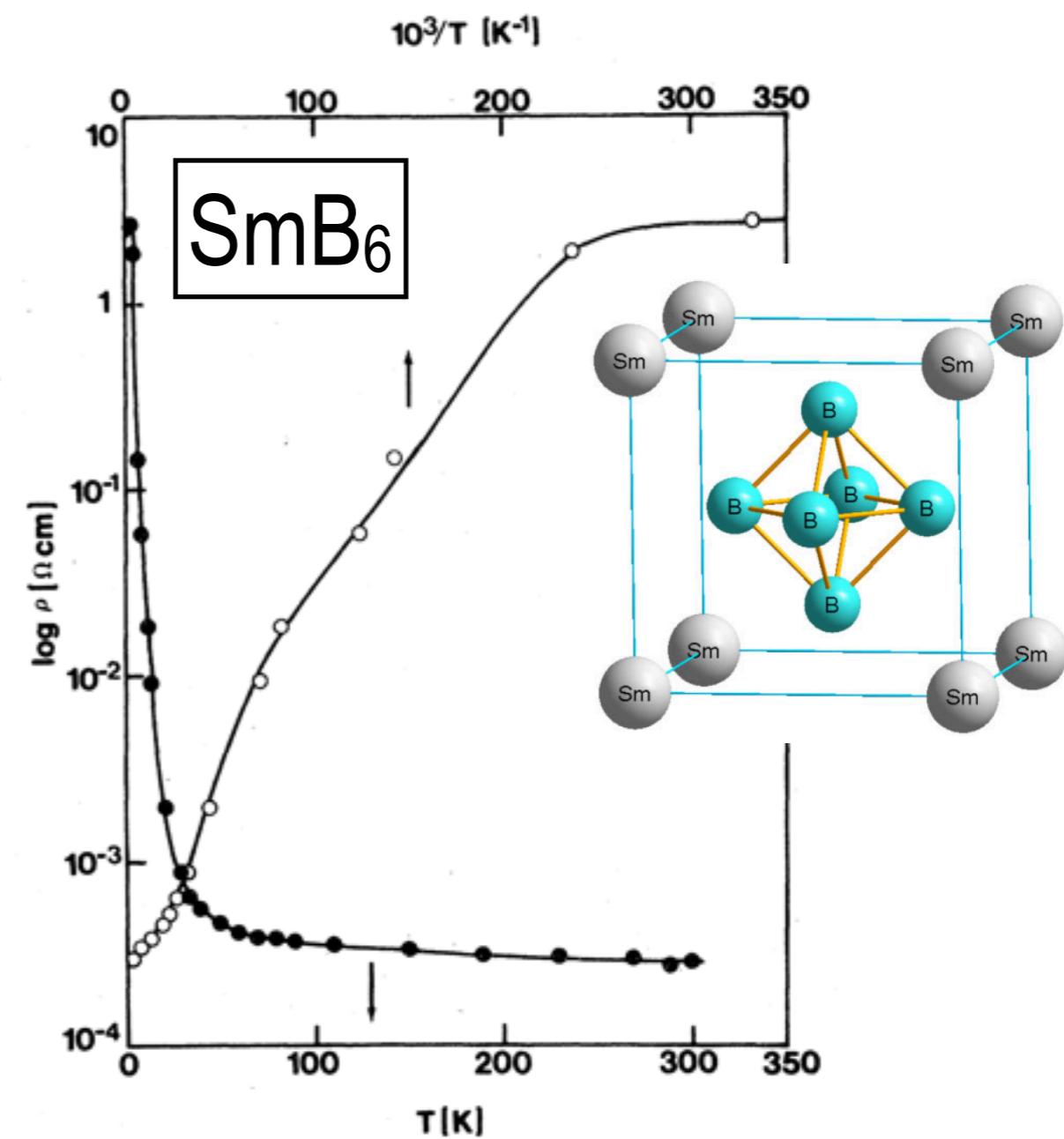
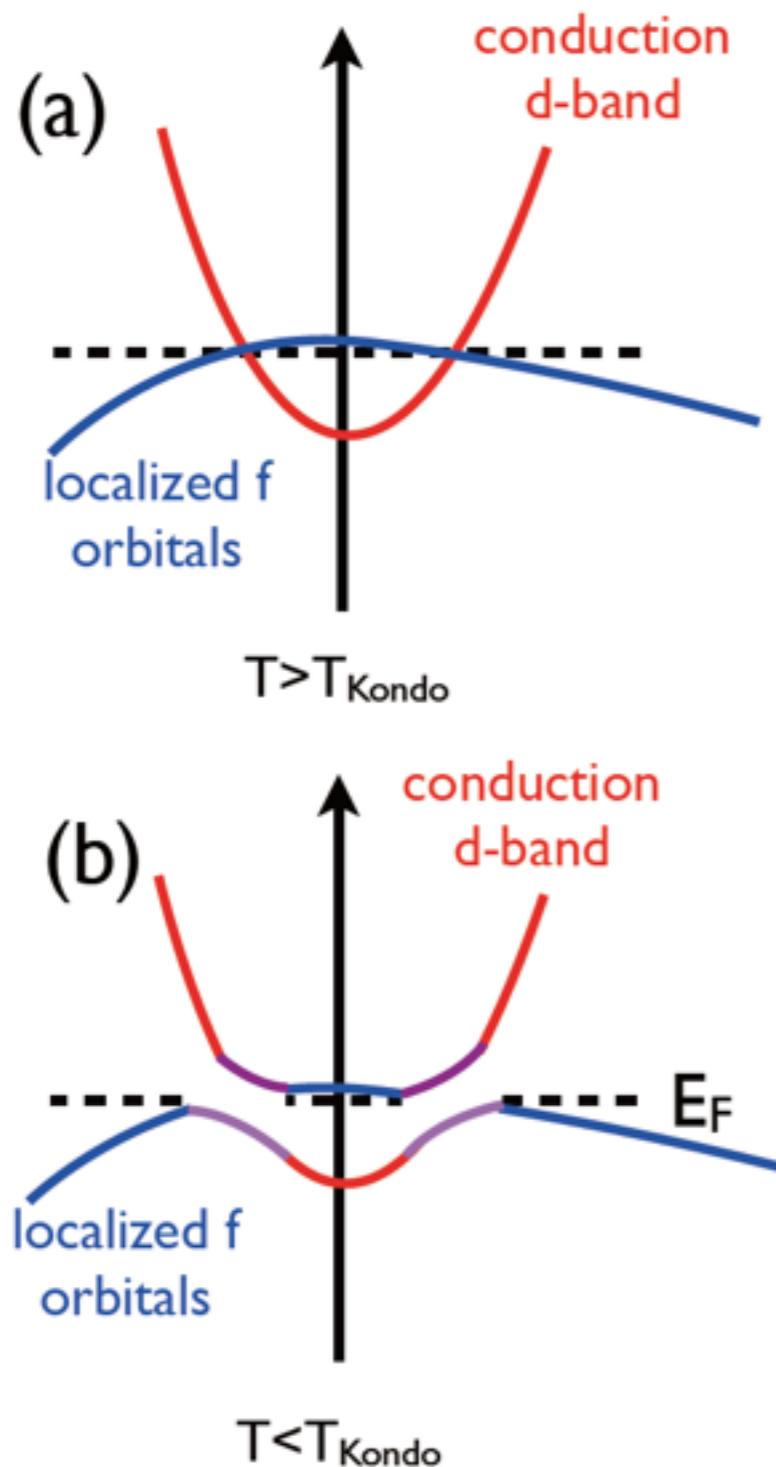
Weak e-e correlation



Kondo Insulator



Kondo Insulator

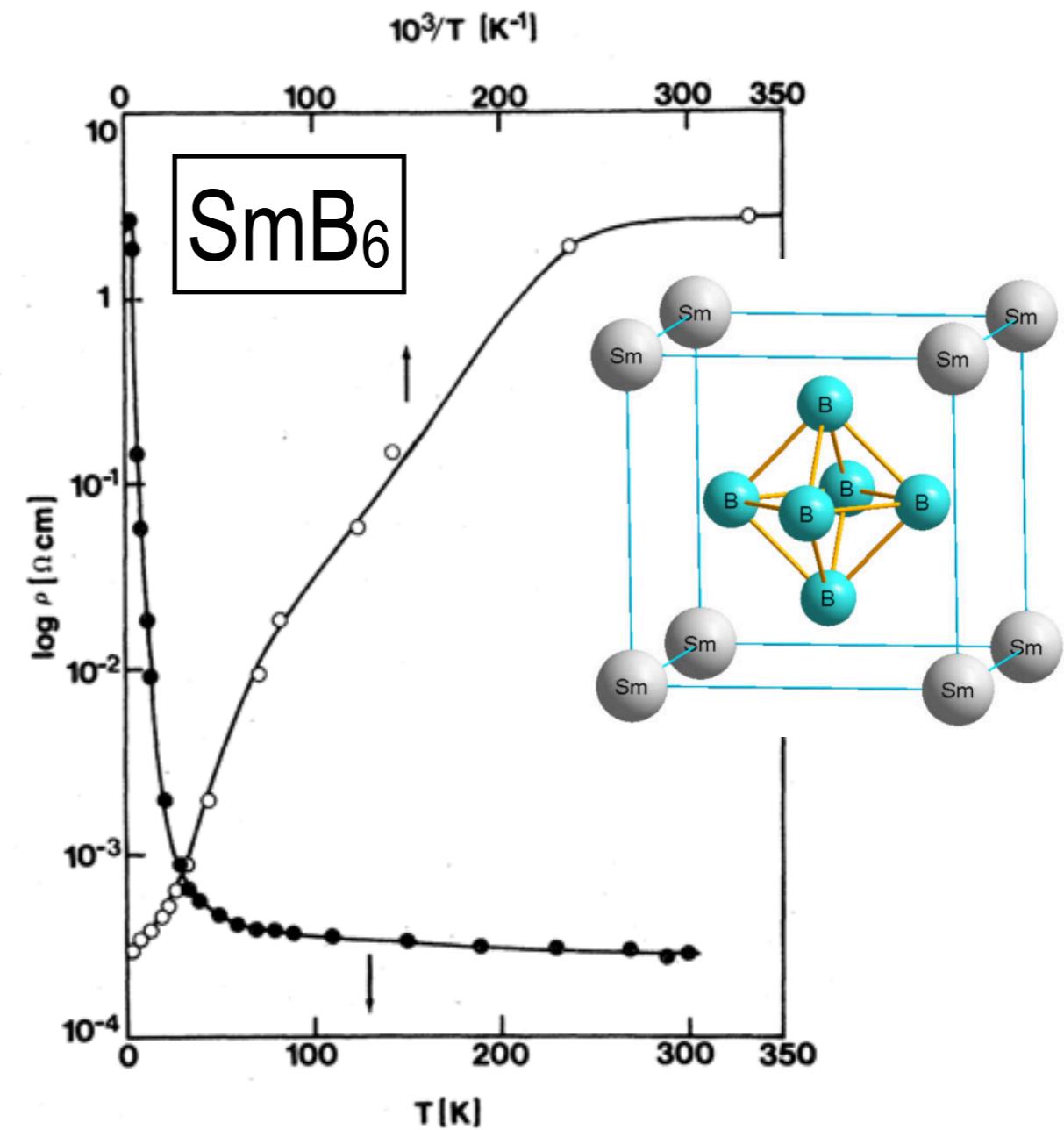
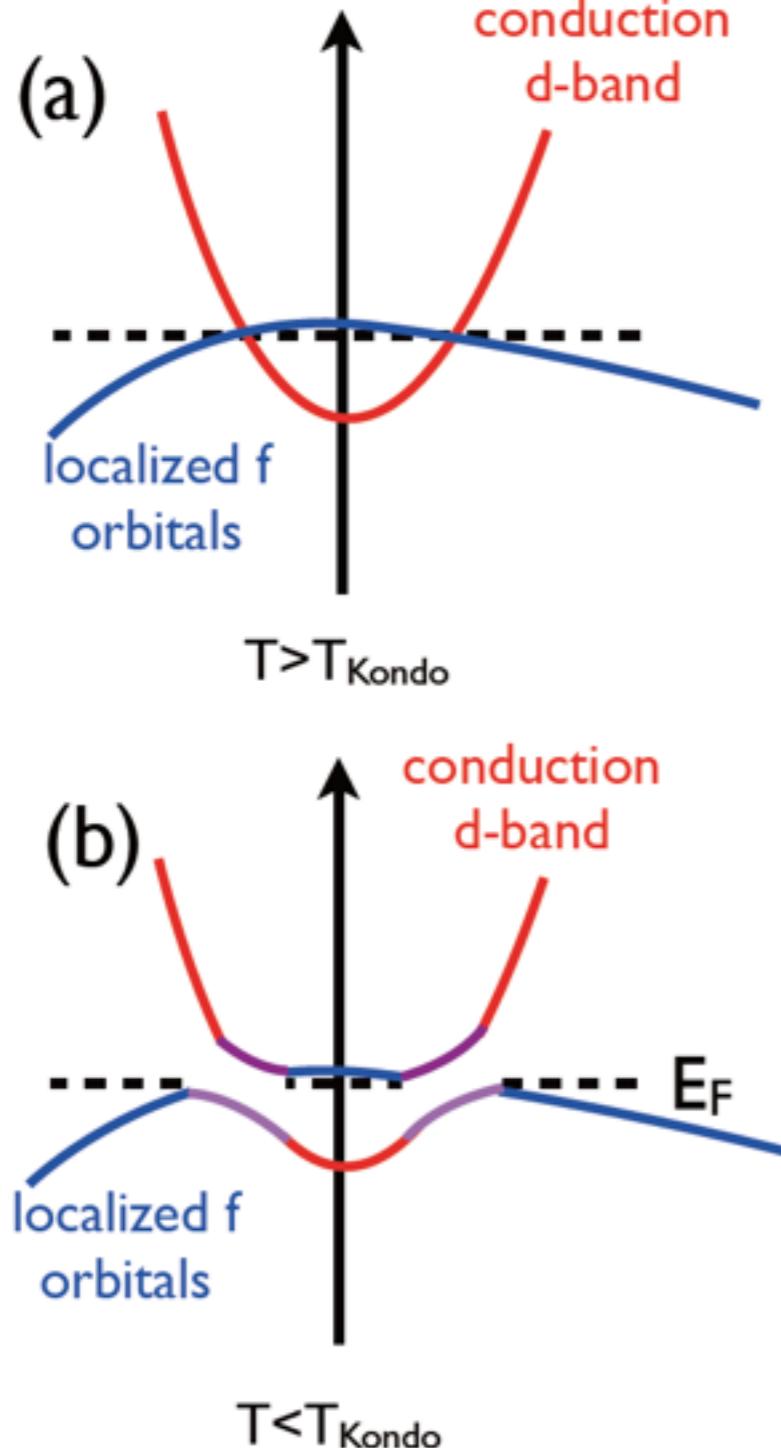


J. W. Allen, B. Batlogg, and P. Wachter, Phys. Rev. B. **20**, 4807 (1979).

Topological Kondo Insulator

M. Dzero, K. Sun, V. Galitski, and P. Coleman, Phys. Rev. Lett. **104**, 106408 (2010).
M. Dzero, K. Sun, P. Coleman and V. Galitski, Phys. Rev. B **85**, 045130 (2012).

Band-inversion naturally exists

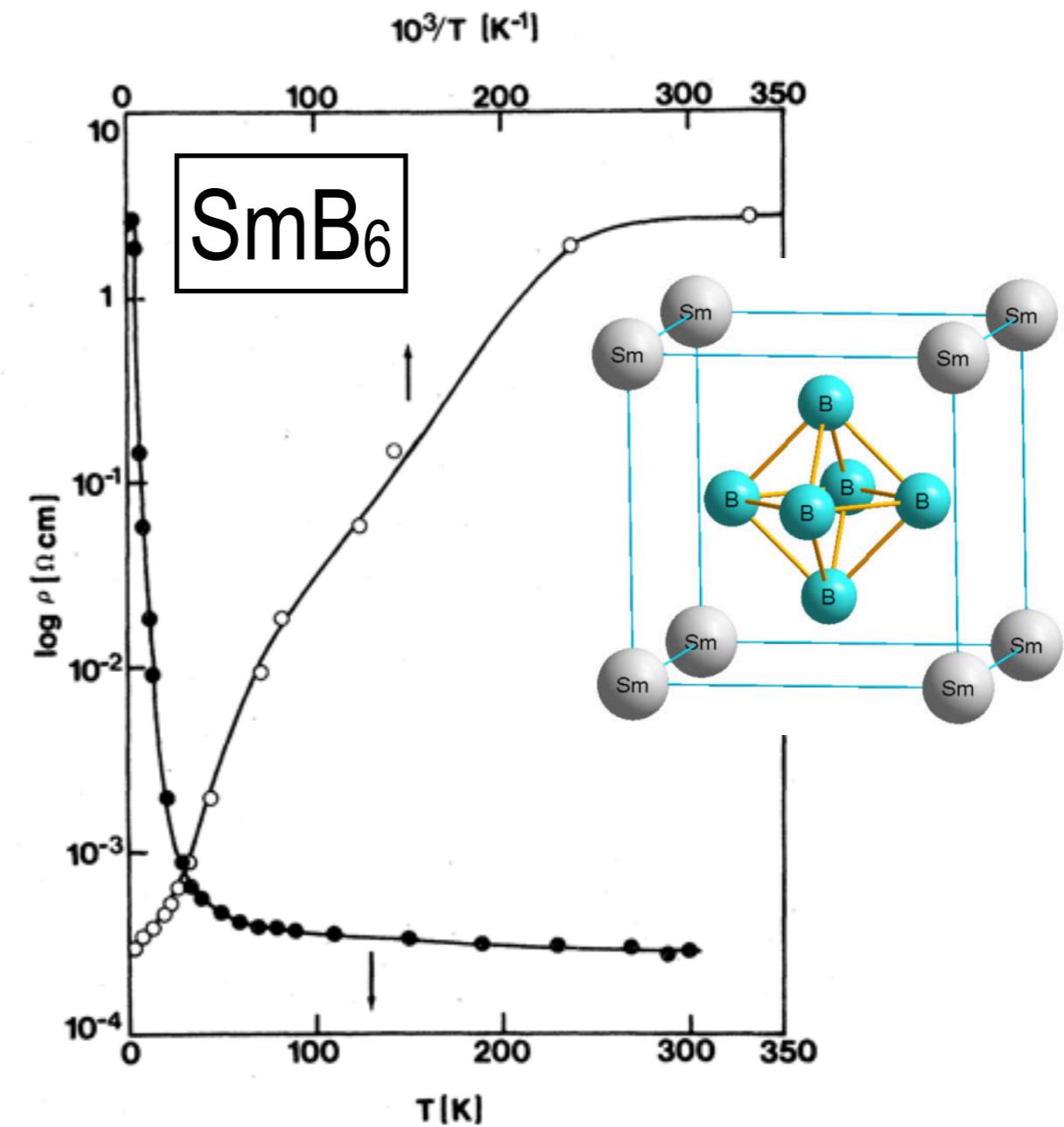
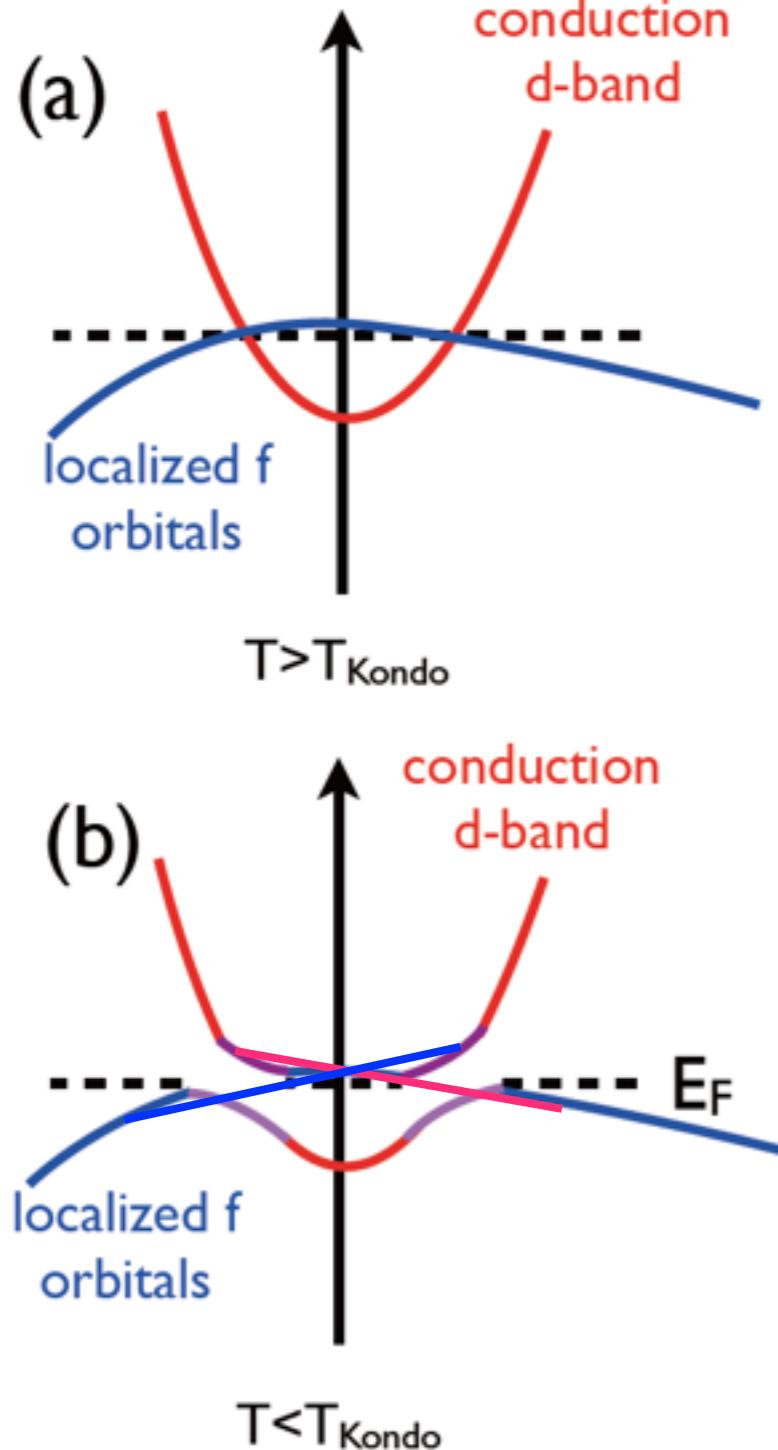


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Topological Kondo Insulator

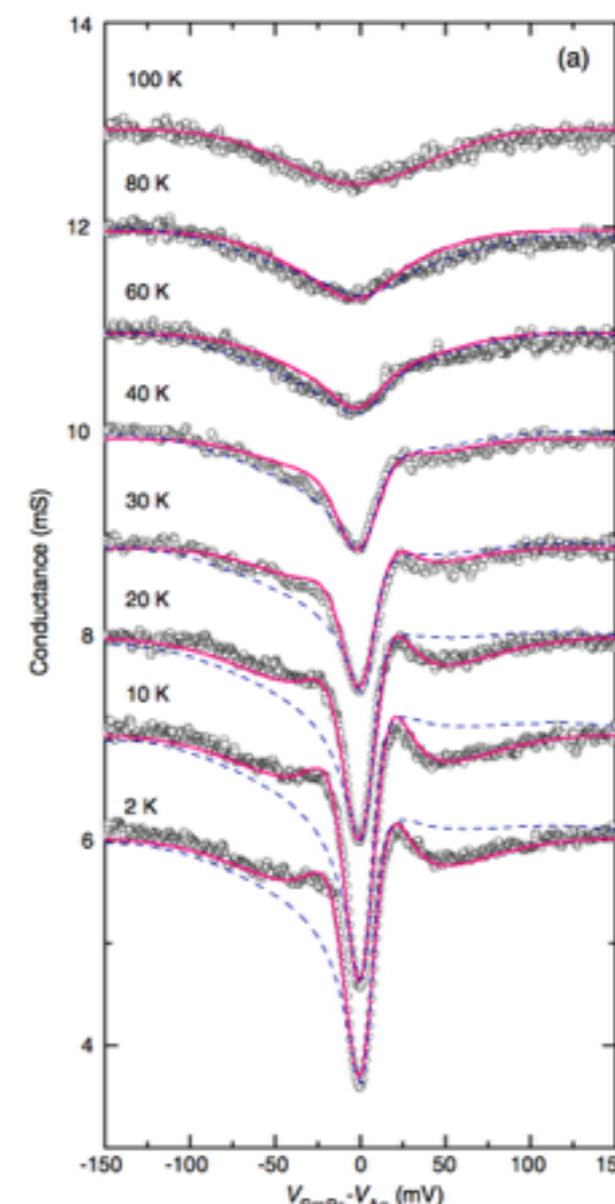
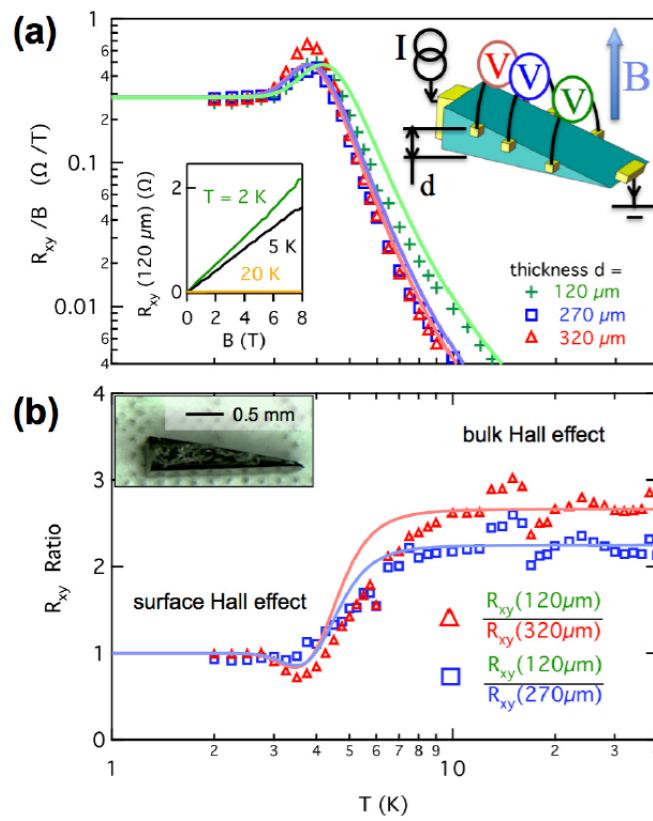
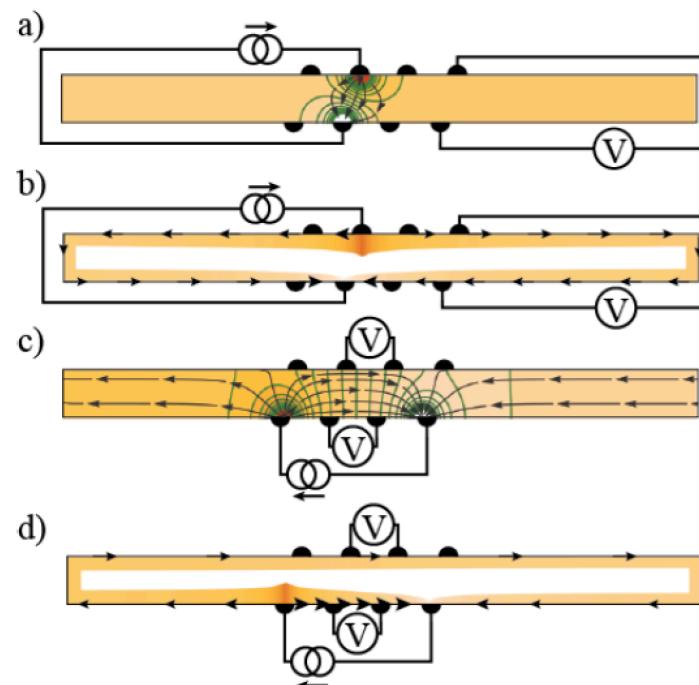
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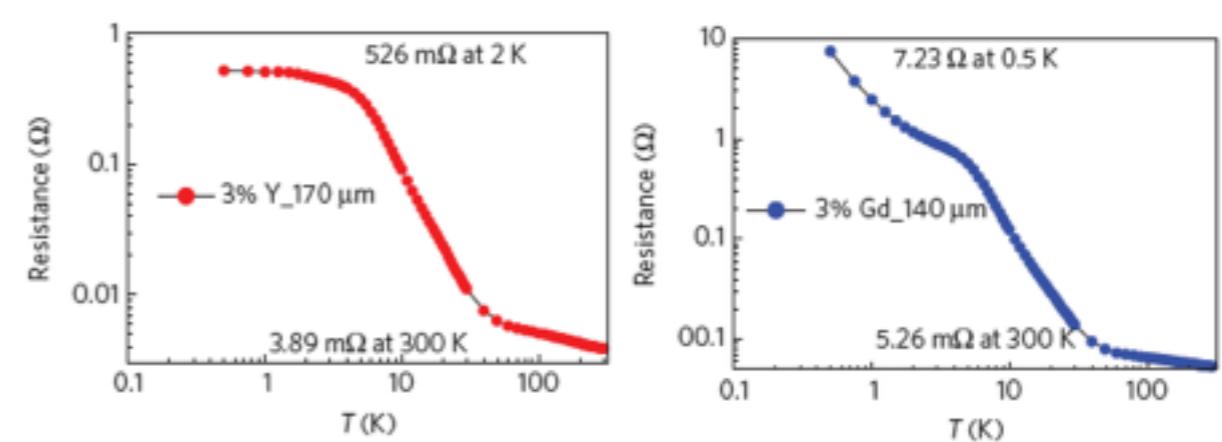
J. W. Allen, B. Batlogg, and P. Wachter, Phys. Rev. B. **20**, 4807 (1979).

Transport evidence of Robust SS

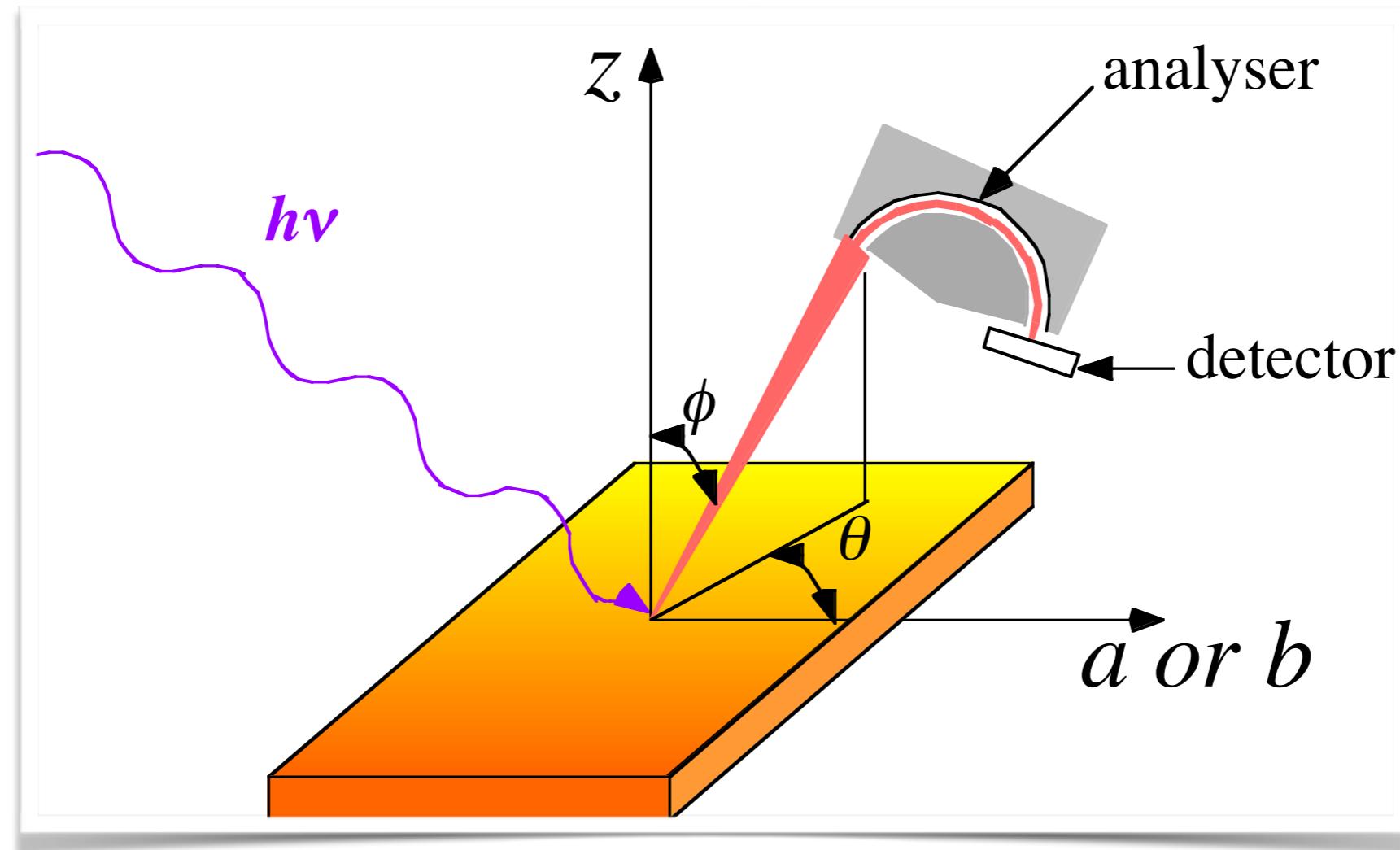


X. H. Zhang et al., Phys. Rev. X 3, 011011 (2013).
 J. Botimer et al., arXiv, 1211.6769 (2012).
 S. Wolgast et al., Phys. Rev. B 88, 180405 (2013).
 D. Kim et al., Scientific Reports 3, 3150 (2013).
 D. Kim, J. Xia and Z. Fisk, Nat. Mater. 13, 466 (2014)
 Thomas et al., arXiv.org (2013), 1307.4133.
 G. Li et al., Science 346, 1208 (2014)
 F. Chen et al. arXiv.org (2013), 1309.2378.
 Z.-J. Yue et al., arXiv.org (2013), 1309.3005.

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Angle-Resolved Photo Emission Spectroscopy



Energy conservation

$$E_B = h\nu - E_k - \Phi$$

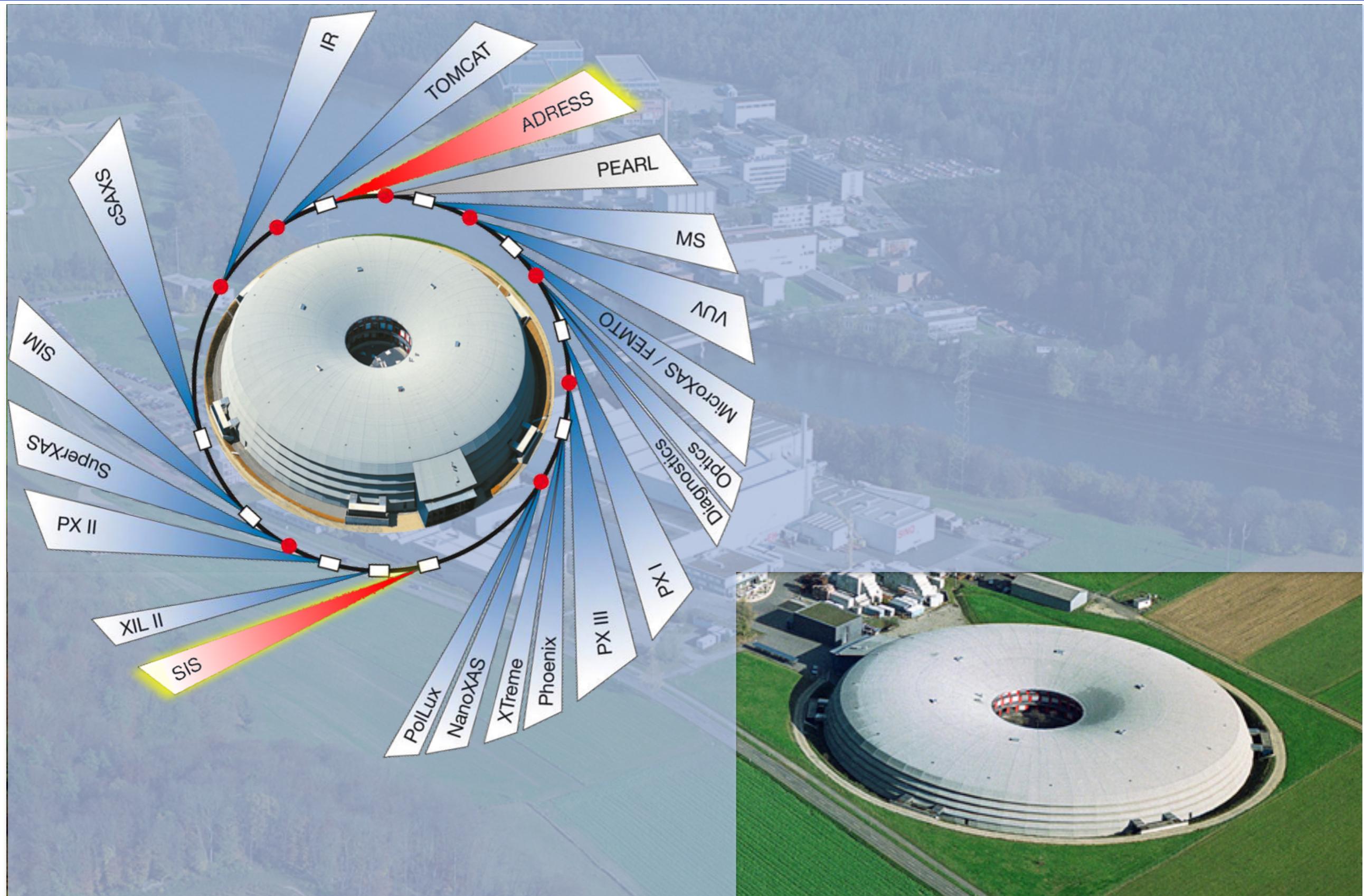
Momentum conservation

$$\mathbf{K}_{\parallel} = \mathbf{k}_{\parallel} + \mathbf{G}_{\parallel}$$

Swiss Light Source, PSI

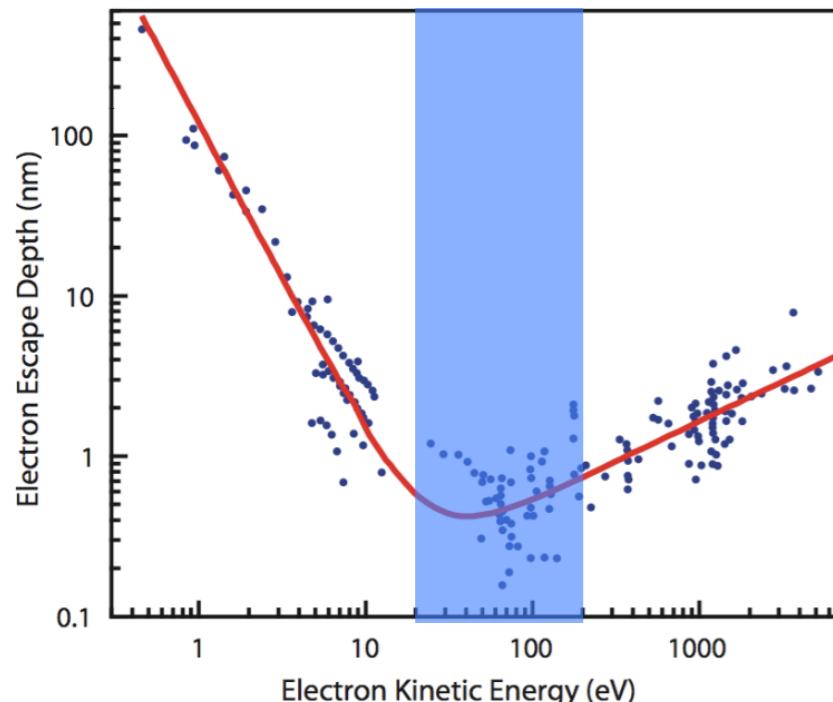


Swiss Light Source, PSI



ARPES @ SLS

From M. P. Seah and W. A. Dench,
Surf. Interf. Anal. 1, 2 (1979).



UV (HR)ARPES @ SIS beamline

Energy range: 10 – 800 eV

(optimized @ 20 – 200 eV)

Flux on sample: 2×10^{15} ph/s

0.1%BW @ 20 eV

Foot print: $50 \times 100 \mu\text{m}^2$

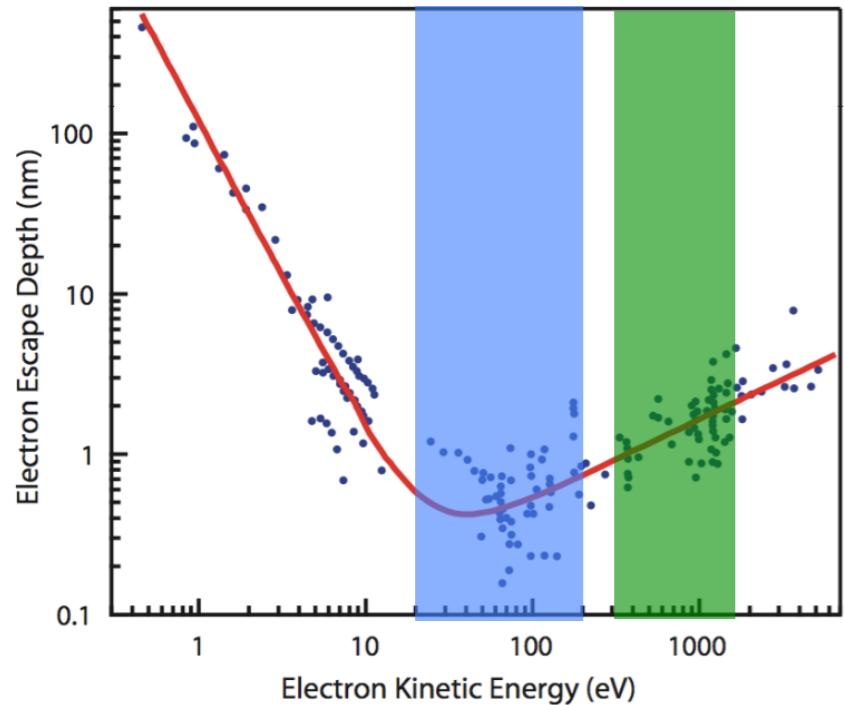
Resolution: < 5 meV @ 20 eV

Analyzer: VG-SCIENTA R4000



ARPES @ SLS

From M. P. Seah and W. A. Dench,
Surf. Interf. Anal. 1, 2 (1979).



UV (HR)ARPES @ SIS beamline

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Flux on sample: 2×10^{15} ph/s

0.1%BW @ 20 eV

Foot print: $50 \times 100 \mu\text{m}^2$

Resolution: < 5 meV @ 20 eV

Analyzer: VG-SCIENTA R4000



Soft-X-ray ARPES @ ADRESS beamline

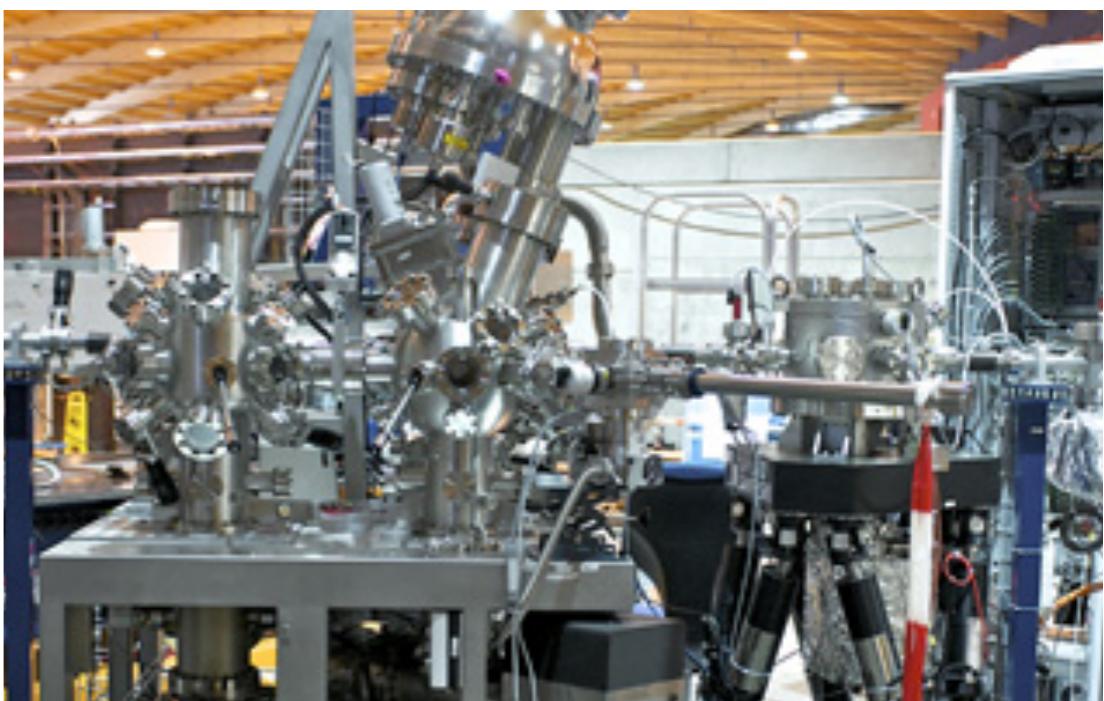
Energy range: 300 – 1600 eV

Flux on sample: 10^{13} ph/s/0.01%BW @ 1keV

Spot size: $30 \times 70 \mu\text{m}^2$

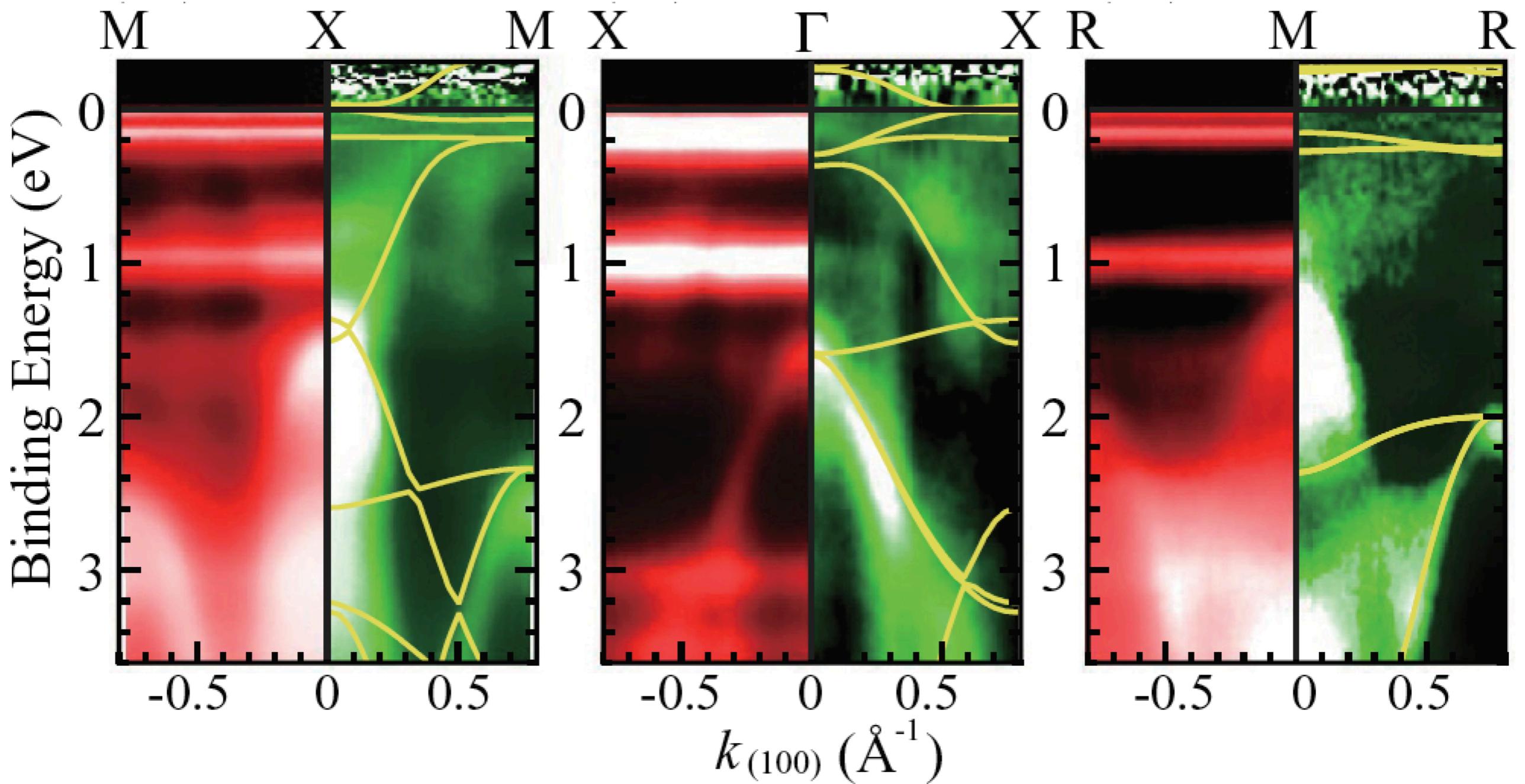
Resolution: 60 meV @ 1 keV (25~30 meV below 600 eV)

Analyzer: PHOIBIOS-150



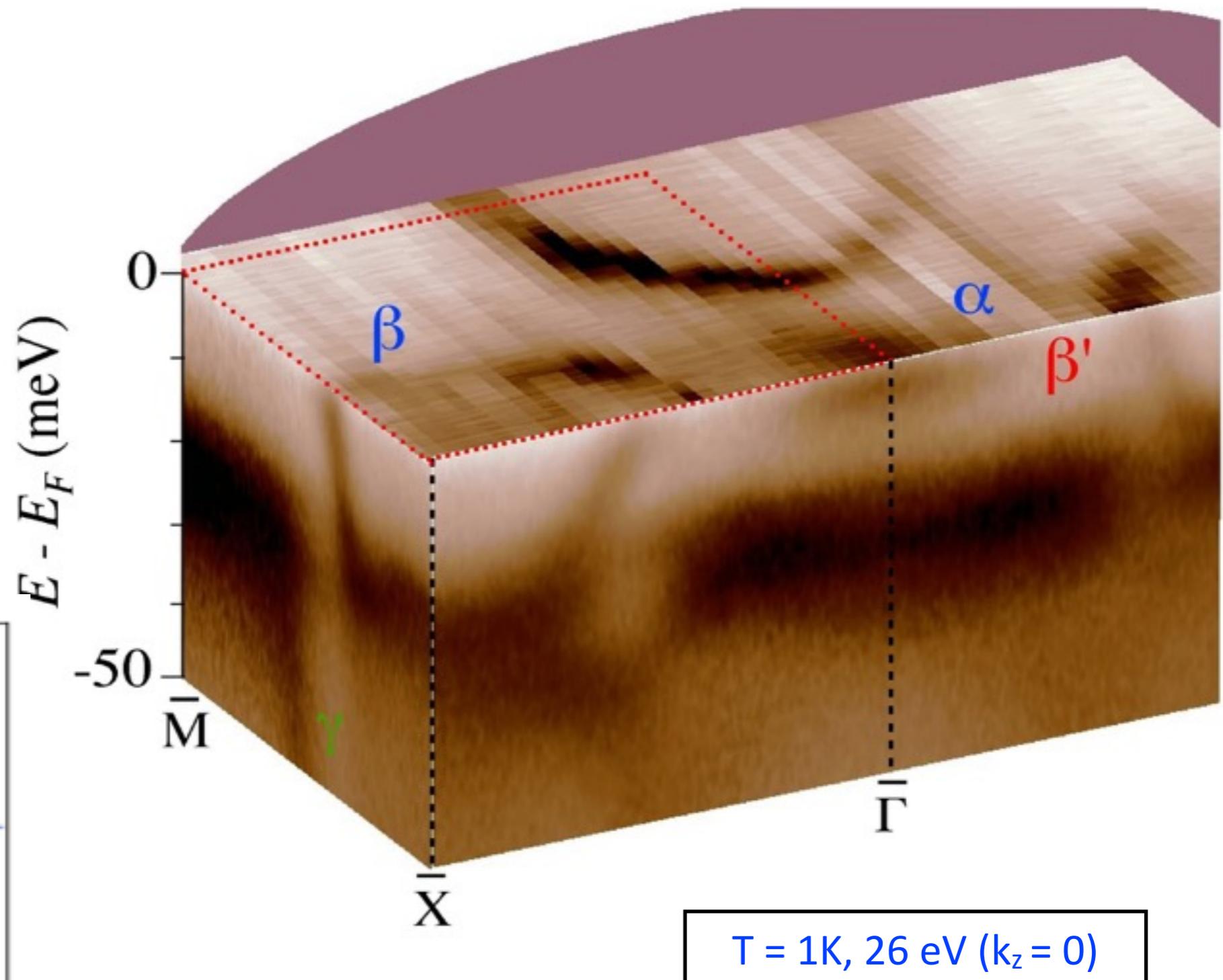
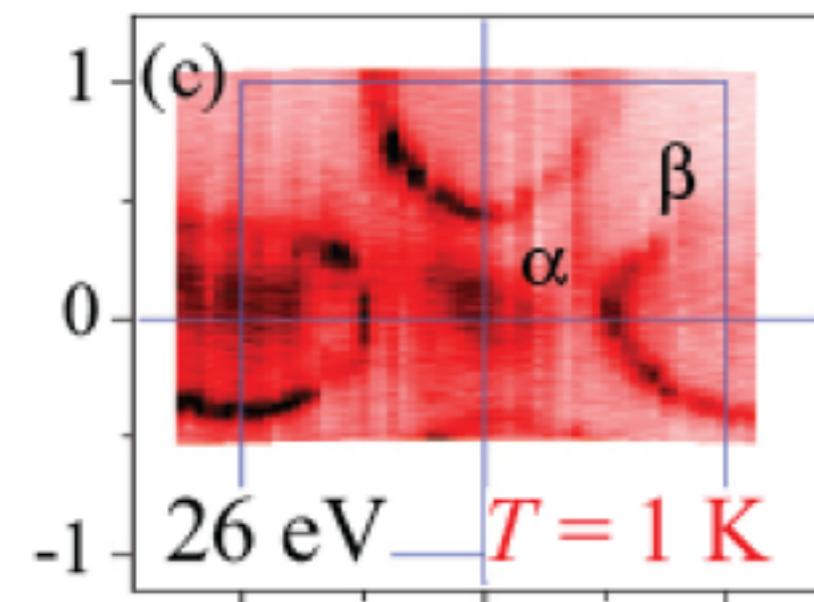
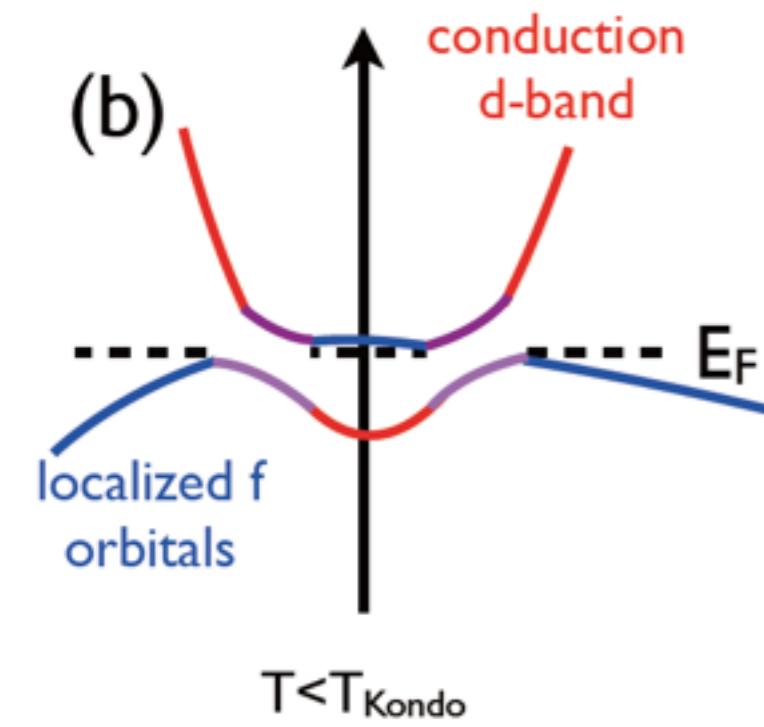
Previous ARPES result on SmB₆

Previous ARPES result on SmB₆

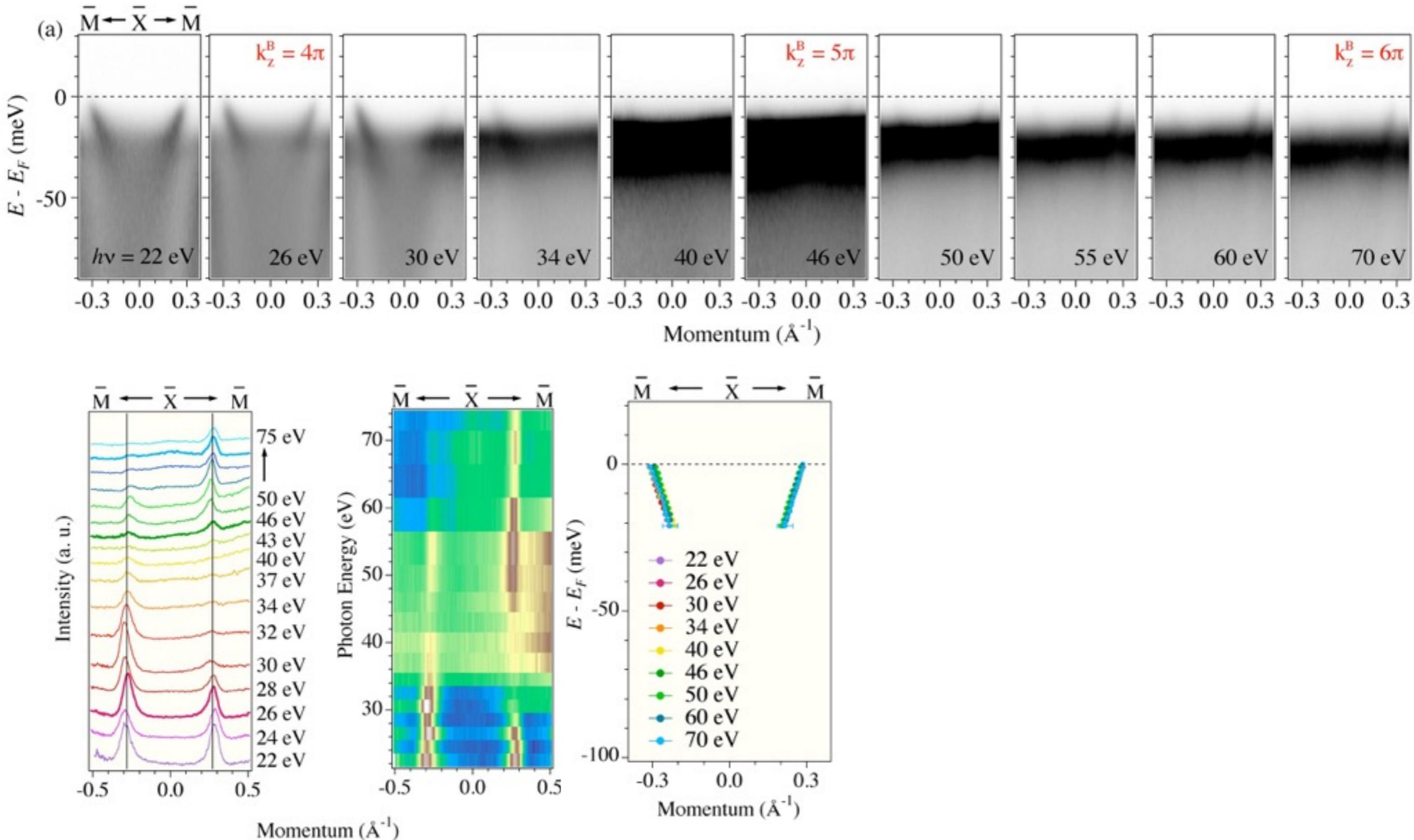


H. Miyazaki *et al.*, Phys. Rev. B 86, 075105 (2012).
J. D. Denlinger *et al.*, Physica B 281-282, 716 (2000).

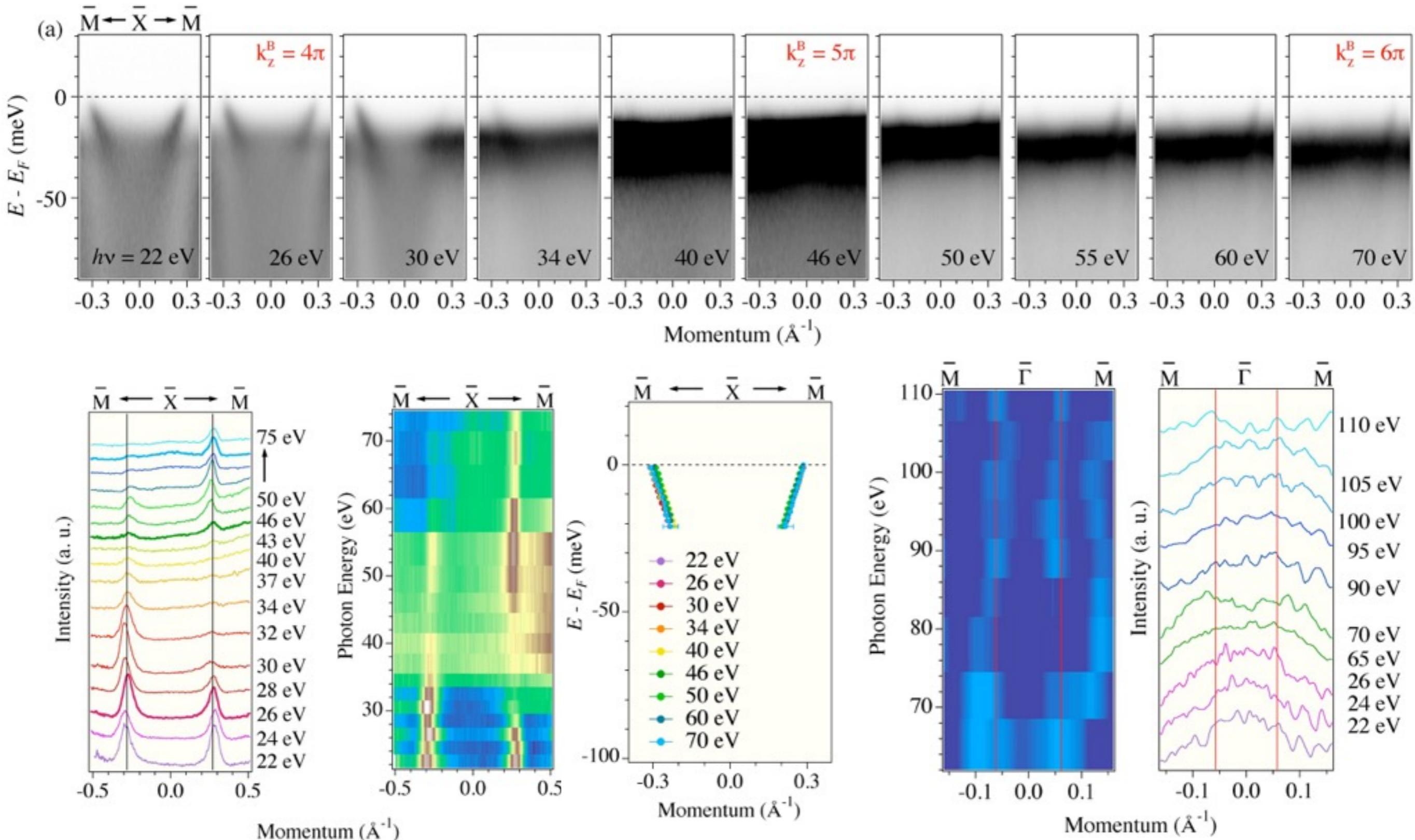
In gap states



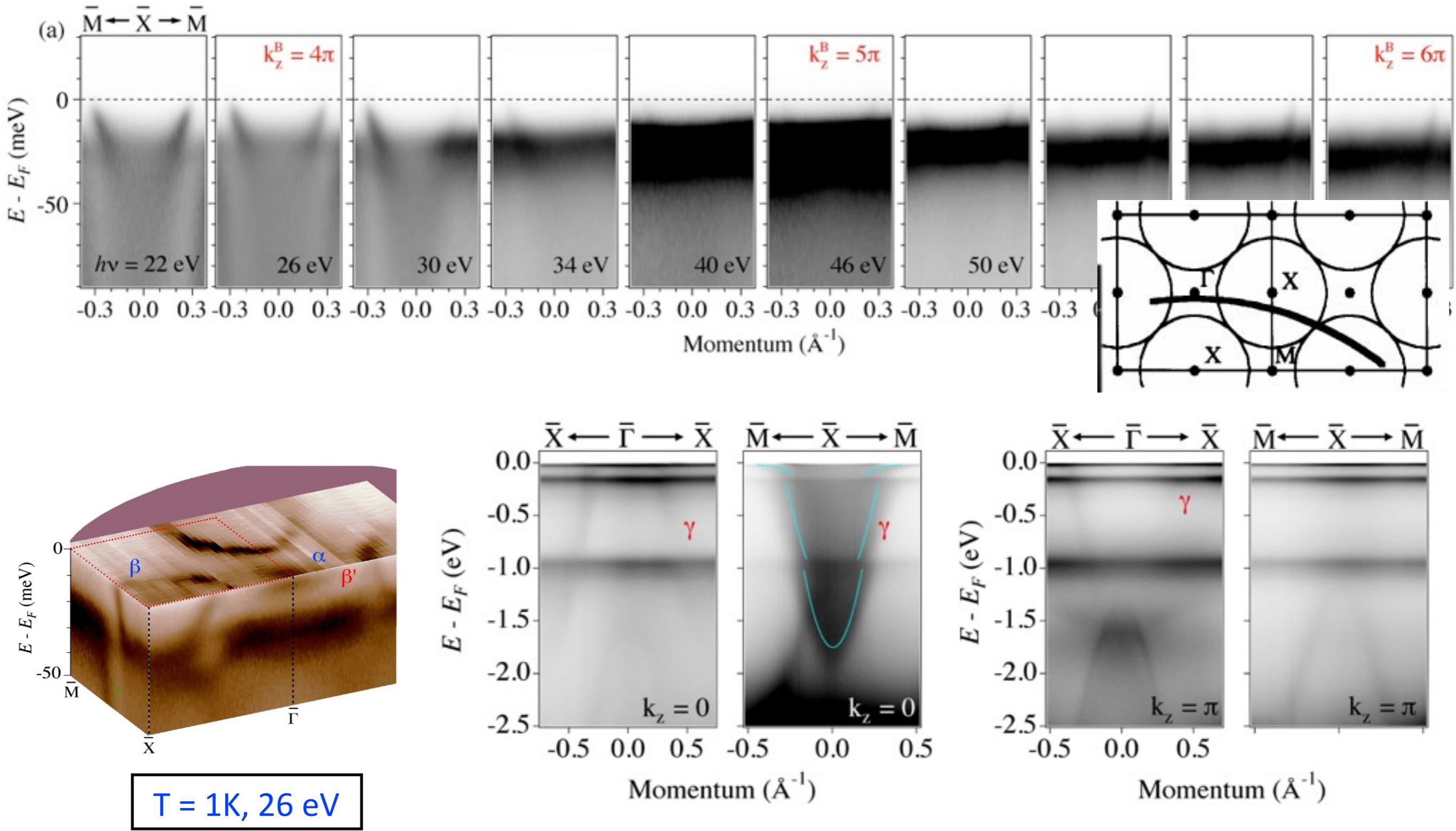
Photon Energy dependence



Photon Energy dependence



Photon Energy dependence

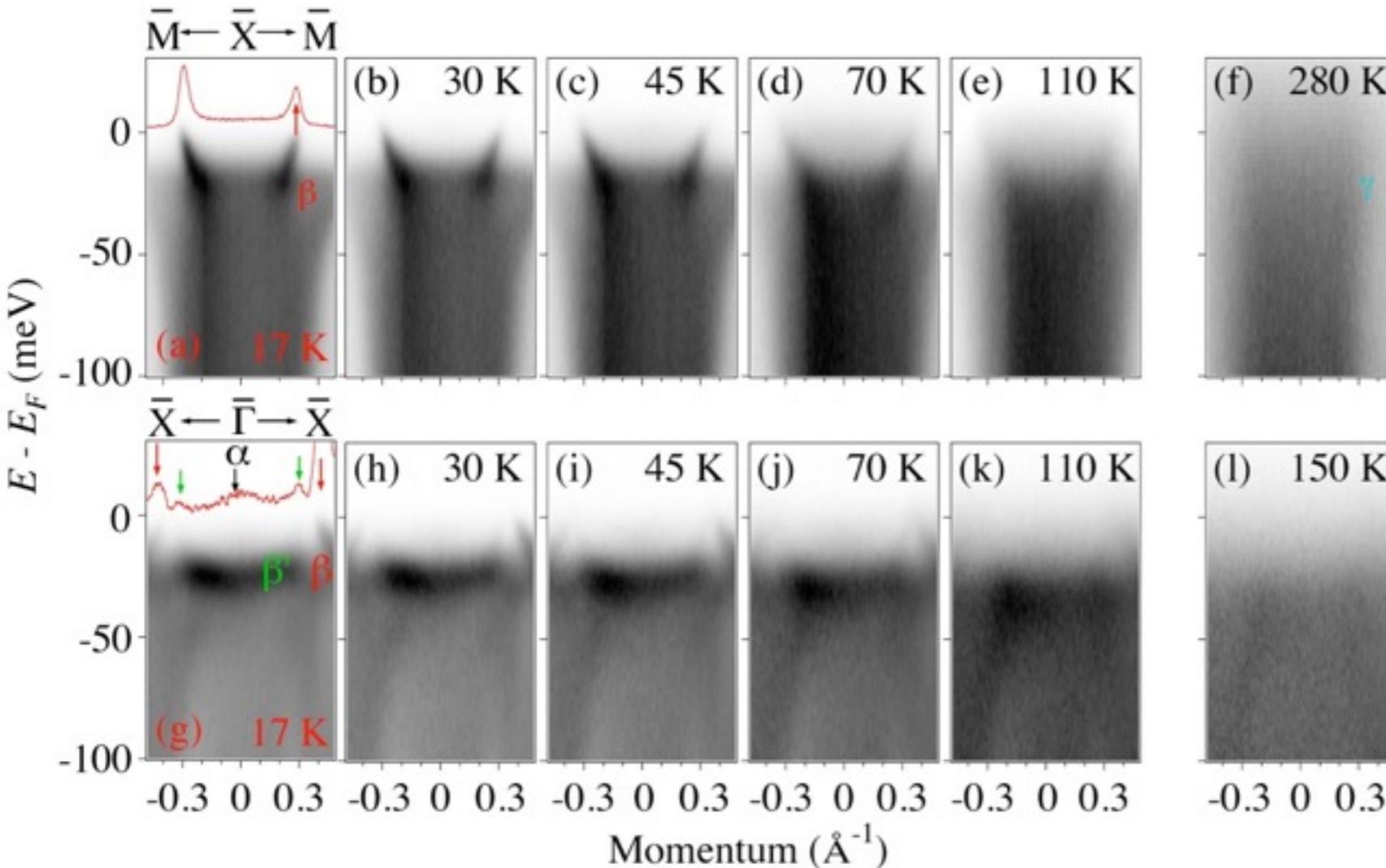


Temperature Dependence

N. Xu *et al.*, Phy. Rev. B 88, 121102(R) (2013)

J. D. Denlinger, J. W. Allen *et al.*,
arXiv. 1312.6637 (2013).

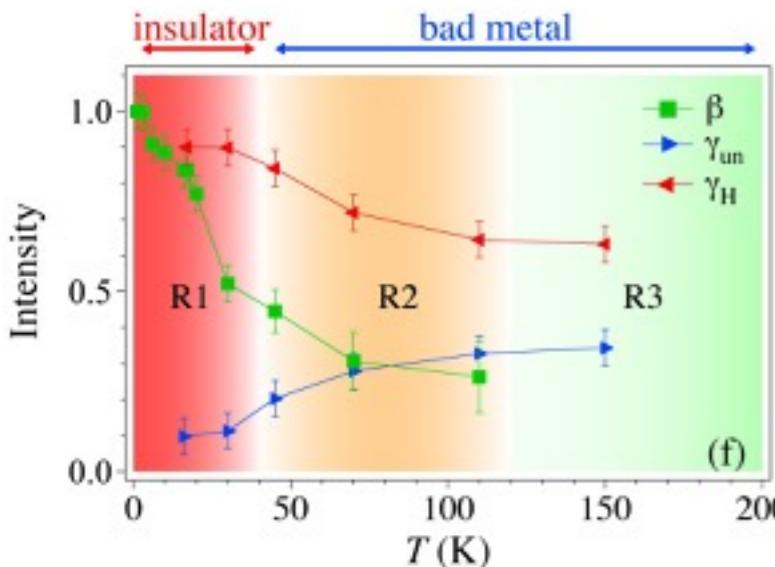
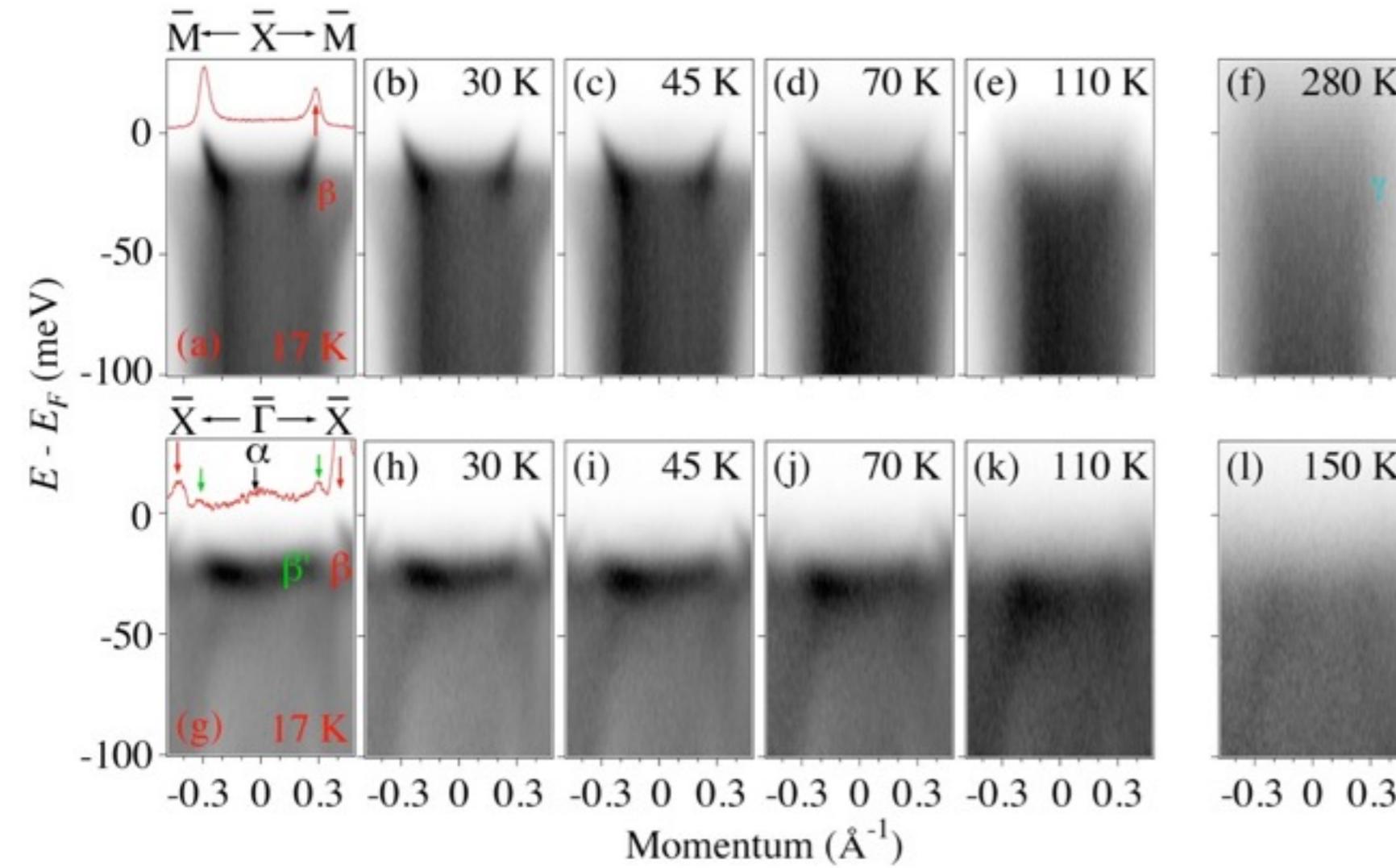
Temperature Dependence



N. Xu *et al.*, Phy. Rev. B 88, 121102(R) (2013)

J. D. Denlinger, J. W. Allen *et al.*,
arXiv. 1312.6637 (2013).

Temperature Dependence

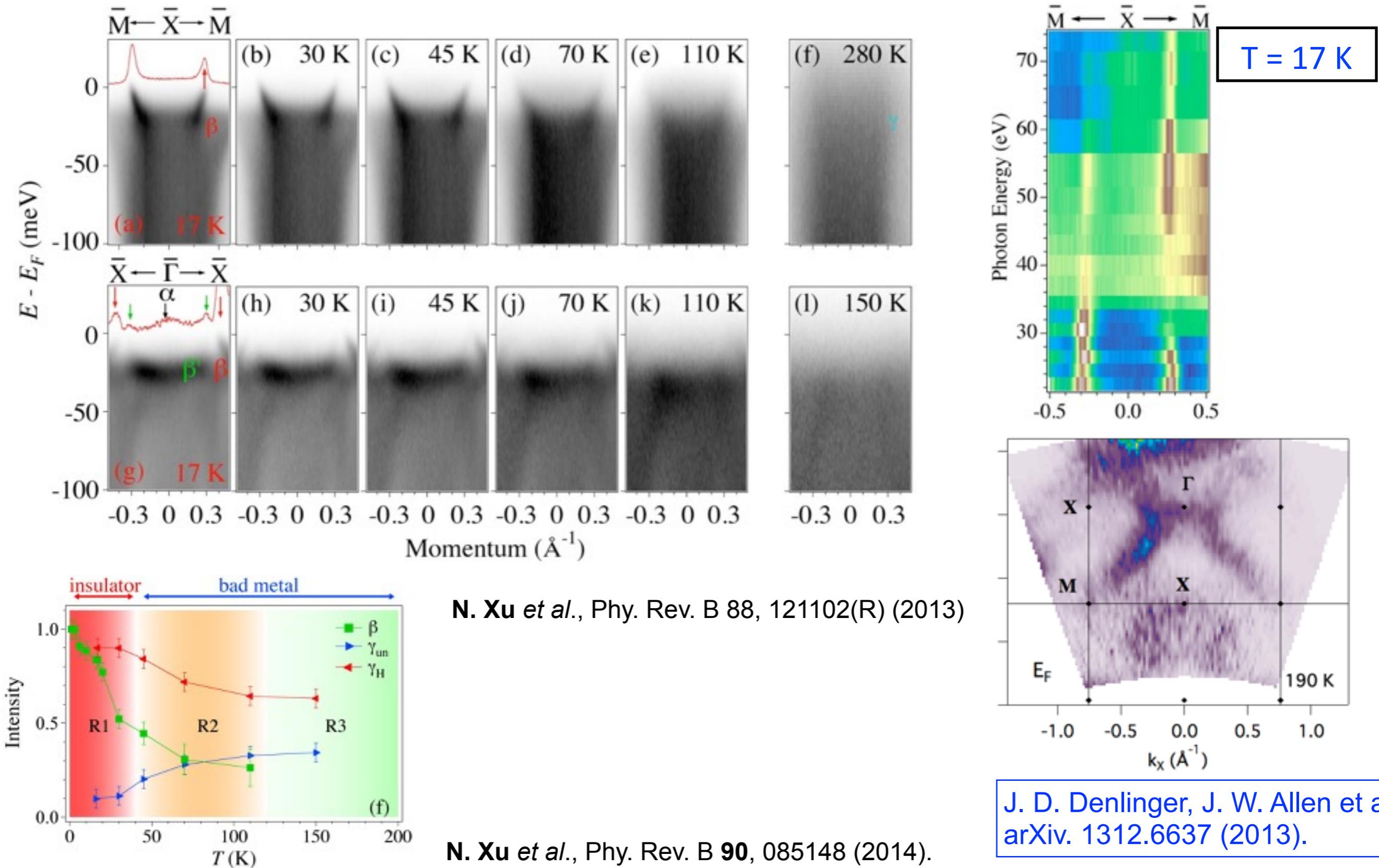


N. Xu *et al.*, Phy. Rev. B 88, 121102(R) (2013)

N. Xu *et al.*, Phy. Rev. B 90, 085148 (2014).

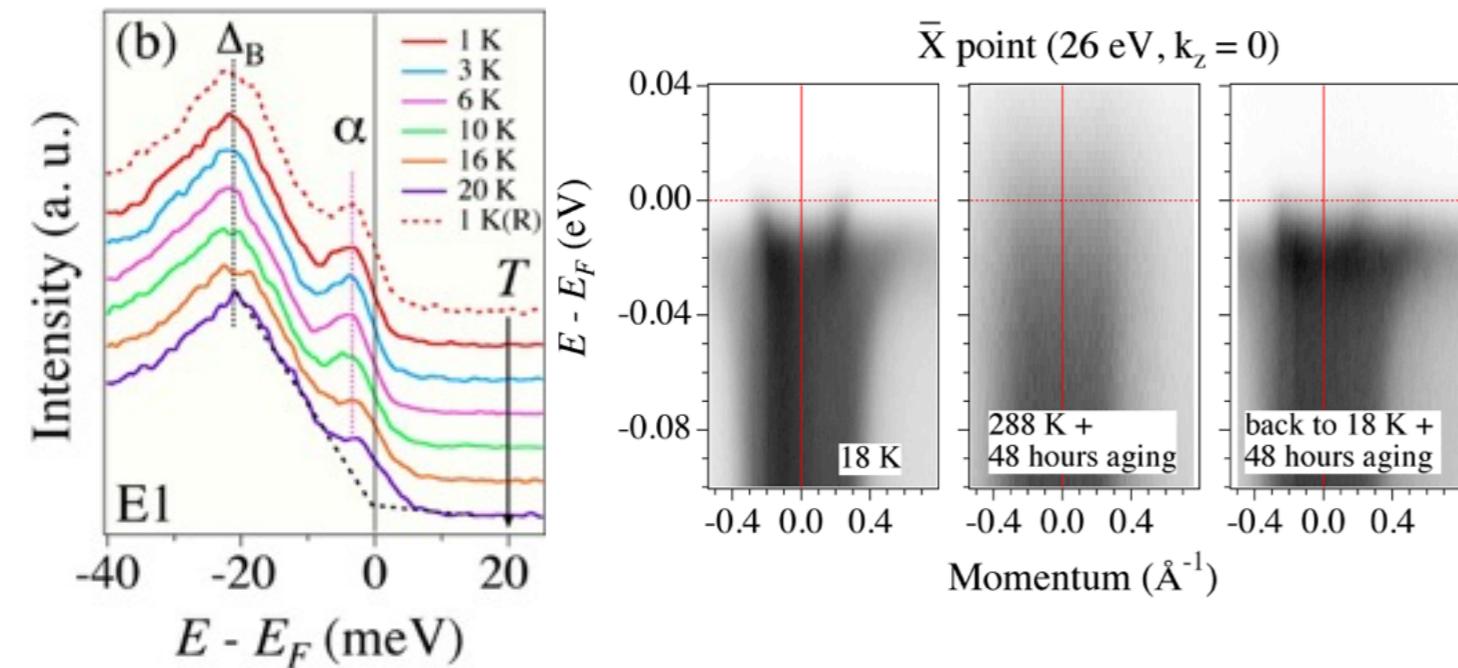
J. D. Denlinger, J. W. Allen *et al.*,
arXiv. 1312.6637 (2013).

Temperature Dependence



Protected SS

Robust from thermo-cycle

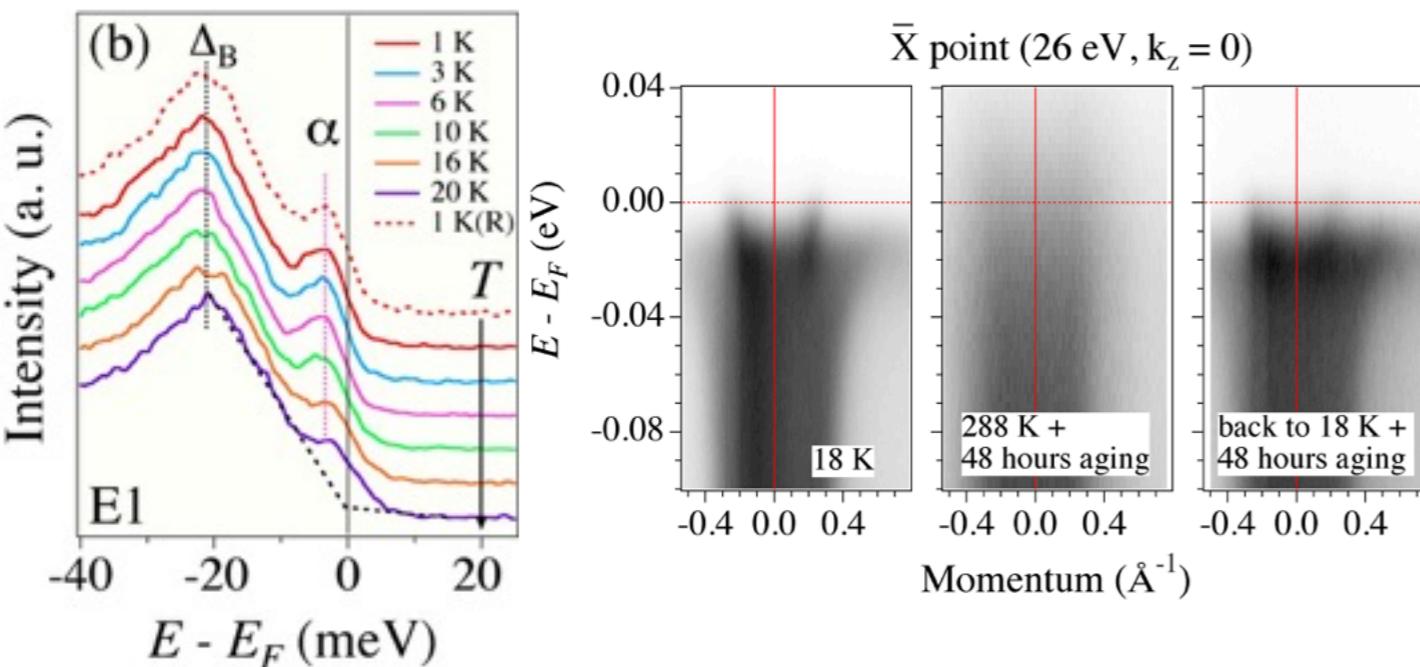


N. Xu *et al.*, Phy. Rev. B **88**, 121102(R) (2013).

Robust from surface conditions

Protected SS

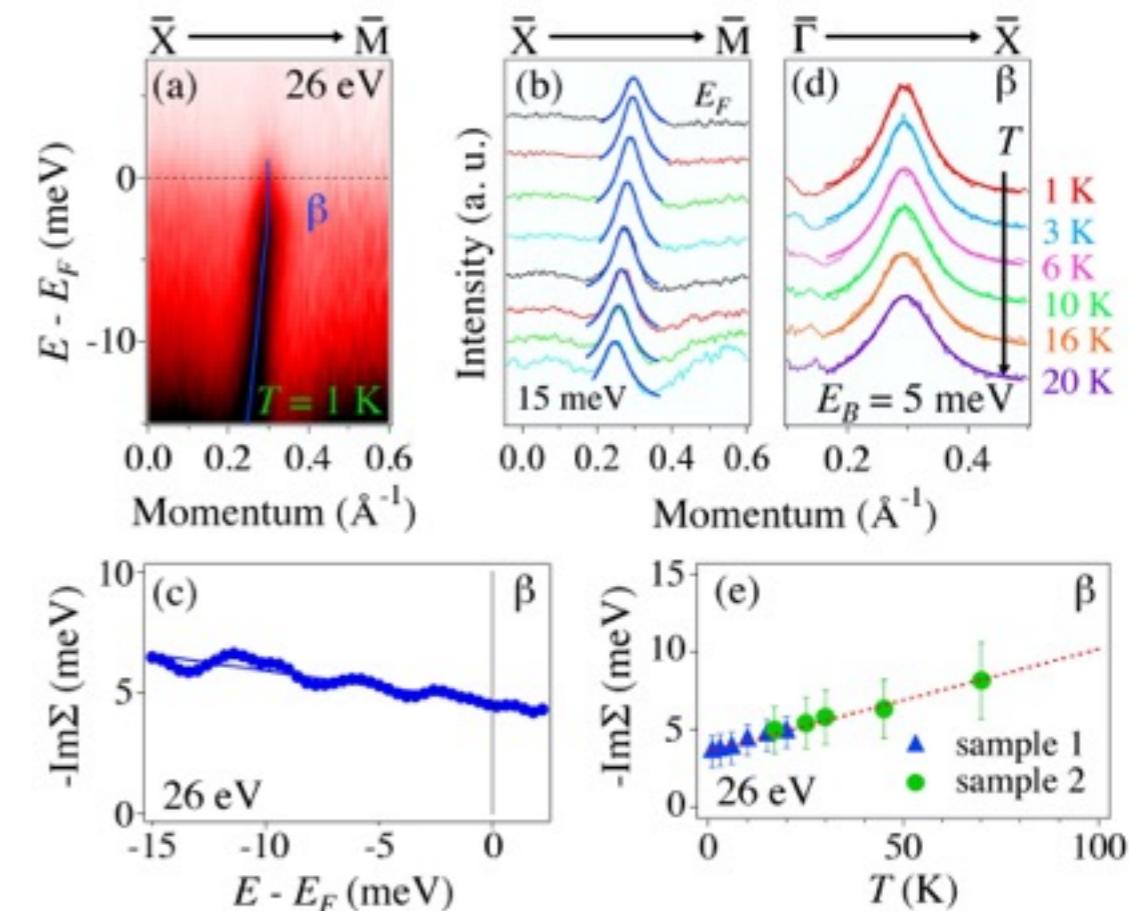
Robust from thermo-cycle



N. Xu et al., Phys. Rev. B **88**, 121102(R) (2013).

Robust from surface conditions

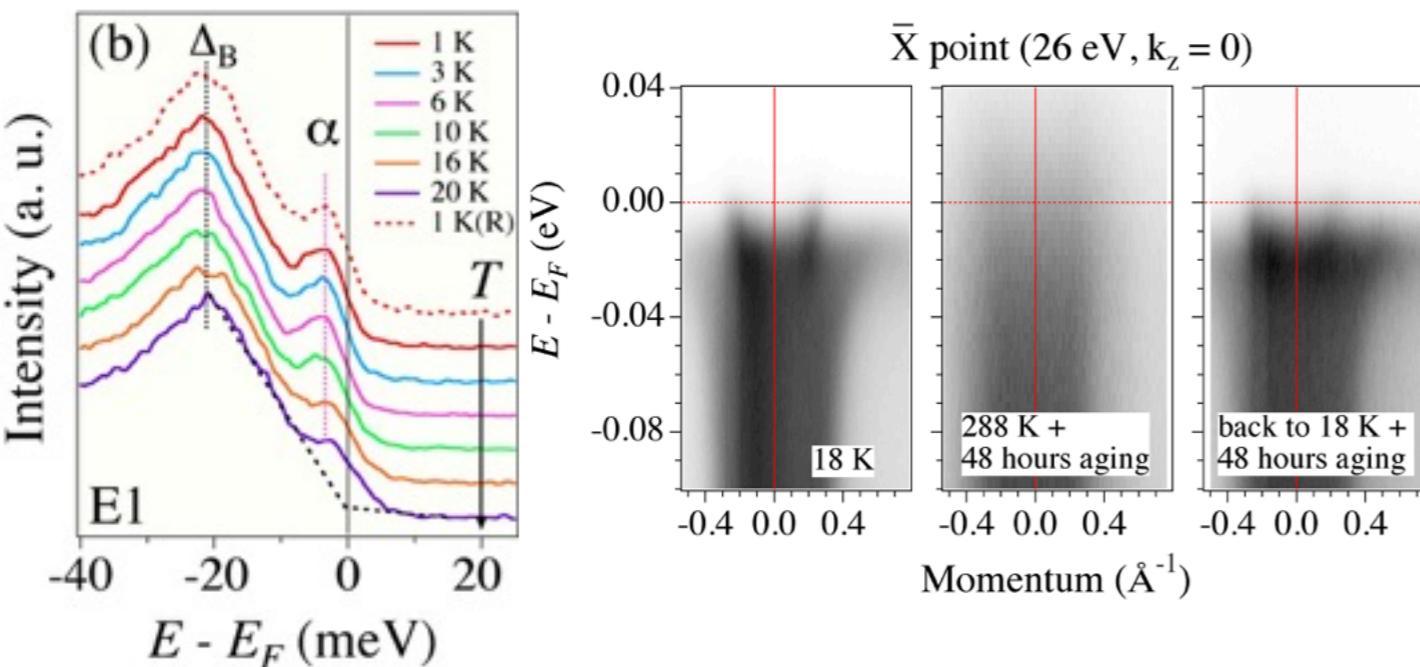
Suppressed scattering rate



N. Xu et al., Phys. Rev. B **90**, 085148 (2014).

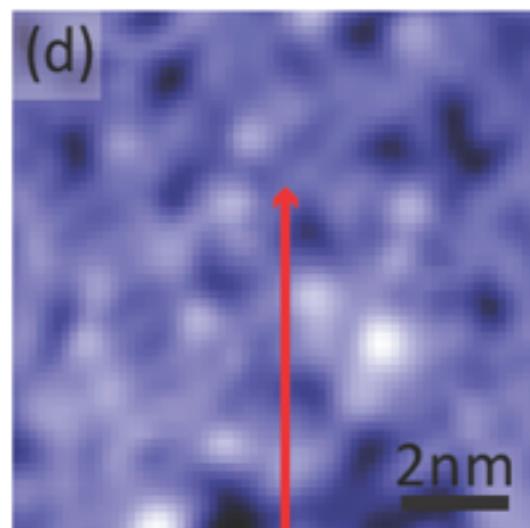
Protected SS

Robust from thermo-cycle



N. Xu et al., Phys. Rev. B **88**, 121102(R) (2013).

Robust from surface conditions

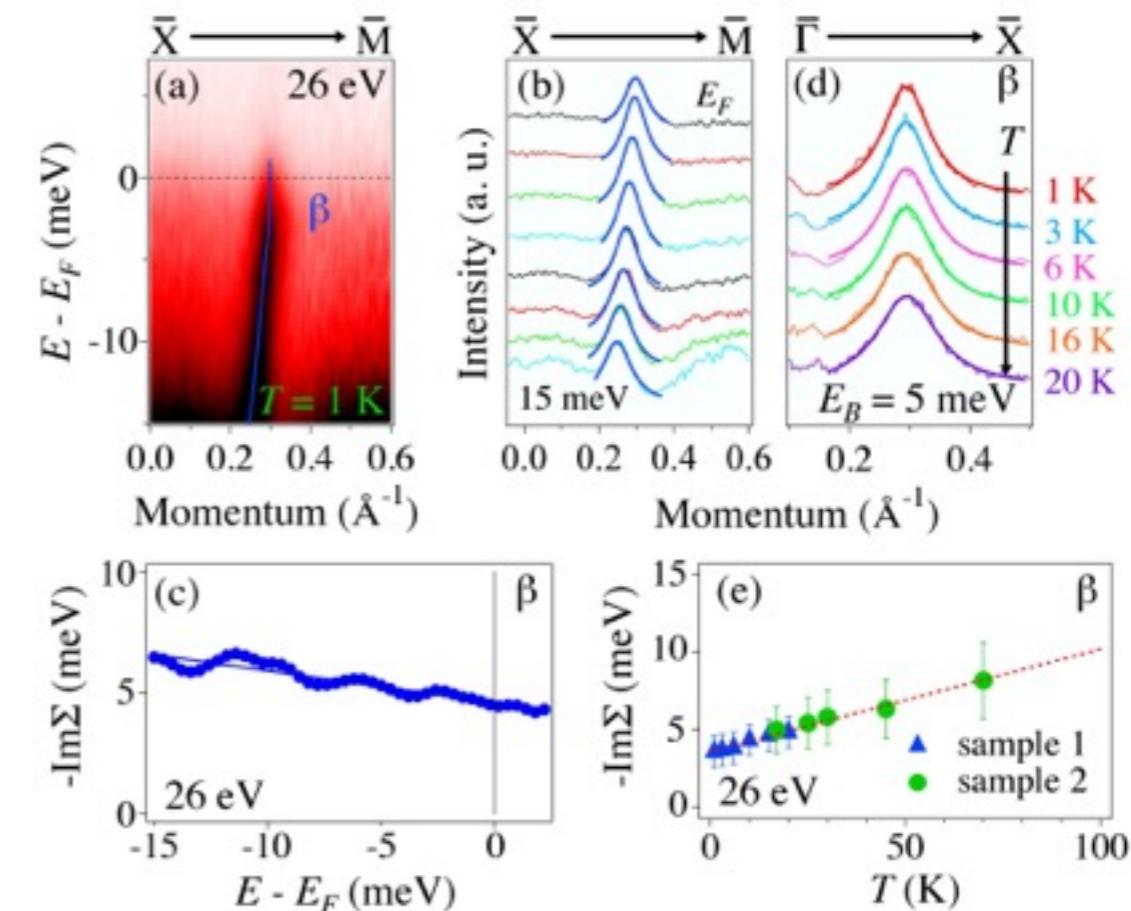


Sahana Rößler et al., PNAS 111, 4798 (2014)

Wei Ruan et al., PRL 112, 136401 (2014)

Michael M. Yee et al., arXiv: 1308.1085 (2013)

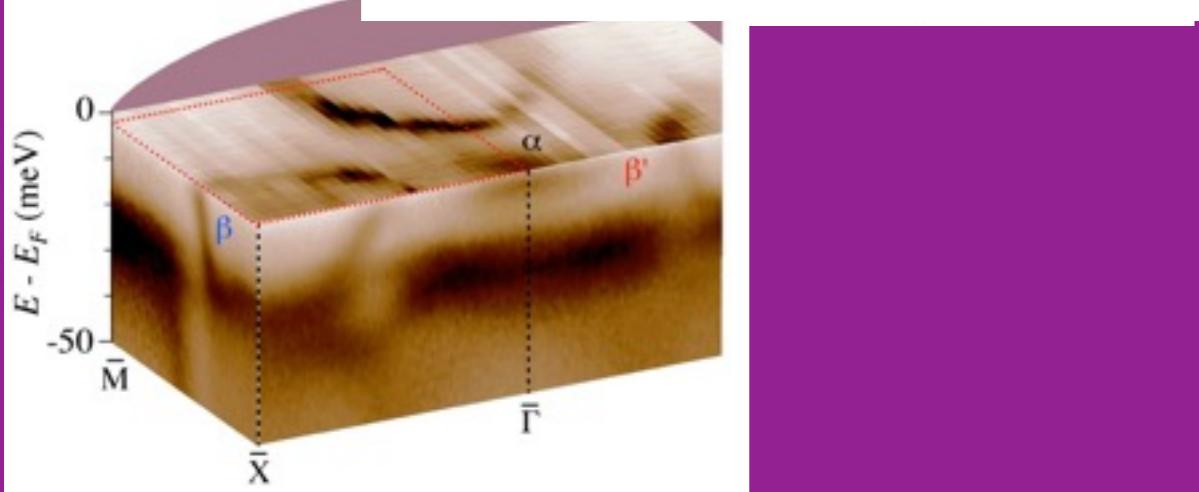
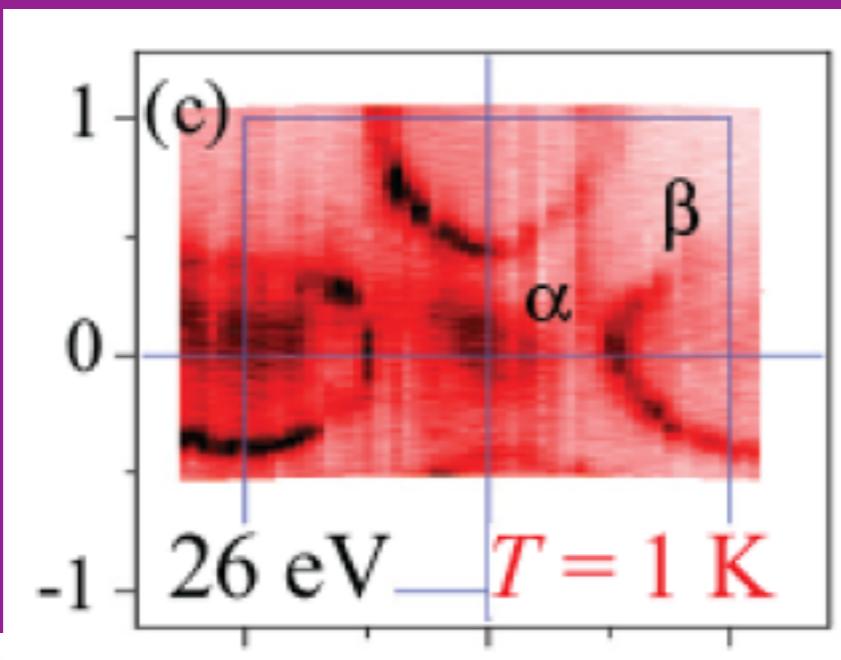
Suppressed scattering rate



N. Xu et al., Phys. Rev. B **90**, 085148 (2014).

Comparison of electronic structure with theory

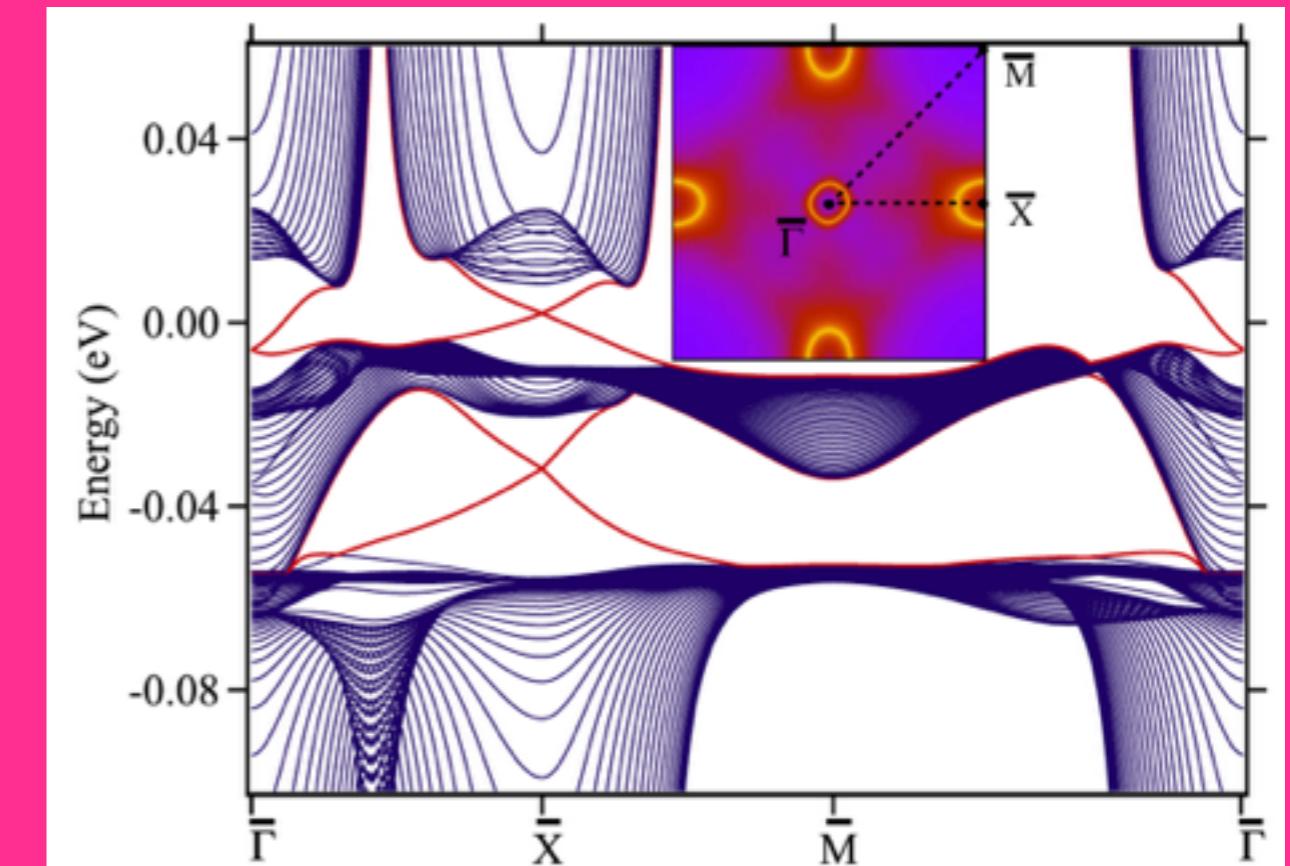
SmB₆



Three SS pockets centered at $\bar{\Gamma}/\bar{X}$ point

N. Xu et al., Phys. Rev. B 88, 121102(R) (2013)

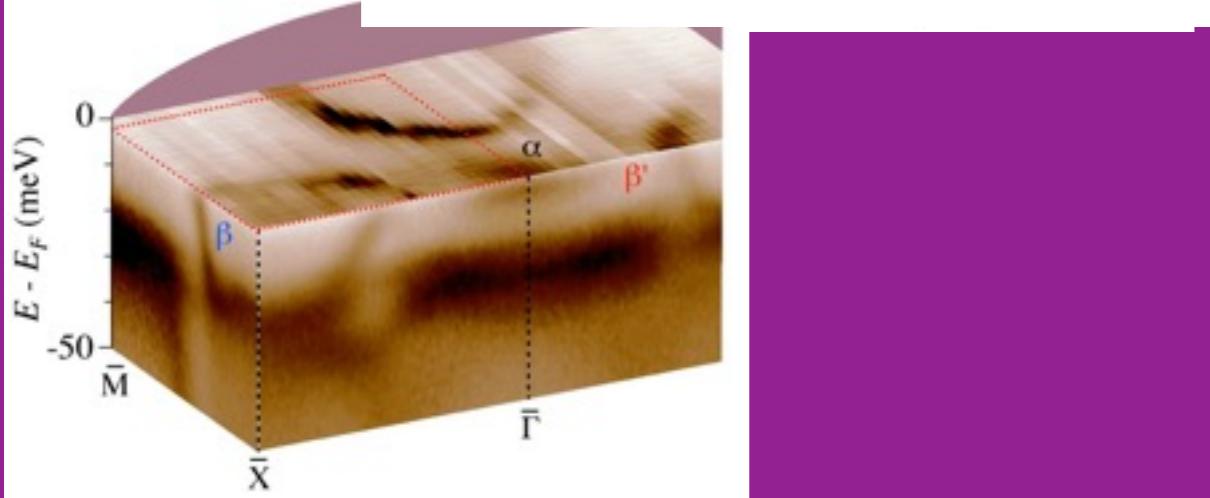
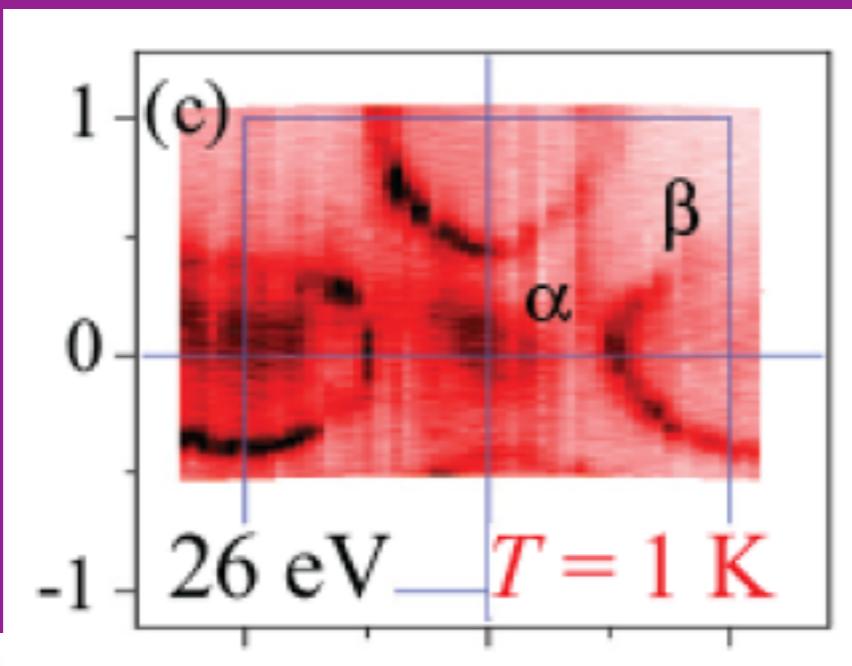
Theoretical prediction of TKI



F. Lu, J. Zhao, H. Weng, X. Dai and Z. Fang,
Phys. Rev. Lett. **110**, 096401 (2013).

Comparison of electronic structure with theory

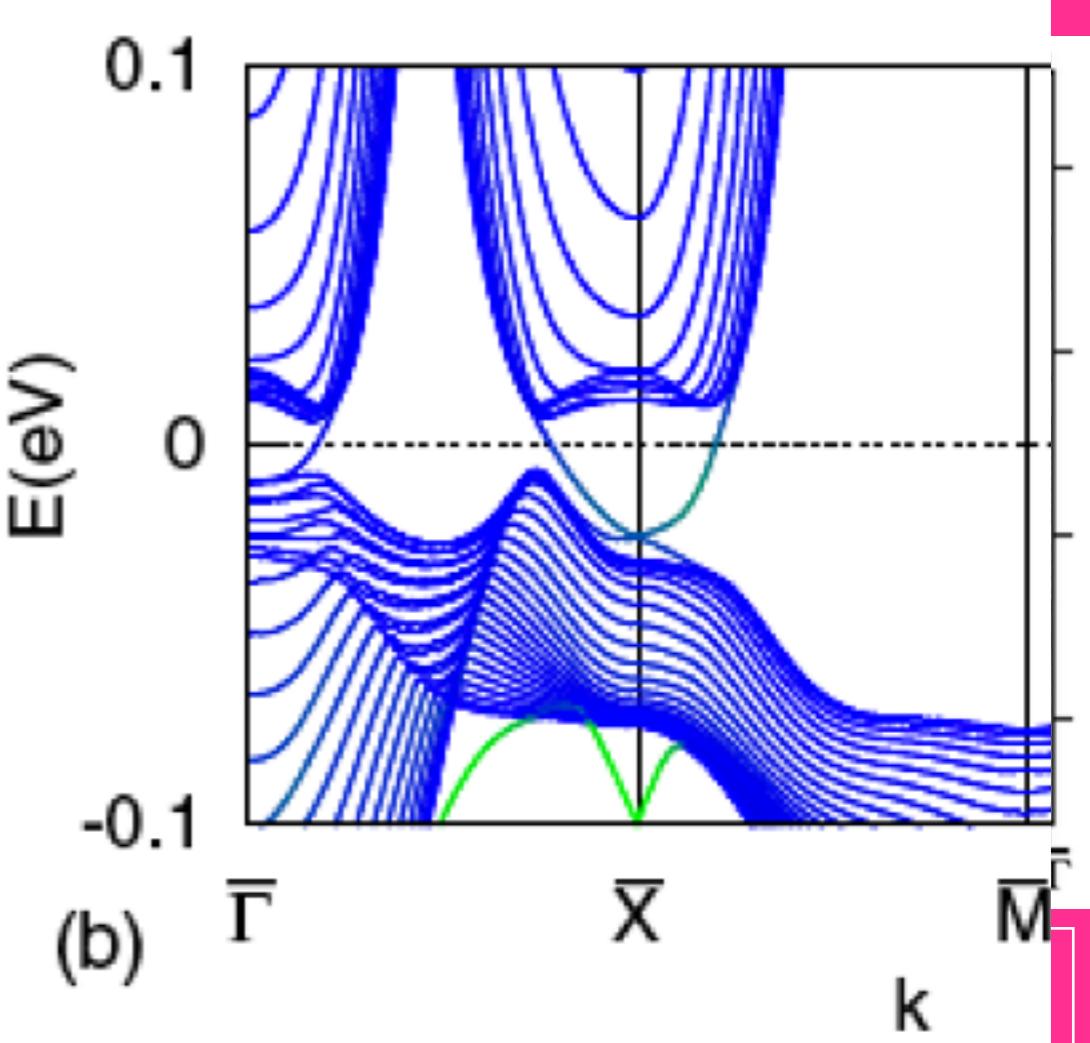
SmB₆



Three SS pockets centered at $\bar{\Gamma}/\bar{X}$ point

N. Xu et al., Phy. Rev. B 88, 121102(R) (2013)

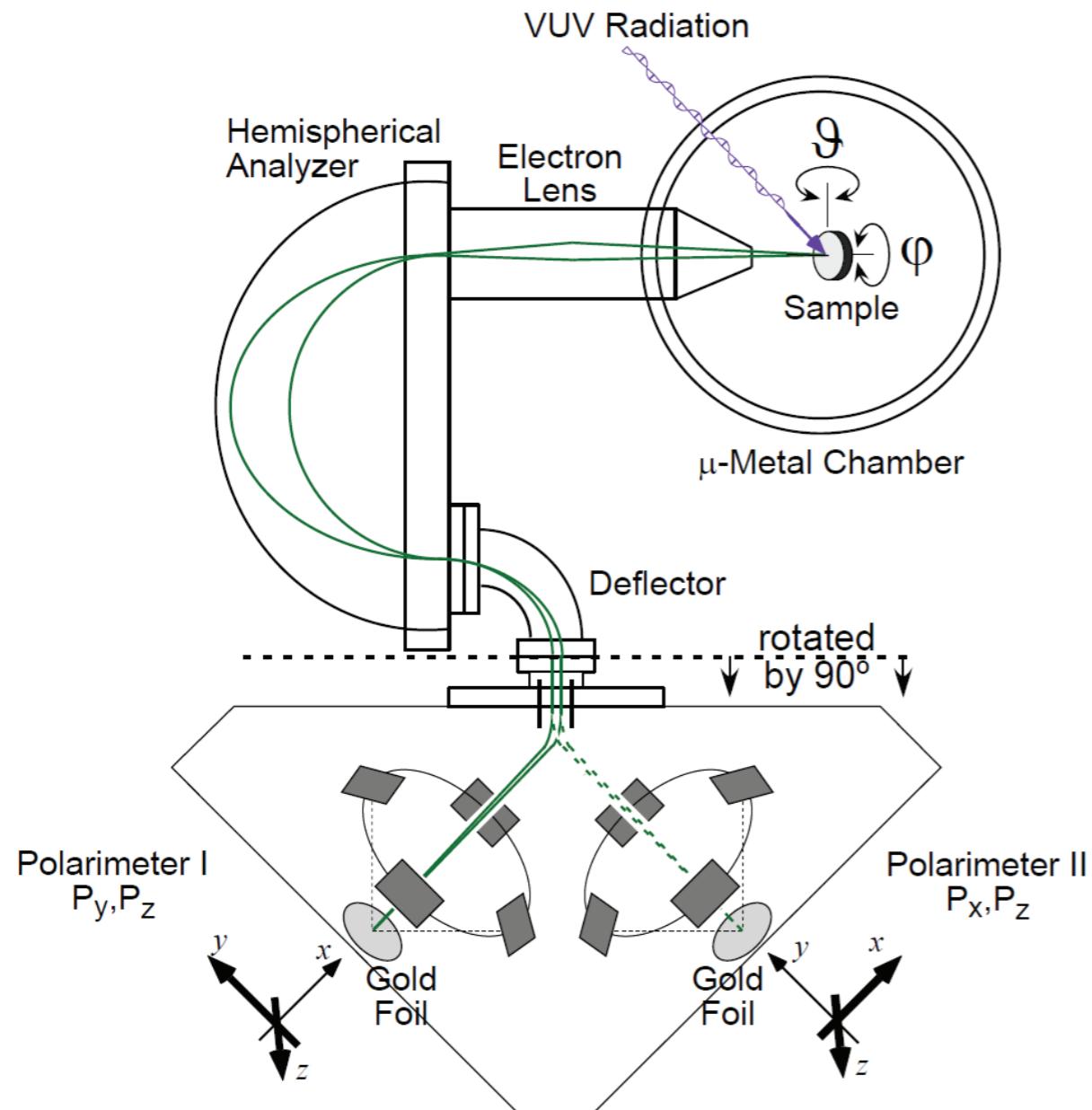
Theoretical prediction of TKI



Pier Paolo Baruselli and Matthias Vojta, PRB 90, 201106(R) (2014)

SARPES

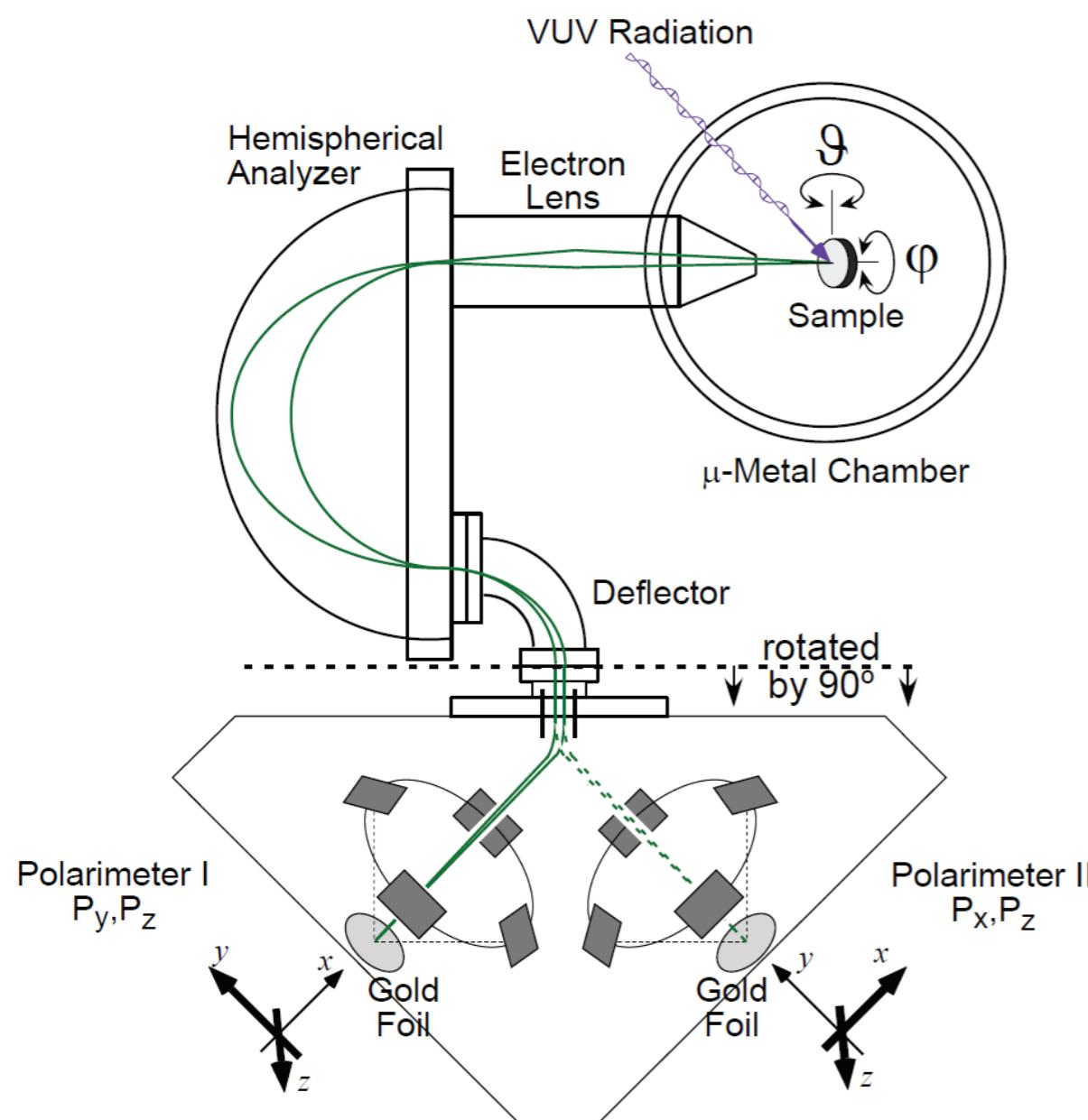
COPHEE = The **C**Complete **P**Hoto**E**mission **E**xperiment



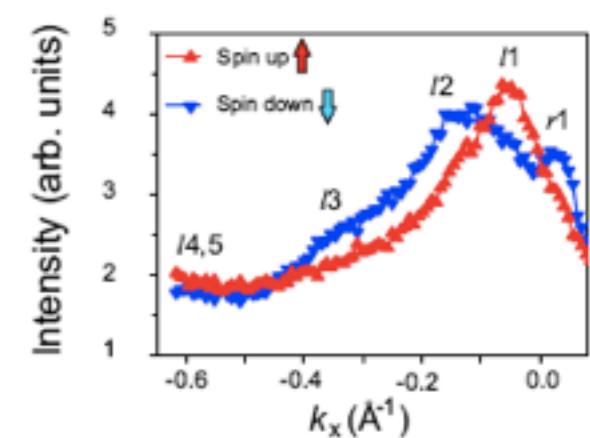
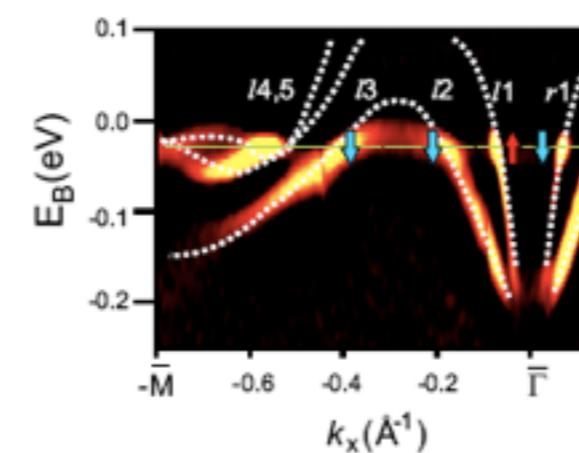
Access to “all” quantum numbers of the
electron: energy, momentum (3D) and spin (3D)

SARPES

COPHEE = The **C**Complete **P**Hoto**E**mission **E**xperiment



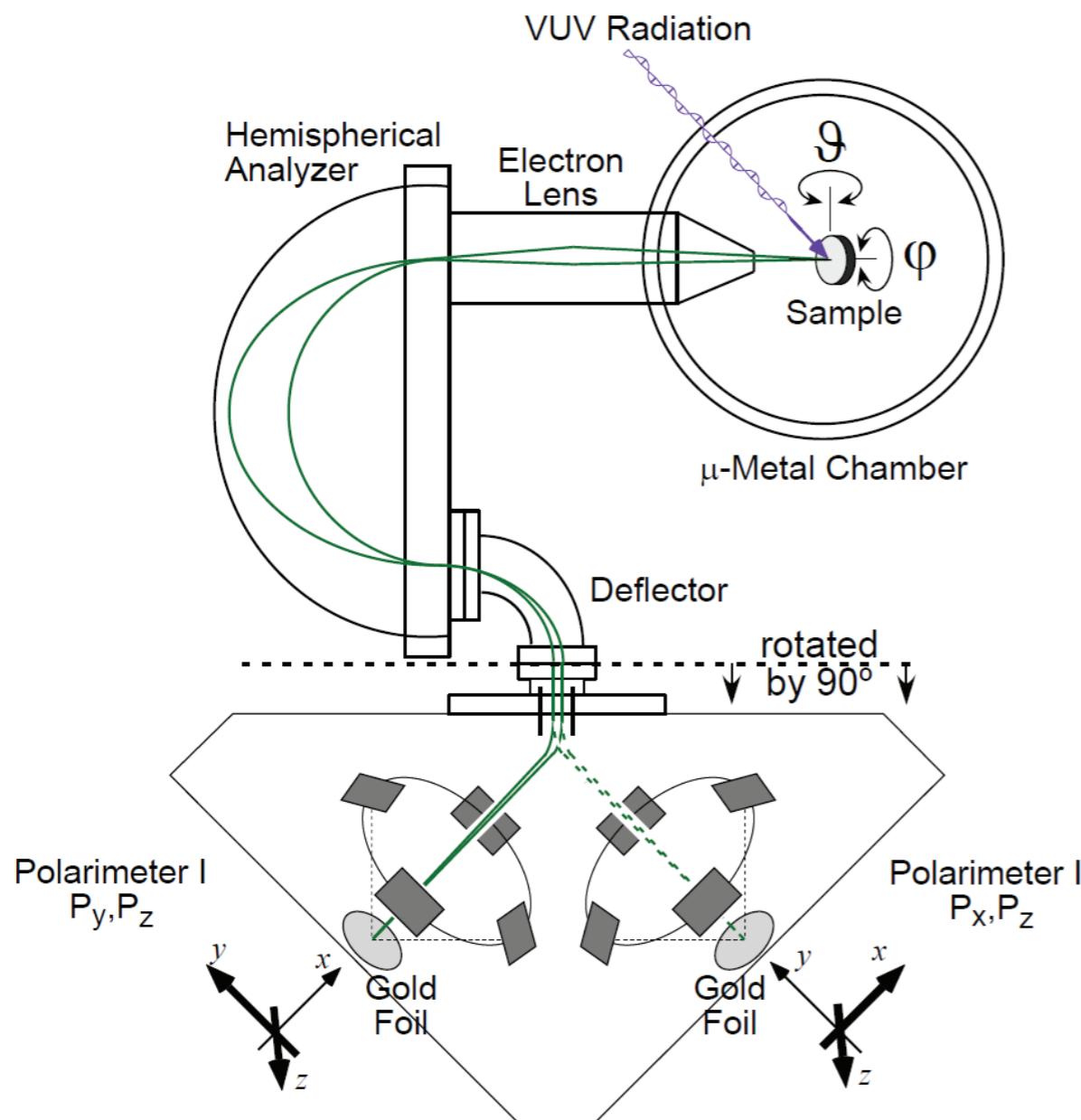
Access to “all” quantum numbers of the
electron: energy, momentum (3D) and spin (3D)



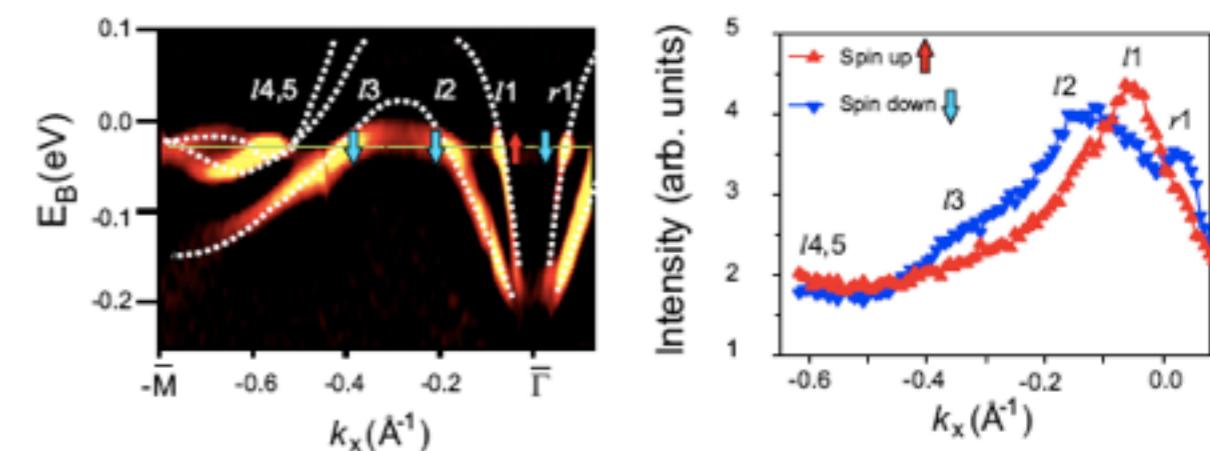
D. Hsieh et al., Science 323, 919 (2009)

SARPES

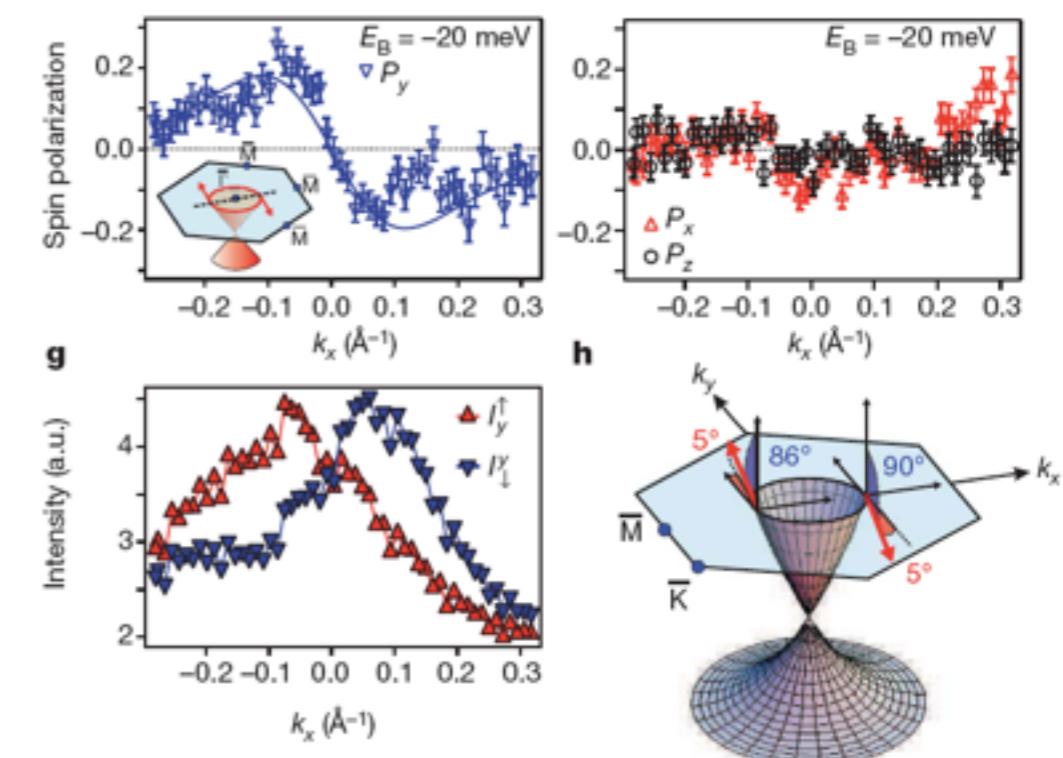
COPHEE = The **C**Complete **P**Hoto**E**mission **E**xperiment



Access to “all” quantum numbers of the electron: energy, momentum (3D) and spin (3D)

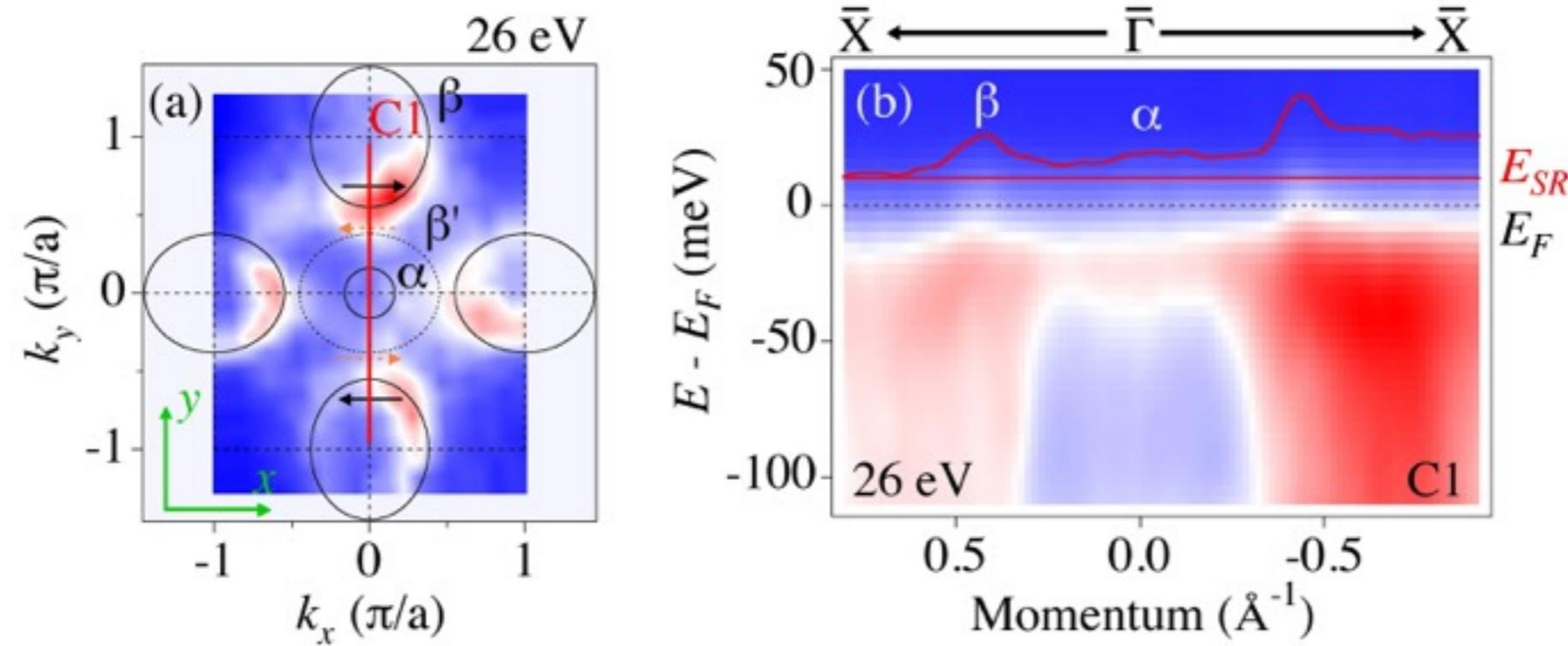


D. Hsieh et al., Science 323, 919 (2009)

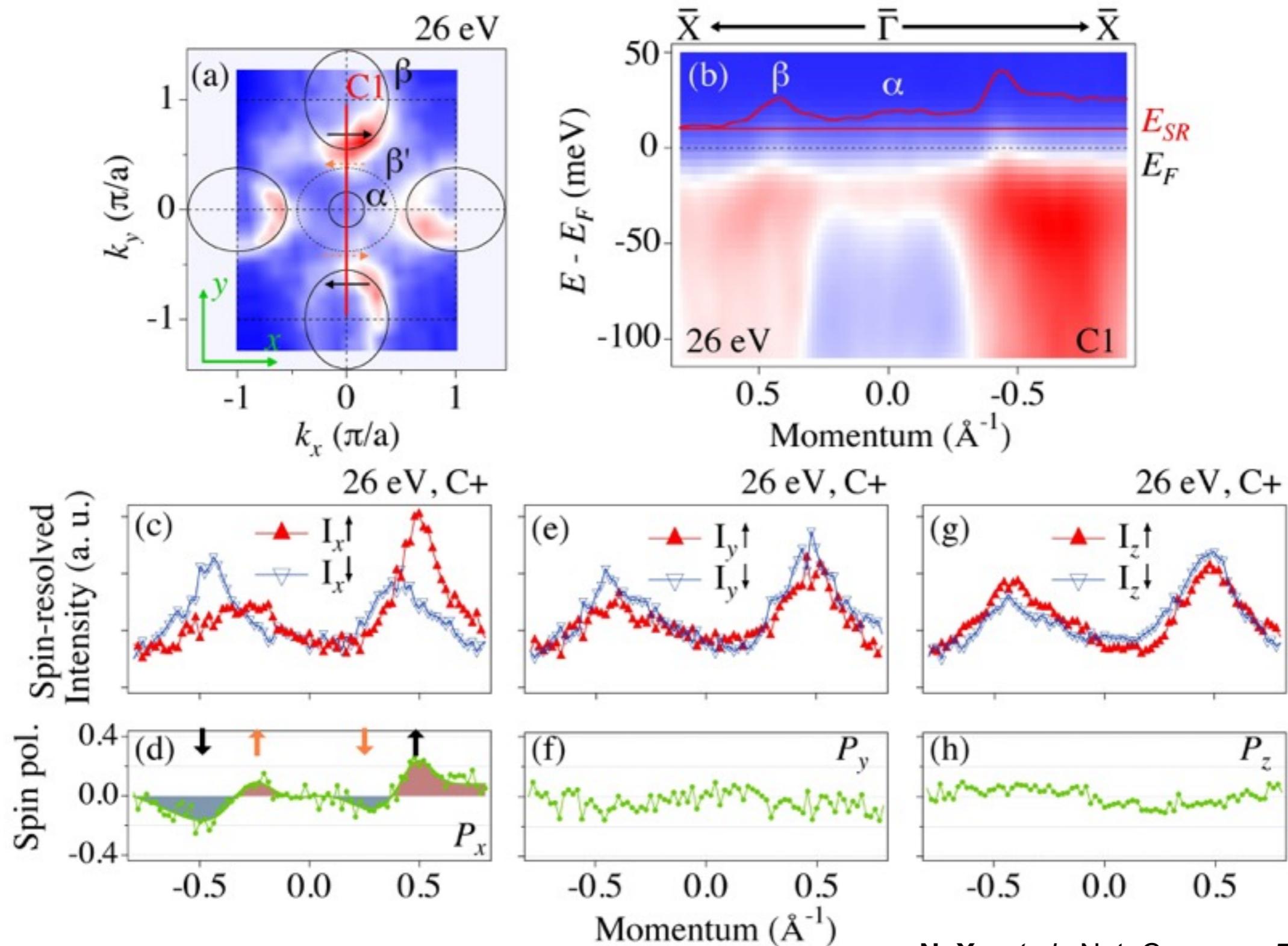


D. Hsieh et al., Nature 460, 1101 (2009)

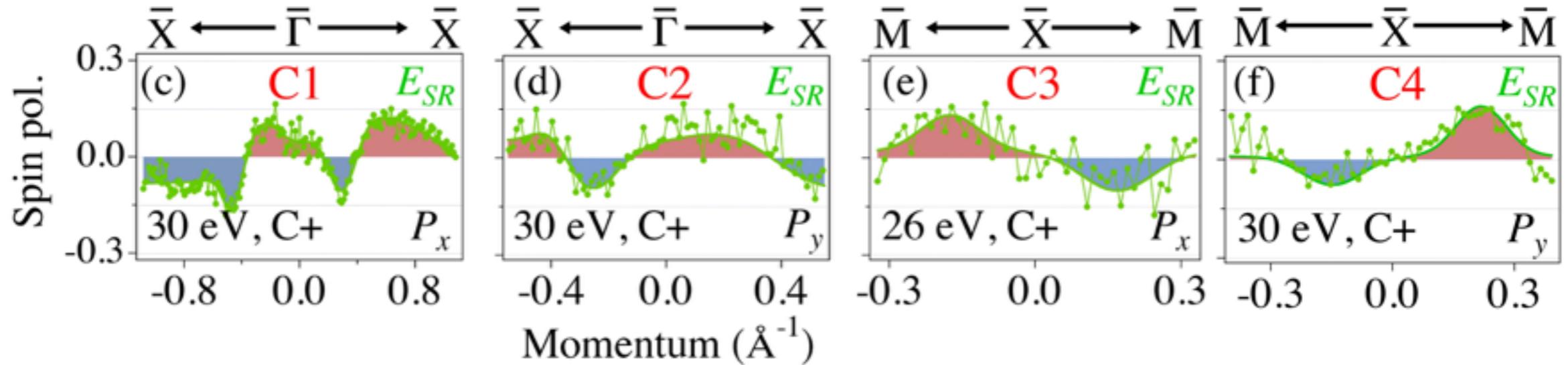
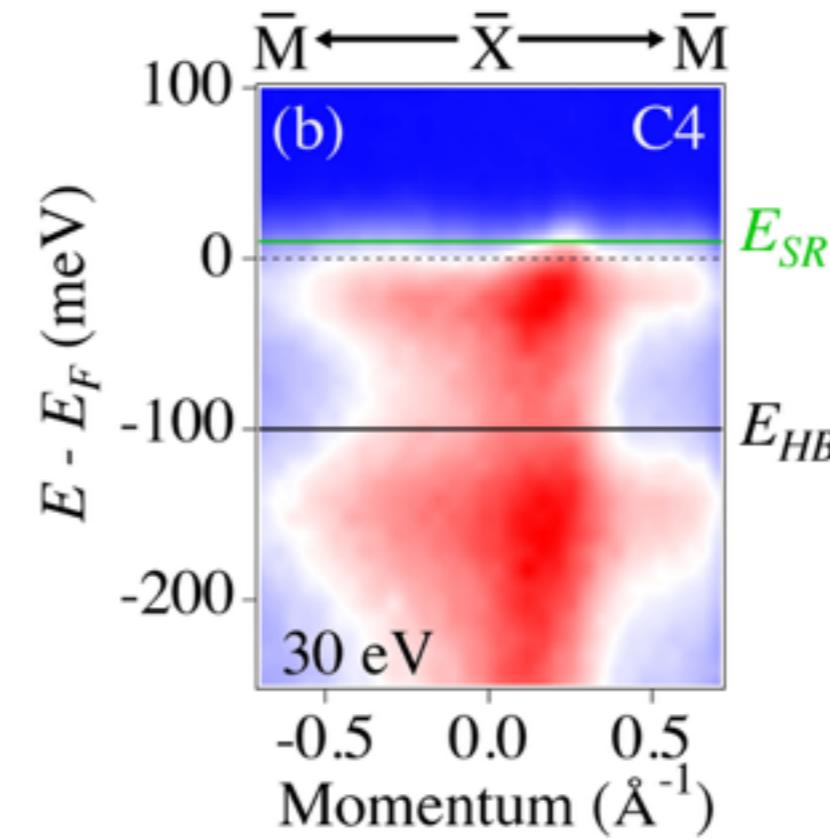
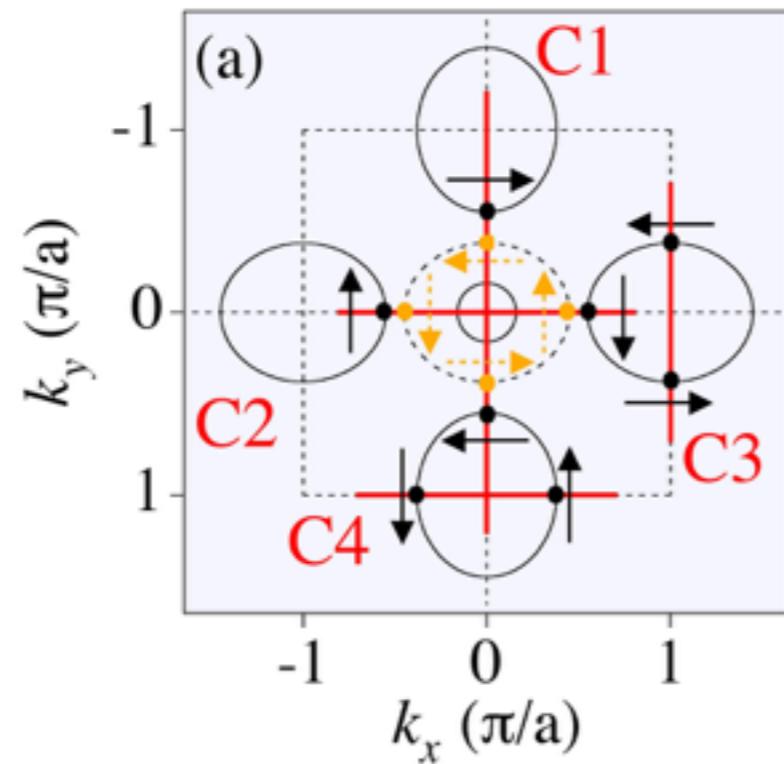
Spin polarization



Spin polarization

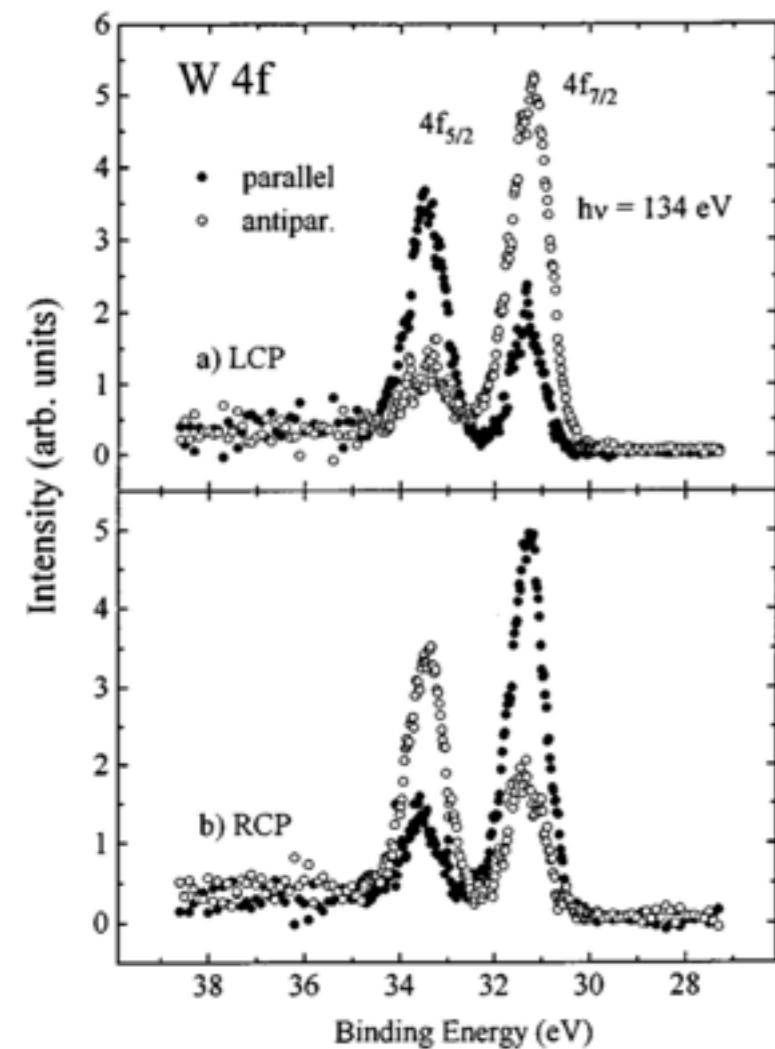


Spin texture



Spin signal from Photoemission effect

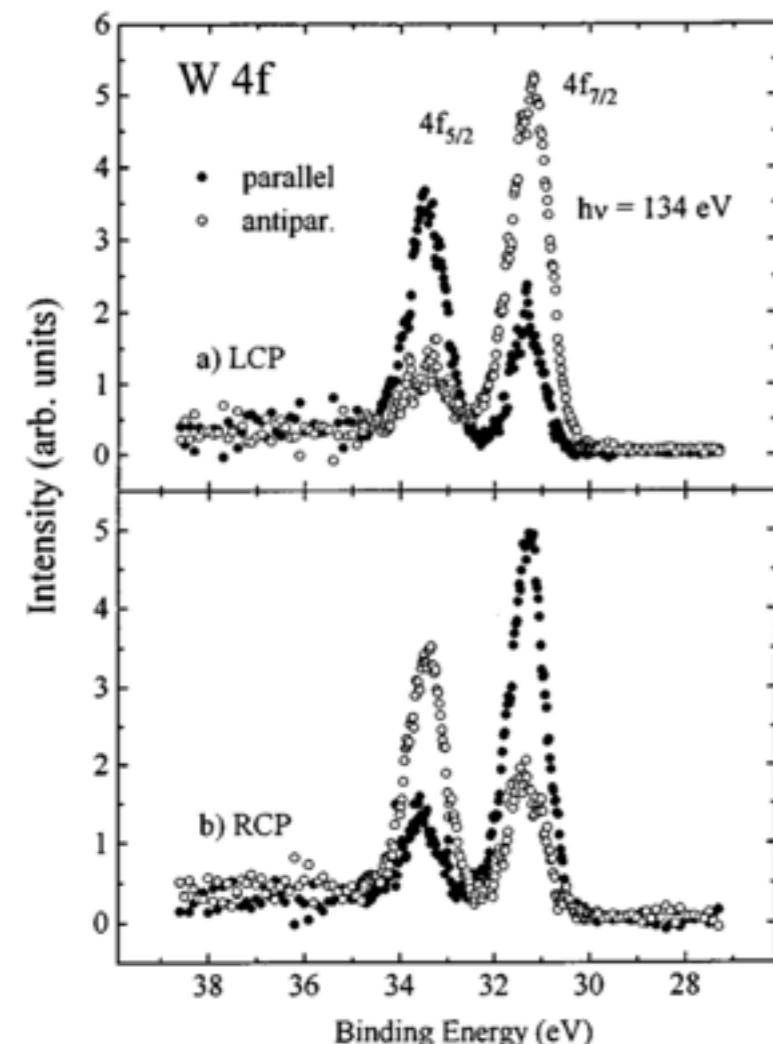
core levels of non-magnetic materials



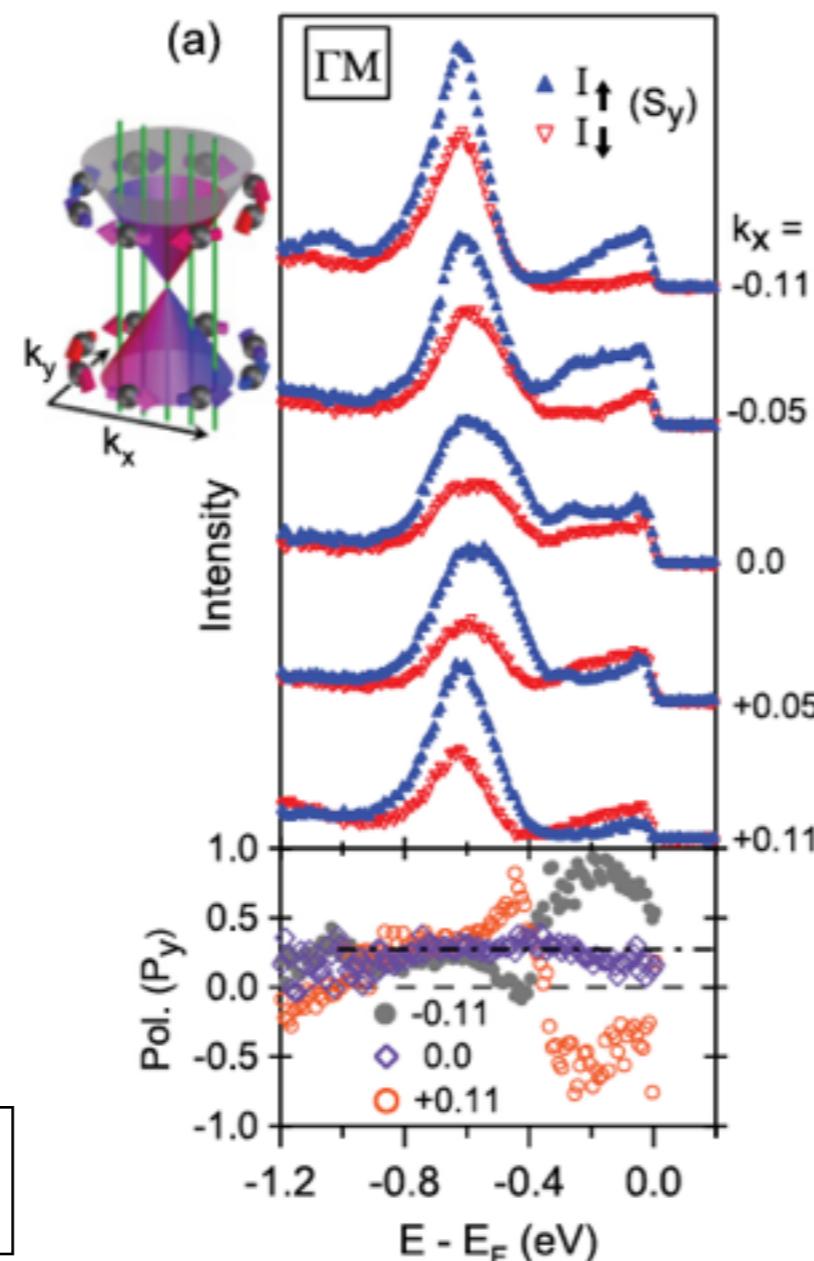
K. Starke *et al.*, Phys. Rev. B 53, 10544 (1996).

Spin signal from Photoemission effect

core levels of non-magnetic materials



bulk valence bands of topological insulators

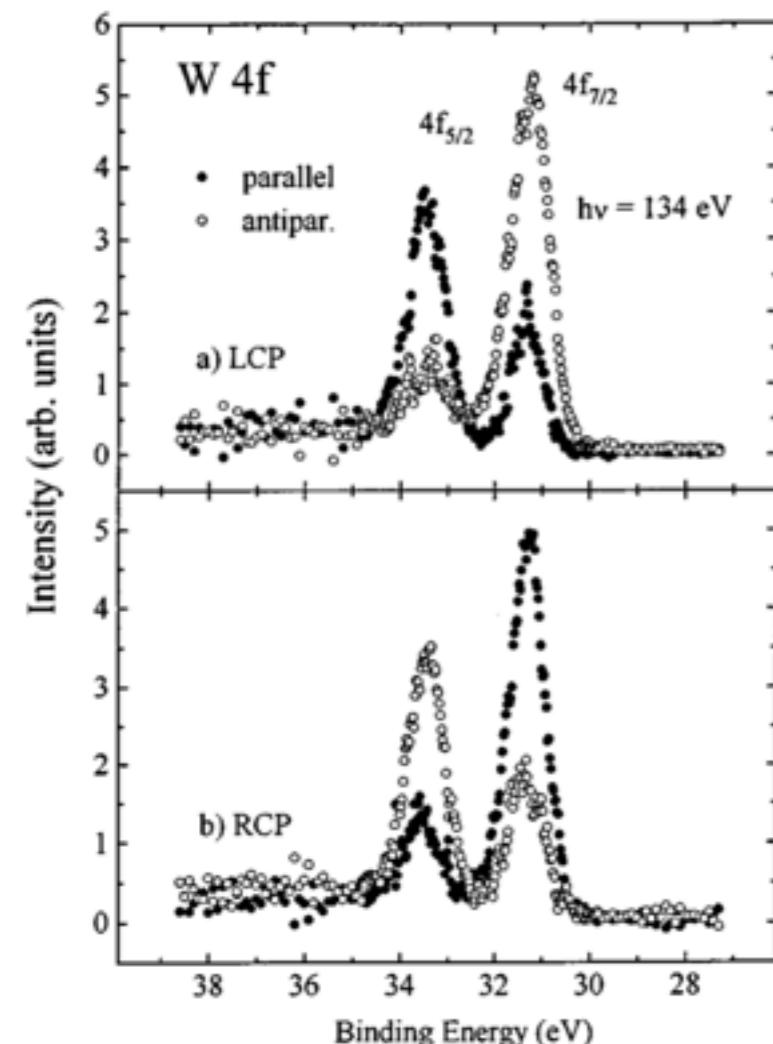


K. Starke *et al.*, Phys. Rev. B 53, 10544 (1996).

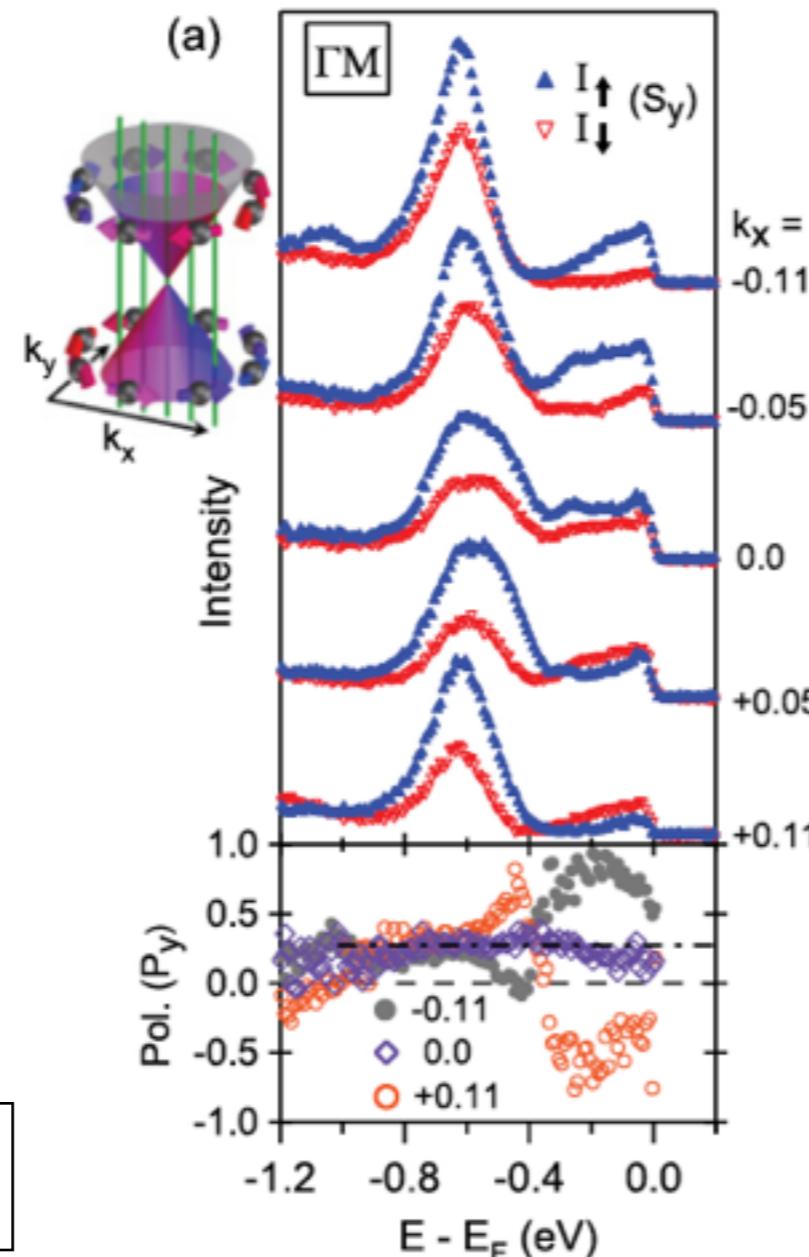
C. Jozwiak *et al.*, Phys. Rev. B 84, 165113 (2011).

Spin signal from Photoemission effect

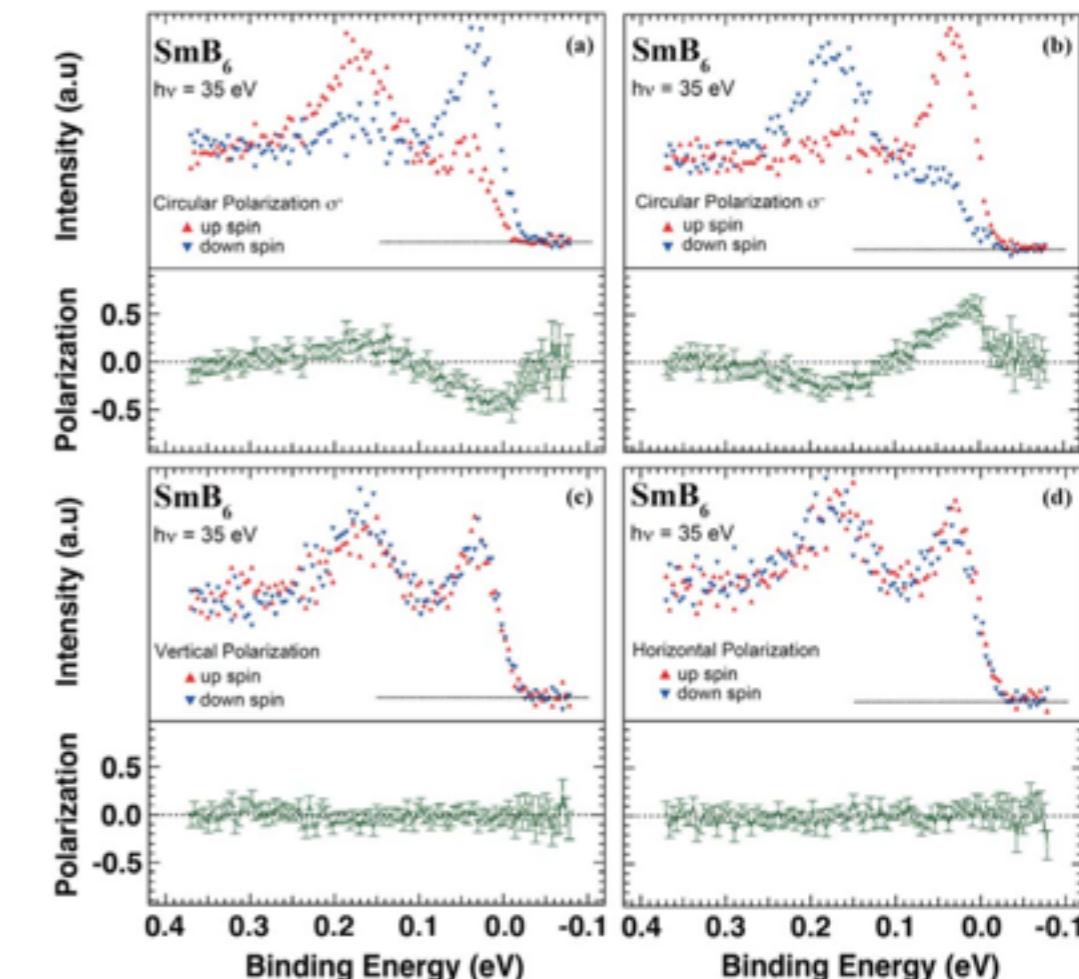
core levels of non-magnetic materials



bulk valence bands of topological insulators



bulk f states of SmB₆

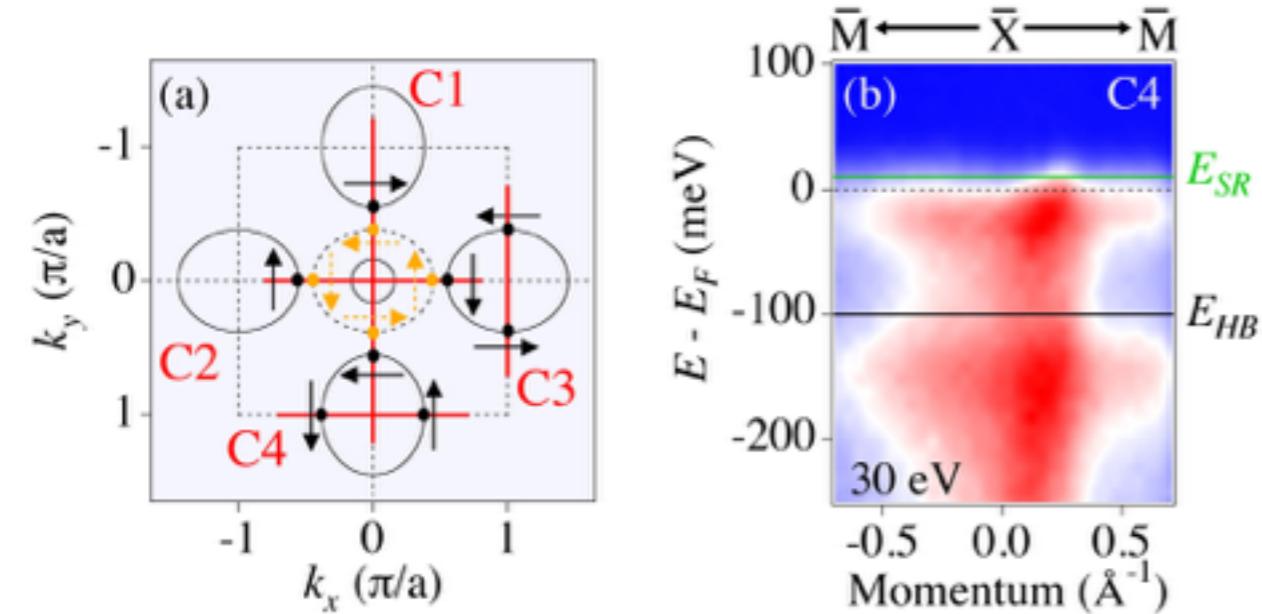


K. Starke *et al.*, Phys. Rev. B 53, 10544 (1996).

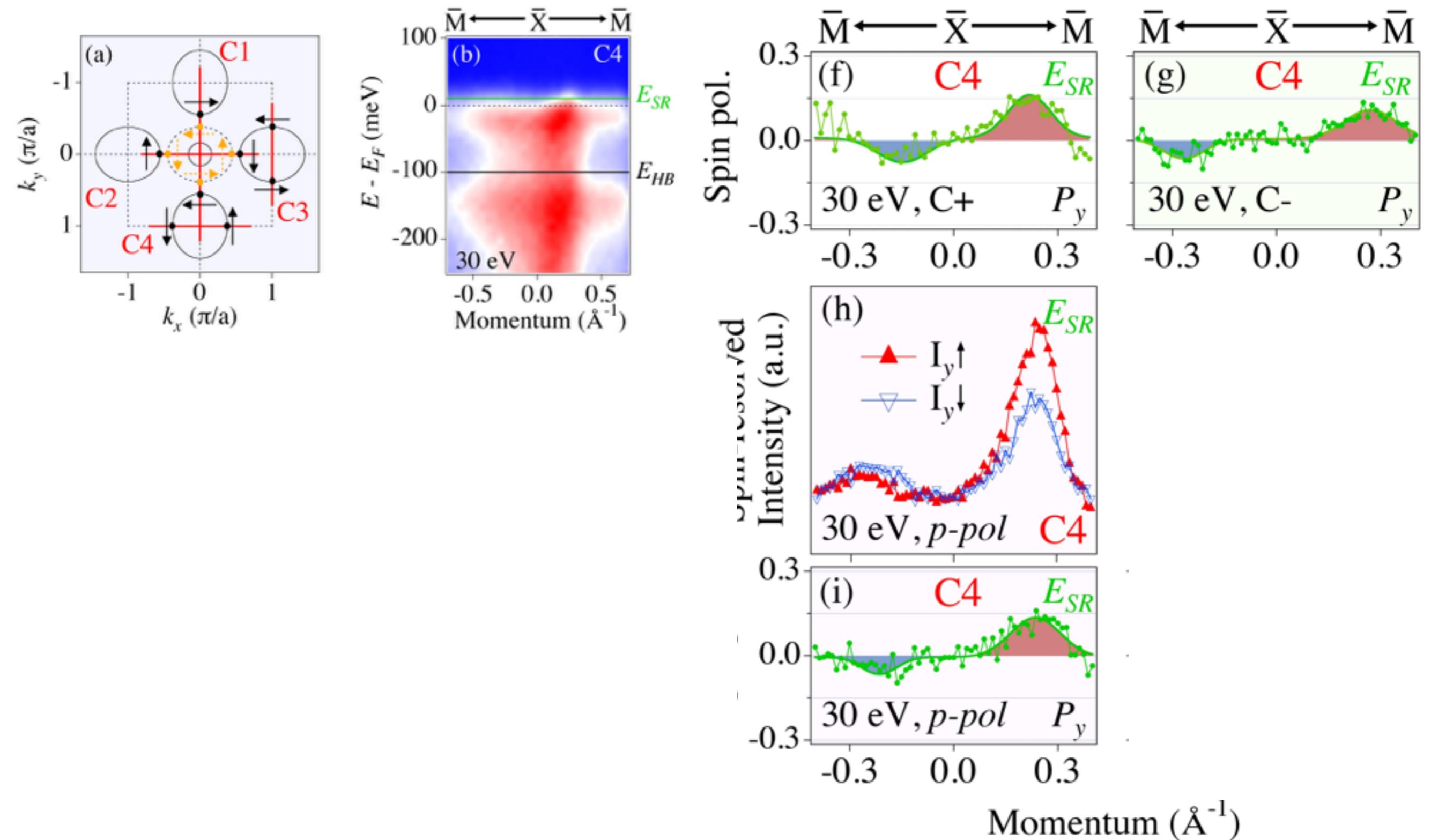
S. Suga *et al.*, J. Phys. Soc. Jpn. 83, 014705 (2014).

C. Jozwiak *et al.*, Phys. Rev. B 84, 165113 (2011).

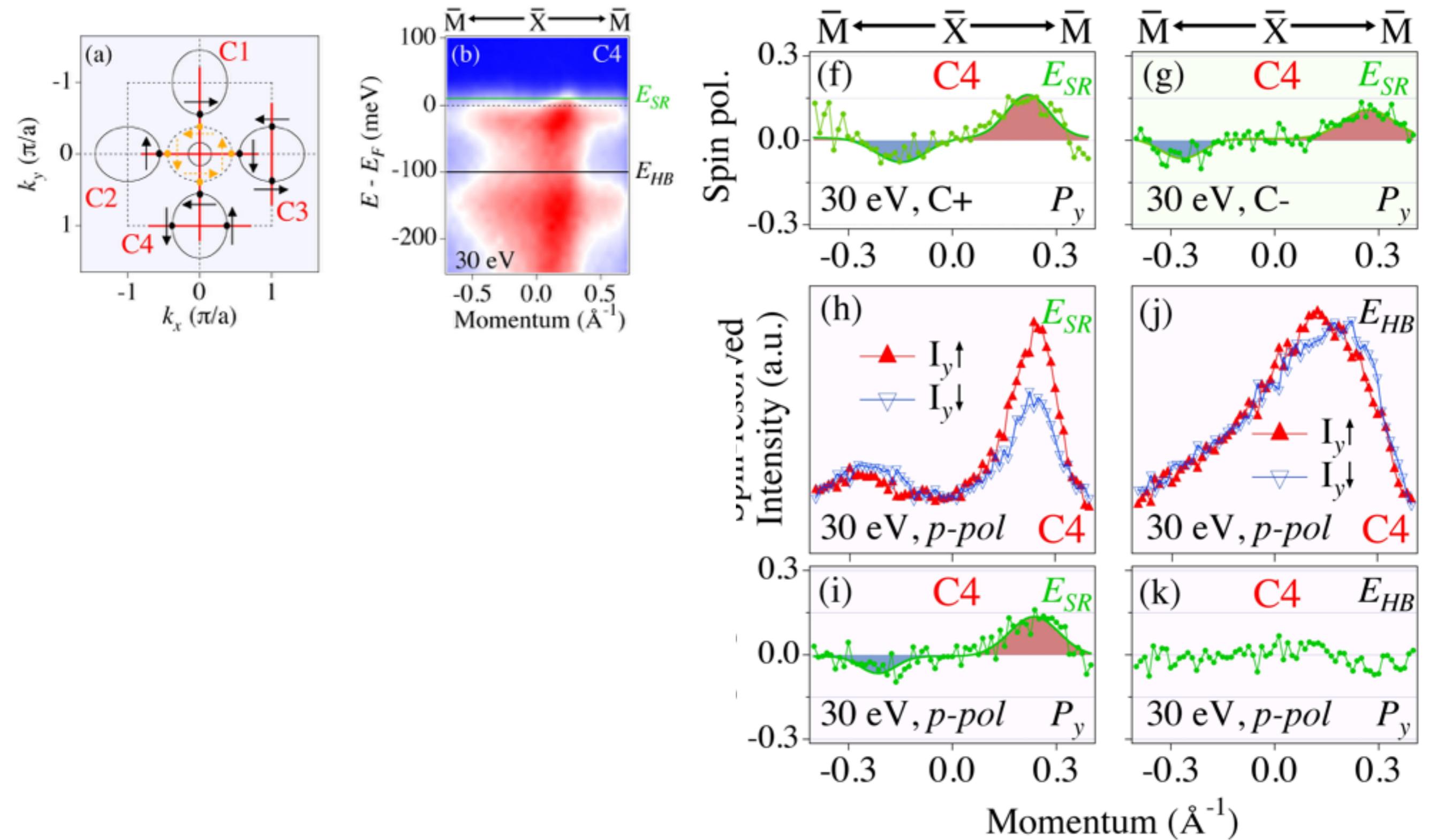
Polarization dependence



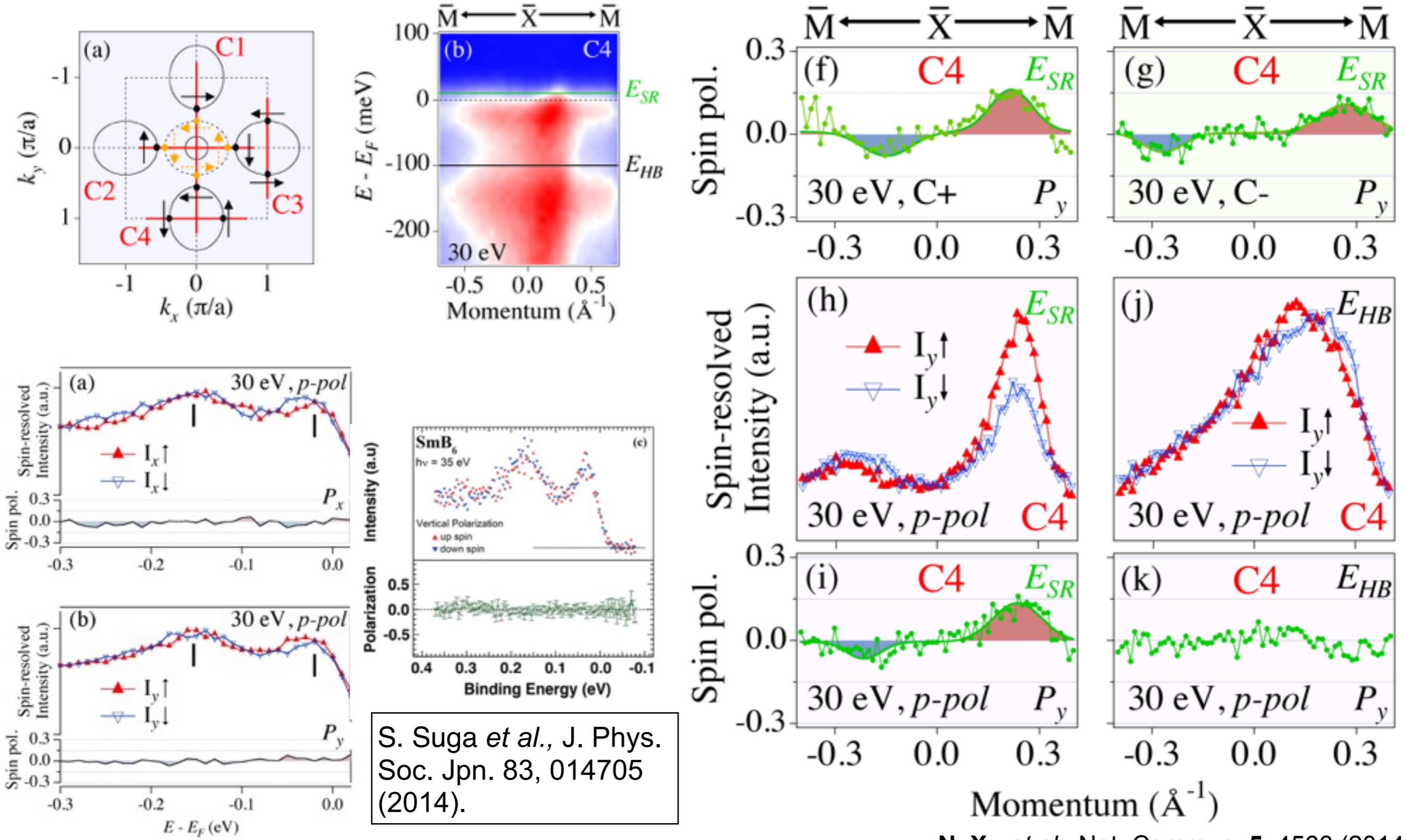
Polarization dependence



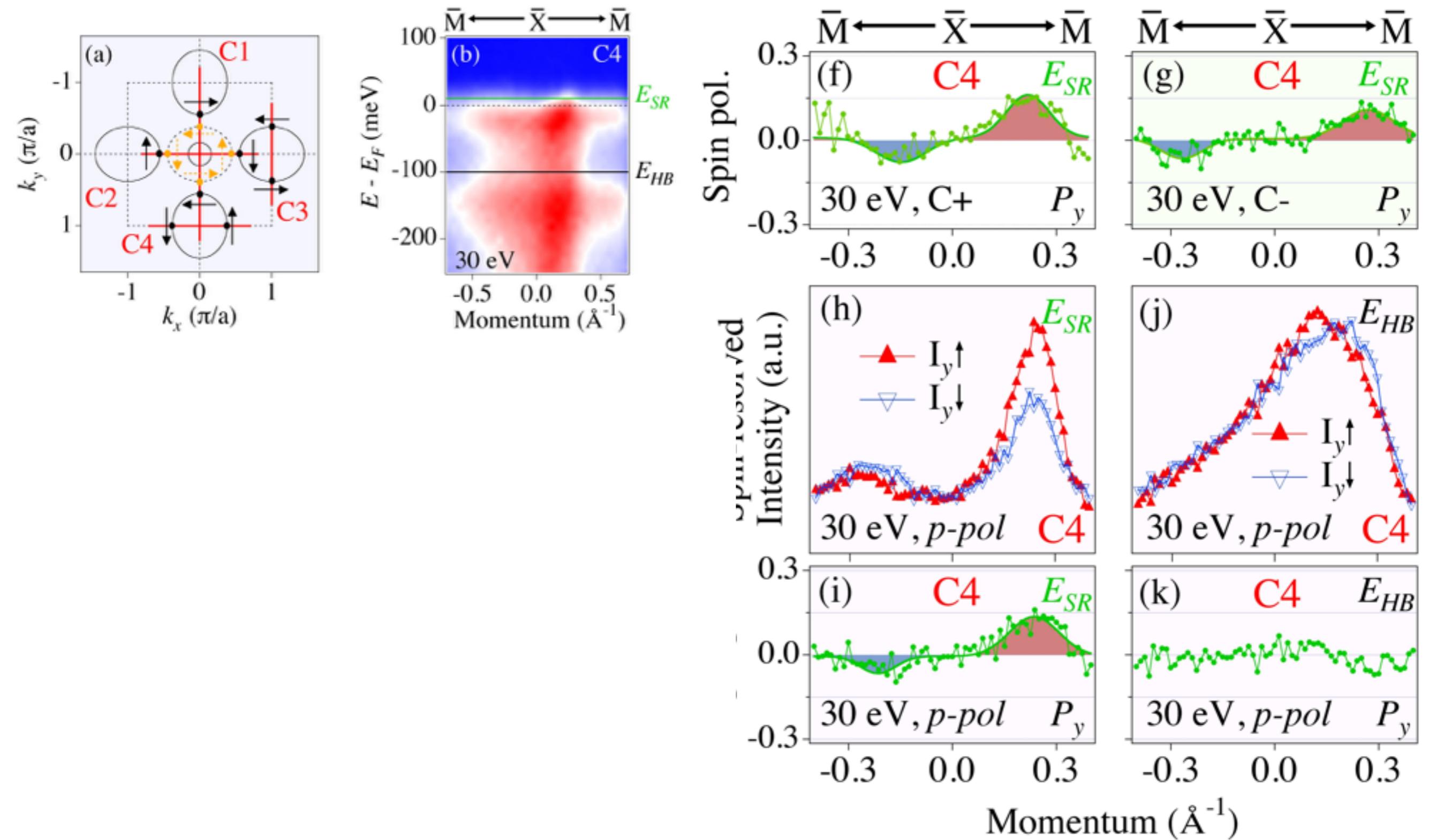
Polarization dependence



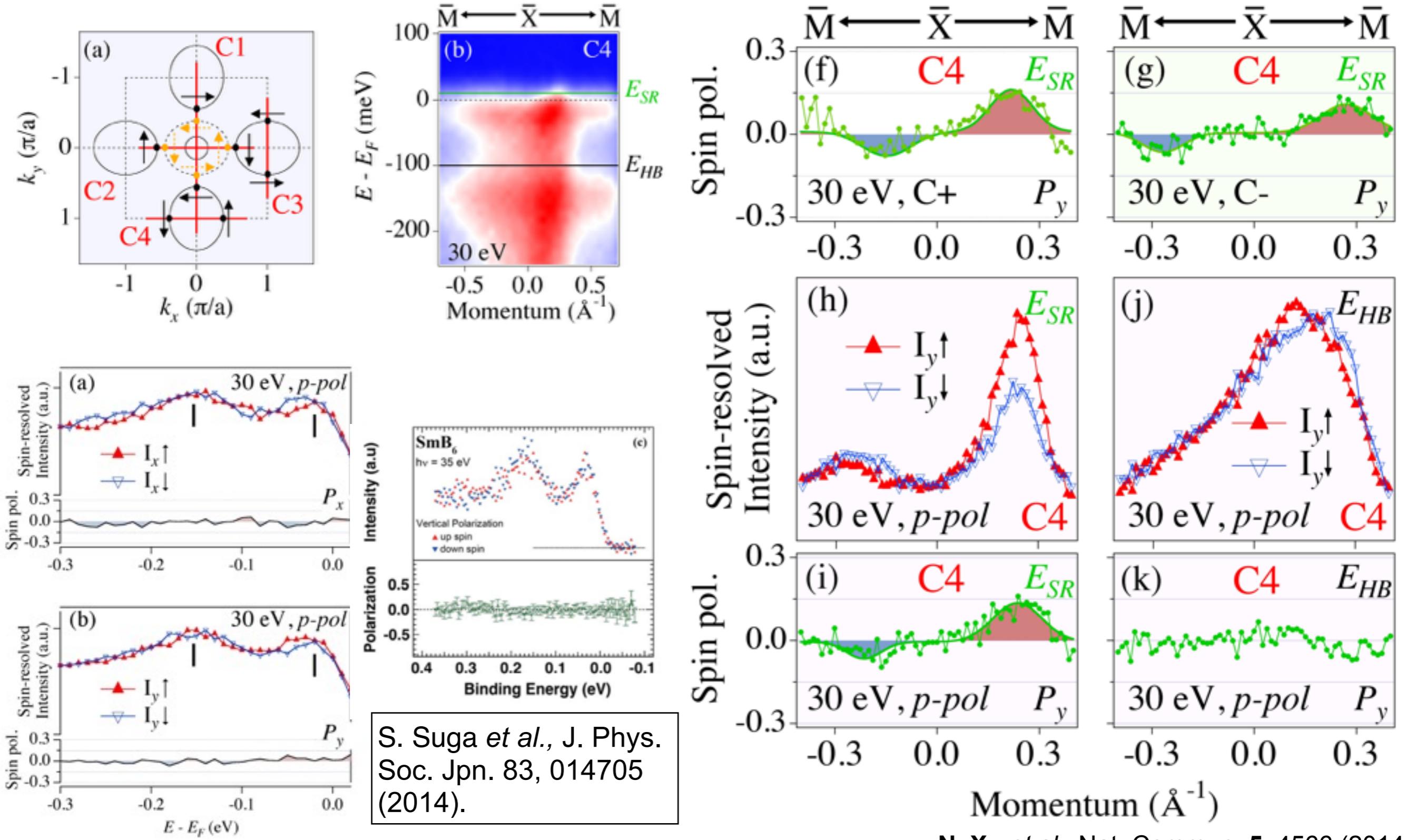
Polarization dependence



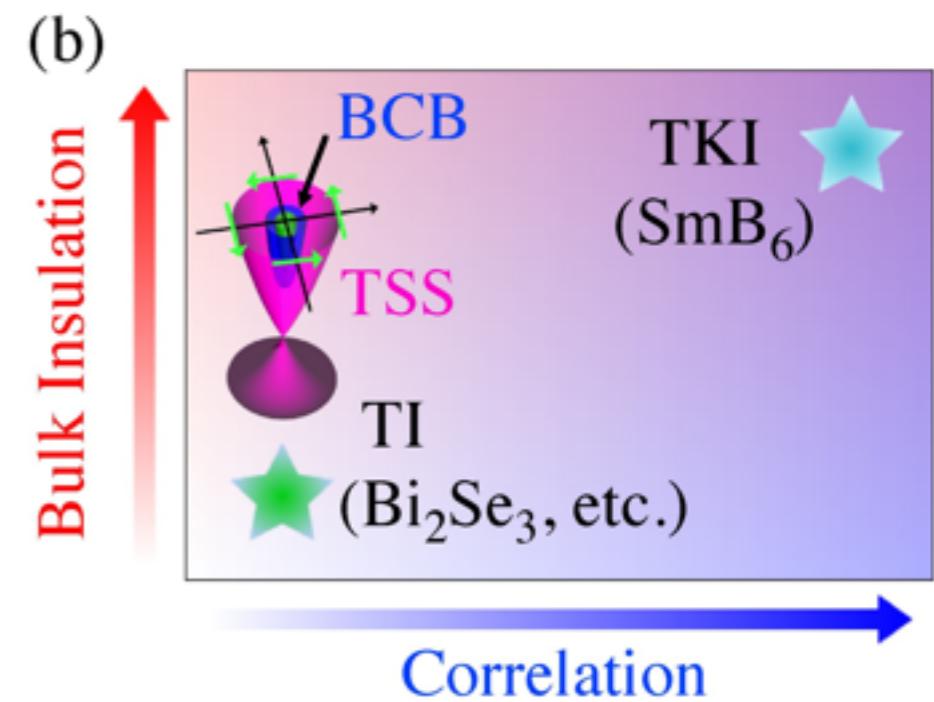
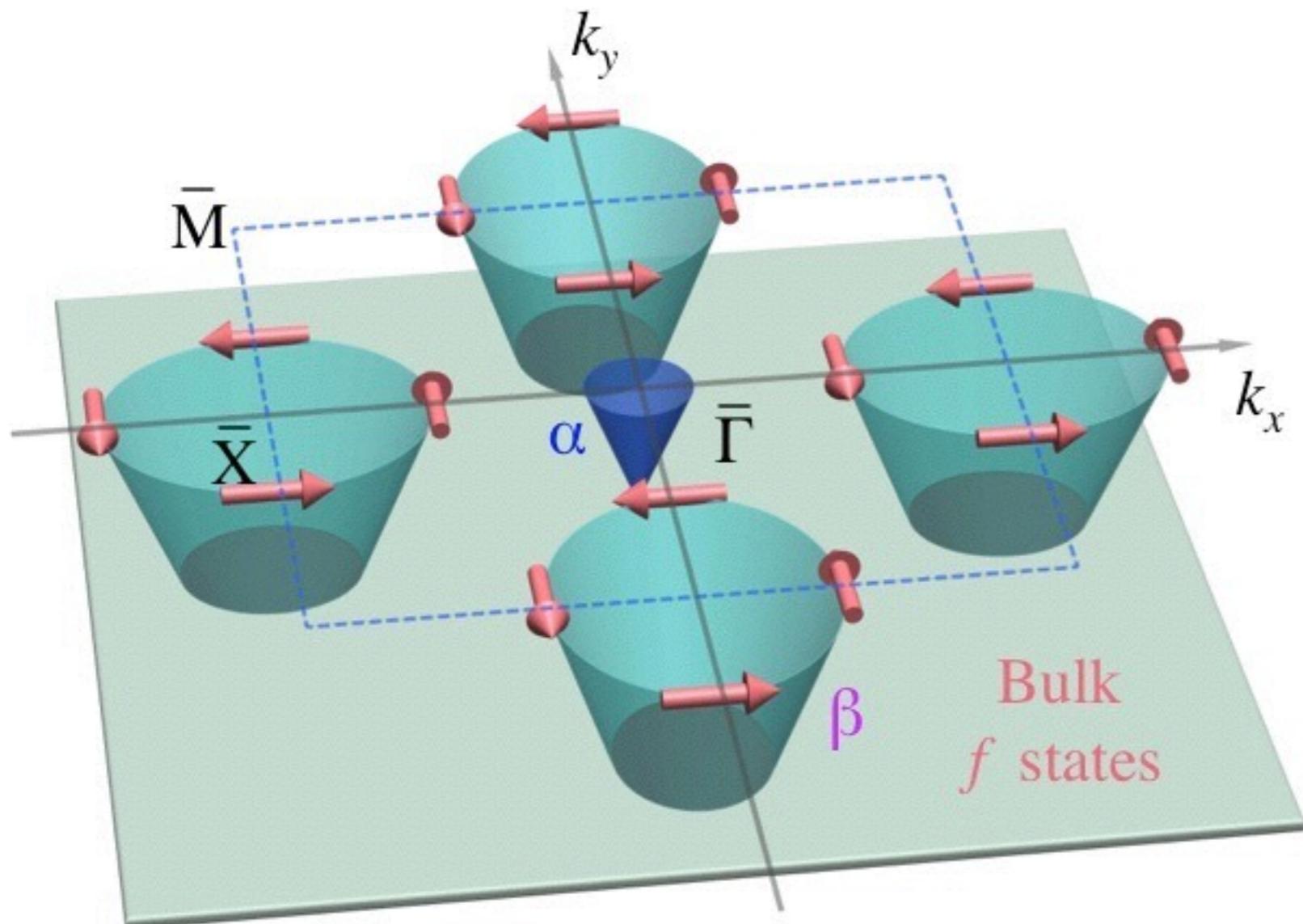
Polarization dependence



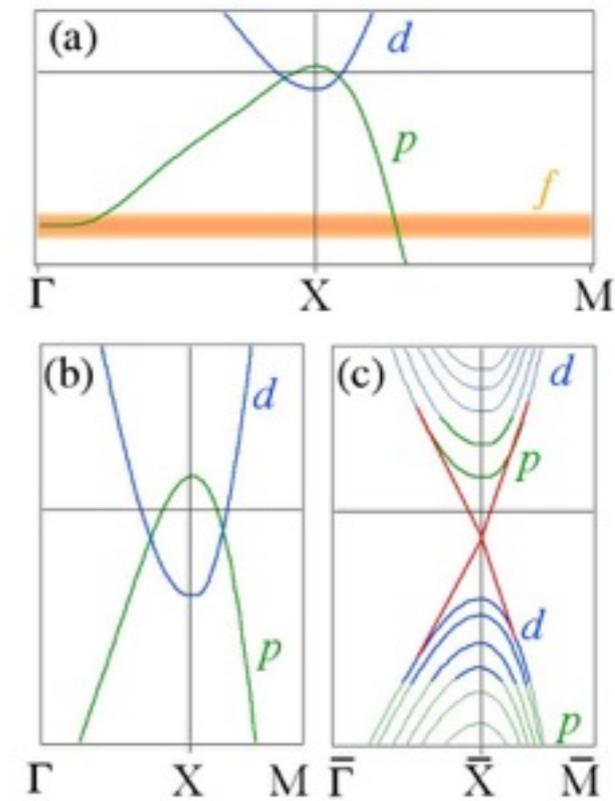
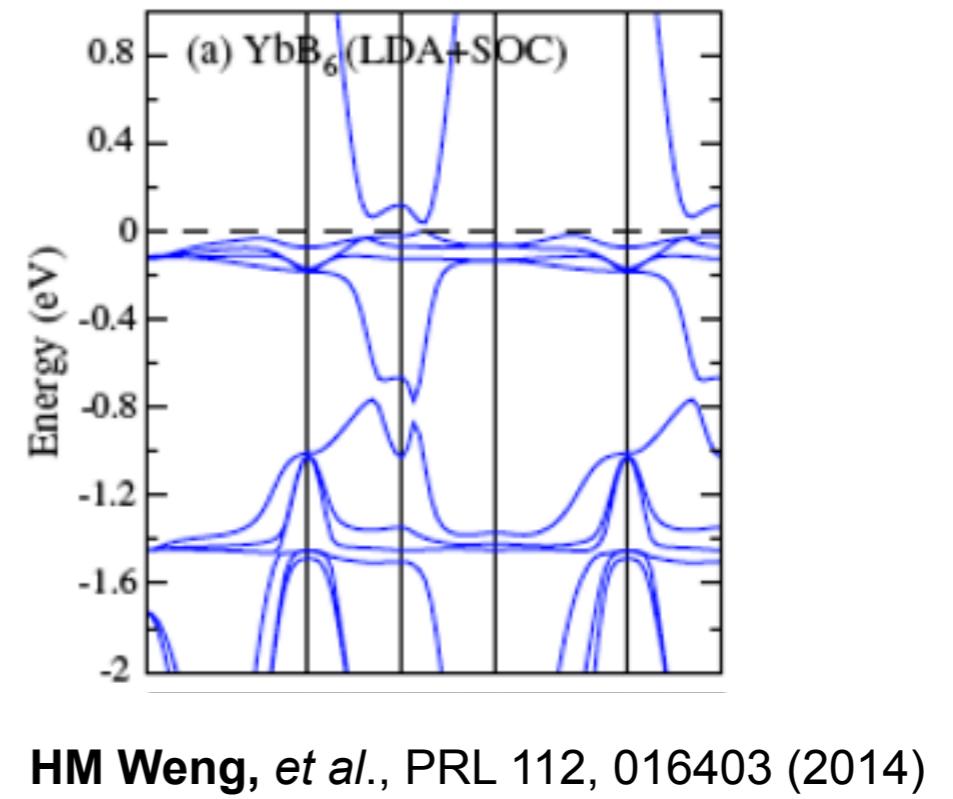
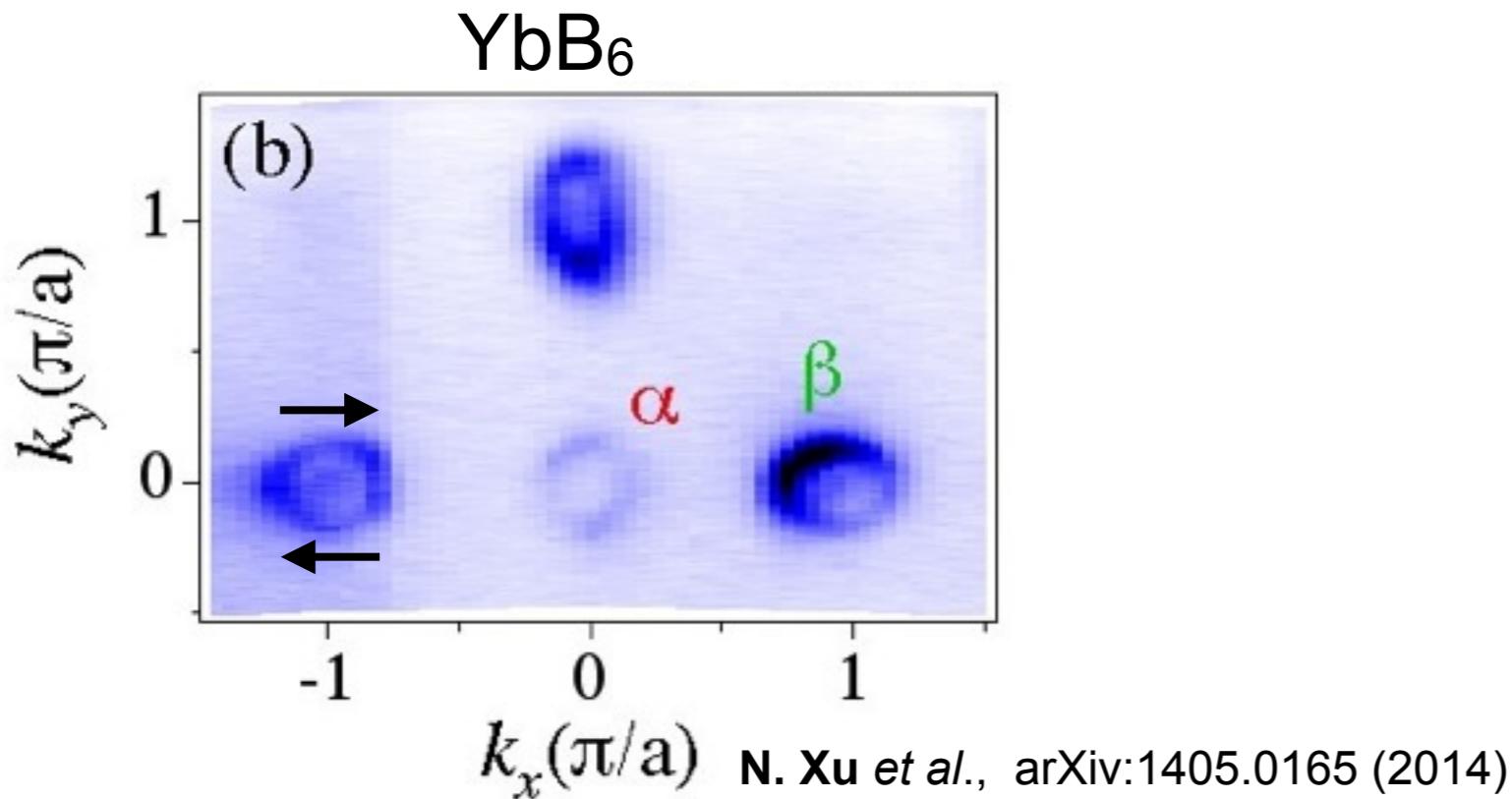
Polarization dependence



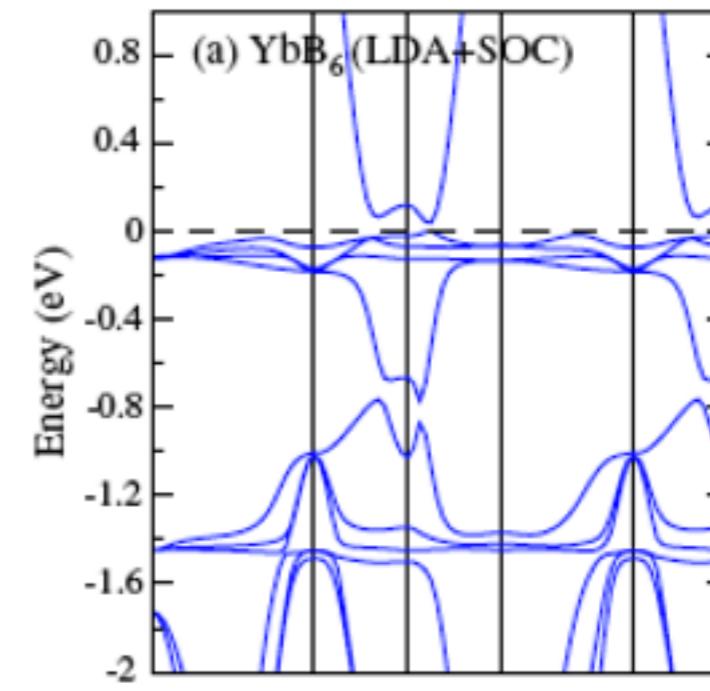
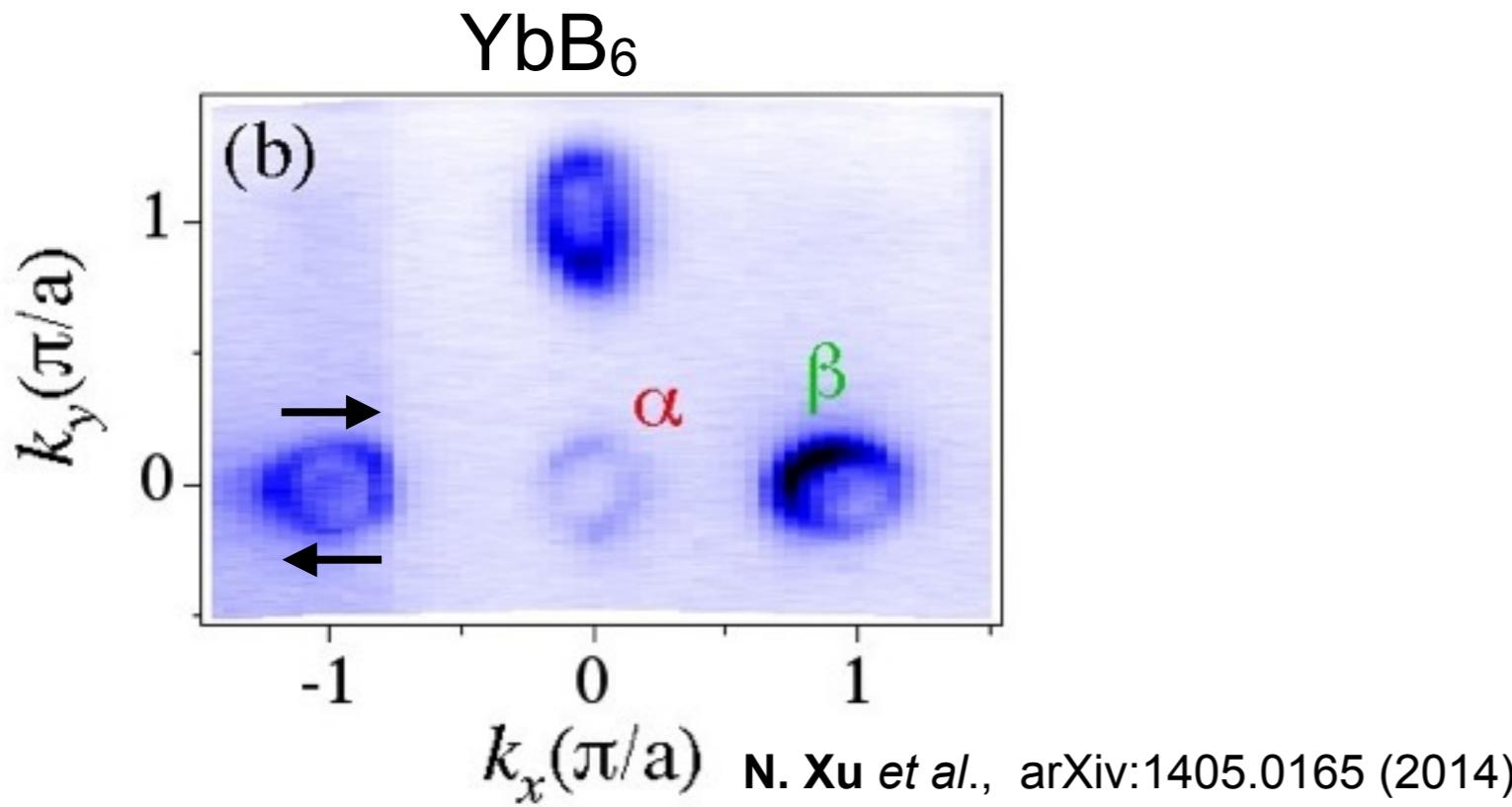
Summary



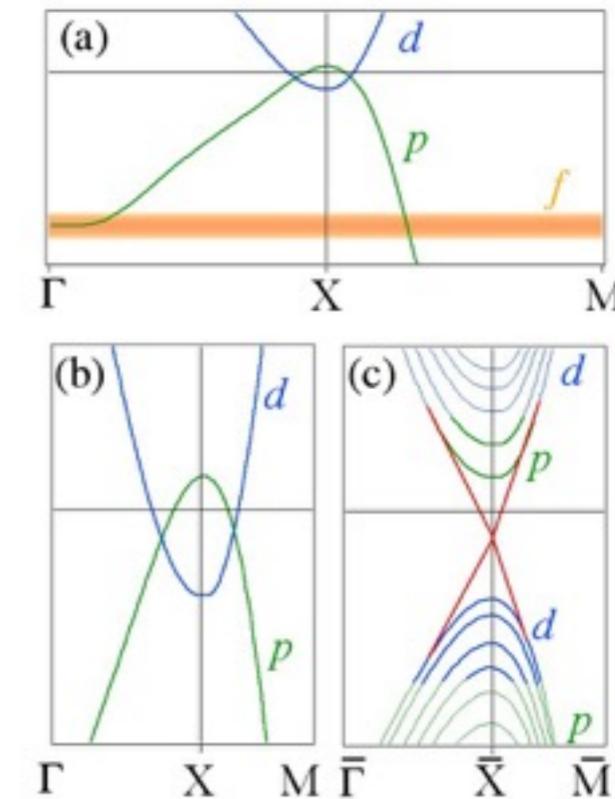
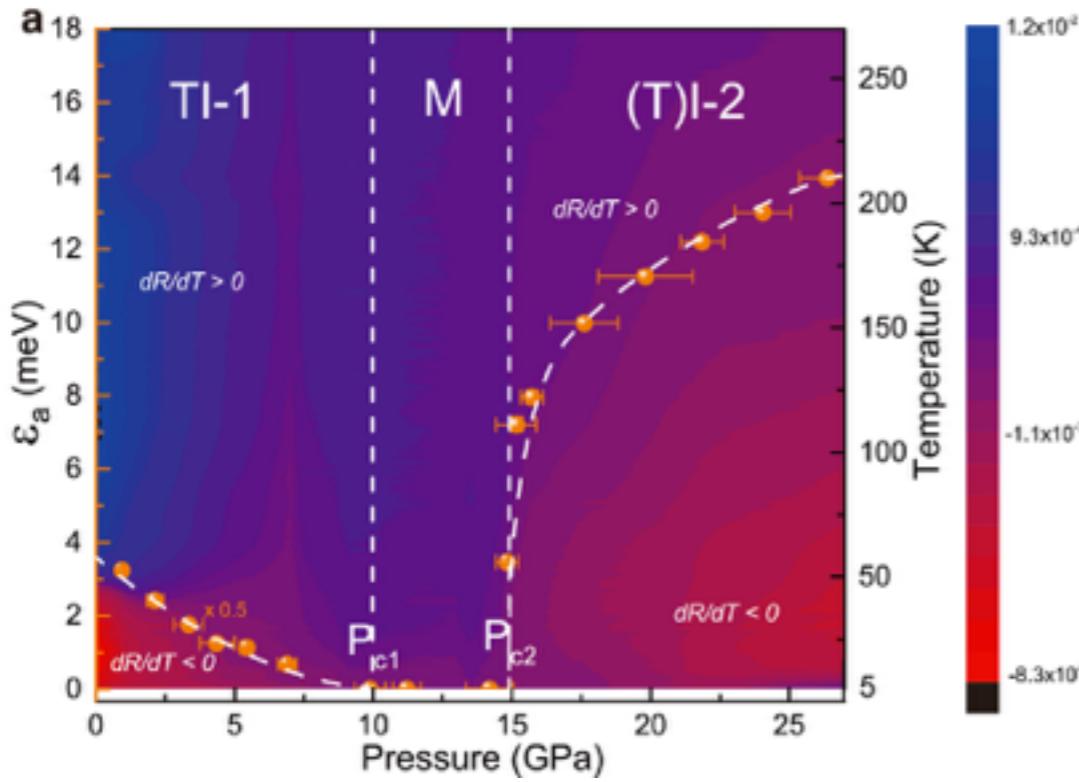
Summary



Summary



HM Weng, et al., PRL 112, 016403 (2014)





Thanks for your attention!